# NAVAL POSTGRADUATE SCHOOL Monterey, California



## **THESIS**

## DESIGN OF A UNIVERSAL TEST PLATFORM FOR RADIATION TESTING OF DIGITAL COMPONENTS

by

Duane E. Amsler Jr.

September 1996

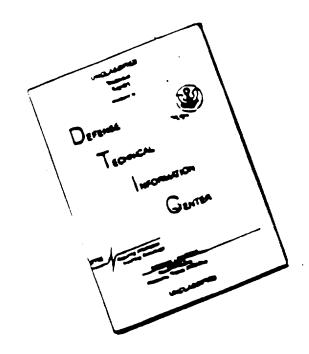
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# DESIGN OF A UNIVERSAL TEST PLATFORM FOR RADIATION TESTING OF DIGITAL COMPONENTS

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Submitted in partial fulfillment of the requirements for the degree of

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September 1996

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#### **ABSTRACT**

In this research, programmable, microcontroller-based test hardware was designed, constructed, debugged, and programmed. The wire-wrapped board will be used to test two custom static random access memory (SRAM) chips, as well as other custom chips designed at the Naval Postgraduate School. Components for the test hardware were selected to allow prototyping with standard parts that can later be replaced with radiation hardened parts as budgets permit. Control of the test hardware is via a RS-232 serial interface, which allows remote control programming and monitoring of the test hardware and device being tested.

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#### I. INTRODUCTION

#### A. OVERVIEW

One of the major constraints in designing for the space environment is the ability of parts to withstand radiation. Radiation hardened (RAD hard) parts are typically reengineered designs of commercially available parts, which are adapted to a RAD hard fabrication process. Traditional designs are reworked to assure immunity to such radiation effects as latchup and single-event upsets (SEUs). The additional engineering and radiation hardened process significantly increases cost and time to market. Ongoing research at the Naval Postgraduate School is developing a process that should allow off-the-shelf gallium arsenide (GaAs) integrated circuits (IC) designs to be fabricated on specially prepared wafers that contain buried, low-temperature grown, GaAs buffer layers. The intent of the program is to run these specially prepared wafers through commercial GaAs wafer processing lines to create radiation-hardened ICs, without additional IC re-engineering and special IC processing steps.

The goal of this research is to create test hardware capable of testing ICs created using low-temperature (LT) GaAs wafers for functionality, as well as immunity to single-event upsets in a radiation environment. The original requirement was to test a Vitesse 256 X 4 static random access memory (SRAM), but additional requirements to test a Motorola 256 x 16 SRAM and a custom SEU detection IC were added. The test hardware is programmable through a RS-232 serial port and can be configured to read and write any desired data and address patterns for devices with up to 80 I/O pins.

Current work in this area is sparse. Oregon State University uses a basic 8051 design for teaching microprocessor basics and have developed very good monitor, which is used as part of this design. A previous thesis by Chris Mooney[1] address interfacing these two SRAMs to a satellite test board. The Mooney thesis design is only for these specific ICs and cannot be used independent of the satellite. This thesis creates a design that is capable of testing these two SRAMs, as well as a multitude of ICs, in a radiated environment.

#### **B. THESIS ORGANIZATION**

The goal of this thesis is to document the design, construction, testing, and programming of hardware that is capable of testing ICs in a radiation environment. To this end, the following organization will be followed. Chapter II will present an overview of the LT GaAs program, as

well as a brief overview of radiation effects. Chapter III discusses the various components selected and their basic operation. Chapter IV will provide a detailed discussion of the design and operation of the test hardware. Chapter V discusses the software involved to run the hardware, as well as the code for specific tests. Chapter VI presents conclusions, as well as potential future improvements and enhancements.

# II. THE LOW TEMPERATURE GALLIUM ARSENIDE RESEARCH PROGRAM

#### A. OVERVIEW

One of the most significant costs in developing systems to operate in the space environment is that of radiation hardening electronic components. These RAD hard ICs are specially engineered to a set of design rules that apply to a specific fabrication process. As a result of this additional engineering, special fabrication processes, and relatively low demand, RAD hard devices are typically 100 times more expensive that their commercial counterparts.

Some of the radiation effects of digital ICs include device degradation, latchup, and single event upsets. Degradation is caused by both the depositing of charge within the device and actual crystal lattice damage. Both will cause the device specifications to change and may eventually result in total failure. Latchup is a condition where a temporary short from power to ground is caused by the interaction between a transistor, a charged particle, and parasitic circuitry on the IC. If this does not destroy the device or power supply, the circuit may be powered down and restarted. A single-event upset is a condition where a particle passes through a transistor or memory element and causes the associated bit to flip, producing a data error. After this temporary data upset, the device will continue to function normally.[2]

To mitigate the effects of radiation, a number of technologies have been developed for complementary metal oxide silicon (CMOS) ICs which require the reengineering of commercial parts, as mentioned above. For high-speed applications gallium arsenide (GaAs) circuits have proven to be superior to emitter coupled logic (ECL) and bipolar complementary metal oxide silicon (BiCMOS) in resistance to degradation and latchup. However GaAs SEU rates are four to seven times greater than most Department of Defense (DoD) requirements. A great deal of research has been conducted at the Naval Postgraduate School and elsewhere to find a method of improving the SEU characteristics of GaAs. One such research effort is called Low Temperature Gallium Arsenide (LT GaAs), where a buffer layer of gallium arsenide is grown at low temperatures, around 200° C, as opposed to the 600°C that is typically used for gallium arsenide processes. It has been shown that this low-temperature buffer layer eliminates SEU effects in GaAs ICs. If successful, this process will allow specially prepared wafers to be run through

traditional GaAs processing steps with commercially developed mask sets. This will significantly reduce the cost of developing high-speed, low-power circuits for space-based applications.[3]

To this end, some LT GaAs wafers were run through commercial processes at both Vitesse and Motorola. Vitesse produced a 256 X 4 SRAM and Motorola produced a 256 X 16 SRAM, both with existing commercial mask sets. These two memories need to be tested for both functionality and resistance to single-event upsets. To this end, the design of a board capable of performing such tests is examined in this thesis. The following two sections detail the electrical characteristics and pin-outs of the LT GaAs chips to be tested.

#### B. VITESSE 256 X 4 SRAM

The Vitesse SRAM was produced with their commercial mask set and was packaged in a 28-pin dual flat pack. This SRAM operates in the 10 ns range and has separate data inputs and outputs. The overall interface includes 8 address, 4 data in, 4 data out, read, write, and two chip select pins, one active high and one active low. Vitesse no longer produces this SRAM as an off-the-shelf part and a third party package was needed to package the die, which is the reason for the somewhat unconventional pin-out of the package. Figure 1 shows the package pin out diagram of the Vitesse SRAM.

			L
1	DI2	D02	28
2	GND	Vtt1	27
3	DO1	DI3	26
4	DI1	DO3	25
5	Vtt1	GND	24
6	DO0	Vttl	23
7	DI0	CS2	22
8	A7	OE*	21
9	A6	CS1*	20
10	A5	GND	19
11	A0	WE*	18
12	A1	A4	17
13	A2	A3	16
14	Vtti	GND	15
			1

Figure 1: Vitesse 256 X 4 SRAM

#### C. MOTOROLA 256 X 16 SRAM

This SRAM mask set is part of a library for digital signal processing (DSP) IC development and does not have off-chip drivers, therefore requiring additional support circuitry. Input and output voltage levels are 0 and 0.9 to 2.0 volts. Thus, voltage reduction is required for

the inputs and amplification for the outputs. The voltage reduction can be accomplished using two diodes with a resistor, and the amplification can be performed with high-speed comparators. This interface circuitry is being developed by another student at the Naval Postgraduate School.

The interface of the chip, which drives the test setup on this board, consists of 8 address, 16 data in, 16 data out, write enable, and clock lines. There are also multiple power and ground connections for the clock buffers, output drivers, and memory elements. The manufacture's data sheet states that the address and write enable lines should be changed during clock low. On a clock high, the address is decoded and data is written if the write line is enabled, or read if the write line is low.

This chip is mounted in a 68-pin leaded chip carrier, again a third party package as this is not an off-the-shelf SRAM at Motorola. Figure 2 shows the pin outs of the 68-pin package.

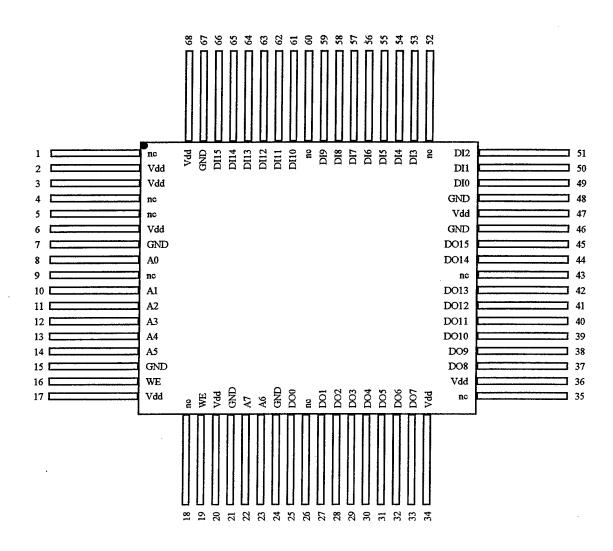


Figure 2: Motorola 256 X 16 SRAM

#### III. COMPONENT SUMMARY

#### A. OVERVIEW

The intent of this project was to design and build test hardware that would allow functional and radiation testing of a Vitesse 256 X 4 SRAM fabricated with the LT GaAs process. The test fixture is required to be portable and capable of interfacing to a laptop computer via a RS-232 serial port. The original considerations for designs were as follows:

RS-232 controlled logic

Microprocessor Based Design

Microcontroller Based Design

Using a single, RS-232 I/O port design would have required a number of registers to control the experiment. For the Vitesse chip, which is a 256x4 SRAM, two 8-bit registers would have been needed to control chip inputs (8 bits for address, 4 bits for data, and 4 bits for control signals CS1, CS2, Write Enable, and Output Enable), and a 4-bit register would have been required for reading data out. This design, although relatively simple, is very limited and only allows for testing of this specific chip. Furthermore, addressing all the registers would require additional hardware and operation would be very slow. To test a more complex chip, other circuitry must be added, and the software correspondingly changed. Ultimately, this design methodology was scrapped due to its limited utility.

The microprocessor-based design was considered, along with the microcontroller-based design, and it was determined that a microcontroller was more flexible and capable due to the built-in features of most microcontrollers, which usually include serial support, on-board ROM, and built-in I/O.

Once it was determined that a microcontroller-based design was to be used, the question of which microcontroller arose. Since one of the design considerations was to have a test fixture that could be used in a radiation environment, the choice was narrowed down to 3 or 4 options. Ultimately, the United Technologies UT69RH051 was chosen for its compatibility with the 8051 family of microcontrollers. The 8051 family has a wealth of development tools available, which greatly aided in the development of this system.

#### **B. SUMMARY OF VLSI COMPONENTS**

Based on the choice of the UT69RH051 as the controller for the design, the following components are required. Data sheets for the following components are available in Appendix C. The first part number is the RAD hard version and the number in parenthesis is the commercial version for each IC.

#### 1. UT69RH051 Microcontroller (i8051)

The UT69RH051 is a RAD Hard version of the Intel i8051 series of microcontrollers. This is a 40-pin device consisting of four 8-bit ports (ports 0-3), with additional pins for clock (XTAL1and XTAL2), address latch enable (ALE), program store enable (PSEN\*), external access enable (EA\*), and reset (RST). Port 0 is a multiplexed port providing both the lower byte of the address and the data byte. The ALE line is asserted when the low order address byte is on port 0. The PSEN\* serves as the read signal for the program memory space, while the EA\* is an input indicating whether to use internal ROM (not available on the UT69RH051) or an external ROM. The XTAL1 and XTAL2 lines are used to provide timing control. The XTAL1 input can be used alone if an oscillator is used to generate timing, otherwise both XTAL lines are used with a simple crystal and capacitor combination. Port 1 may be used for special purpose I/O. However, it is used here as a basic 8-bit I/O port. Port 2 provides the high-order address byte. Port 3 provides for general I/O control to include the read (RD\*) and write (WR\*) signals to memory and the serial transmit (TXD) and receive (RXD) lines to the RS-232 interface.

#### 2. MAX233

The MAX233 is a multi-channel RS-232 driver/receiver that converts serial data between 0 and +5 V (TTL) and ±10 V (RS-232). This chip has the added benefit of not requiring any additional power supply beyond the +5 V on which the chip and board operate. The only pins of interest are Tin, Tout, Rin, and Rout, which are the transmitter and receiver inputs and outputs. Other interface pins are tied together per the data sheet.

#### 3. HS-82C55ARH (82C55)

The HS-8255ARH is a general-purpose, programmable, I/O device with 24 I/O pins organized as ports A, B, and C. Ports A and B are 8-bit ports and can each be programmed as either byte input or byte output. Port C is divided into two 4-bit I/O groups, each of which can be programmed as input or output. The port C lines can be configured to be individually set or reset

in output mode, which aids in the simulation of control signals. For interfacing, chip select (CS\*), write (WR\*), read (RD\*), two address lines, and 8 data lines (D0-D7) are provided. A RESET pin is also provided to allow the 8255 to be started in a known program state. Lines A0 and A1 specify ports A, B, C, or control-word access.

#### 4. UT28F64 (AM2764A)

The UT28F64 is a RAD hard 8Kx8 PROM manufactured by United Technologies. This PROM will operate on 5 V and has an access time of 35ns. The interface pins are 13 address lines, 8 data lines, 3 control lines, power and ground. The three control lines are output enable (OE\*), which is essentially a read line, chip select (CE\*), and a programming line (PE\*), which is asserted during programming and held high during operation. The 2764 has one additional pin, Vpp (pin 1) which is used during programming and is tied high for operation.

#### 5. UT67164 (61C64)

This is an 8Kx8 RAD hard SRAM with a 55 ns access time. The UT67164 is also SEU hardened but is contained in a 600 mil package, as opposed the standard 300 mil used for standard SRAM's, as well as the 61C64 used on the prototype board. Interface pins are identical to the PROM with the omission of the program lines.

#### C. SUMMARY OF MSI COMPONENTS

#### 1. UT54ACS08 (74HC08)

The UT54ACS08 is a RAD hard version of a quad 2 input AND gate.

#### 2. UT54ACS138 (74HC138)

The UT54ACS138 is a RAD hard version of a 3-to-8 line decoder with three enable inputs, one active high, and 2 active low. When the proper input conditions are met, a single output line will go low indicating that it is selected, all other outputs remain high.

#### 3. UT54ACS245 (74HC245)

The UT54AC245 is a tri-state octal bus transceiver. It is RAD hard and has an 8-bit A bus, an 8-bit B bus, an enable line, and a direction control line. As with the other devices, if the enable line is inactive (high), both buses are in the high impedance state. If the enable is asserted, data is transmitted from the A to the B side if the direction input is high, otherwise data is sent from the B to the A side.

#### 4. HCS573MS (74HC573)

The HS573MS is an octal latch with tri-state outputs and is RAD hard. The 573 has a broadside configuration where all inputs are on one side and all outputs are on the other. The interface pins consist of 8 input bits and 8 output bits, as well as an output enable (OE\*) and a latch enable (LE). When output enable is not asserted (high), the outputs are in the high impedance state. When latch enable is high, the latch is transparent. When the latch enable is asserted, the input data at that moment is held on the outputs until the latch enable goes high again.

#### 5. HCS574MS (74HC574)

The HCS574MS is a RAD hard broadside octal D flip-flop with tri-state outputs. It has 8 input and 8 output pins, as well as an output enable (OE\*) and a clock (CP) pin. On a low-to-high transition of the clock line, data on the inputs is stored and available on the outputs until the next low-to-high transition (assuming outputs are enabled).

#### D. DIGITAL COMPONENT ELECTRICAL REQUIREMENTS

The majority of electrical components are available in both CMOS and TTL compatible versions. For driving external components, HCT (high speed CMOS supporting TTL I/O levels) components are used, otherwise HC (high speed CMOS) components are used. Port 0 of the 8051 is capable of driving 4 TTL loads or a virtually unlimited number of CMOS loads (as the typical CMOS load draws an order of magnitude less current than TTL loads). The remainder of the 8051 ports will sink 3.5mA or source 0.3 mA, which is more than sufficient to drive 10 CMOS loads. The bus transceivers at the outputs of the XX245 will sink and source 12mA, which is sufficient to drive virtually any device to be tested. The outputs of the 8255 will sink and source 2mA, which is sufficient to drive most control lines. Further interface limitations will be discussed in Chapter V. A summary of the output currents of the devices used are shown in Table 1.

Communicati	In this said	10000
8051 Port 0	-7.0	7.0
8051 Port 1,2,3	-0.3	3.5
MAX232/233	-1.0	3.2
HS-82C55ARH	-2.0	2.0
UT28F64	4	4.0
UT67164	4	4.0
UT54ACS08	-8.0	8.0
UT54ACS10	-8.0	8.0
UT54ACS138	-8.0	8.0
UT54ACS139	-8.0	8.0
UT54ACS245	-12.0	12.0
HC573MS	-7.2	7.2
HC574MS	-7.2	7.2

**Table 1: Summary Of Component Pin Currents** 

#### E. DISCRETE COMPONENTS

#### 1. Crystal Oscillator

A crystal oscillator with a frequency of 7.3728 MHz was used to provide timing input to the microcontroller. This seemingly odd frequency aids in ensuring the baud rates on the serial port fall within standard ranges such as 4800, 9600, etc. The microcontroller will run on any frequency from 2 - 20 MHz.

#### 2. Capacitors

#### a. $10 \mu F$

A 10  $\mu$ F capacitor is used in conjunction with a resistor to generate a time delay for the reset line of 8051 and 8255 on power-up. This value is recommended in the data sheets.

#### b. $1\mu F$

Four, 1  $\mu$ F capacitors are used with the MAX232 to provide  $\pm 10$  V DC using the charge pump circuitry built into the device. These will not be required on the production board as the MAX233 will be used, which does not require external capacitors.

#### c. $.1\mu F$

These capacitors are used for decoupling, that is providing a momentary source of current when ICs switch, providing voltage stability.

#### 3. Resistors

A  $8.2K\Omega$  resistor is used in conjunction with a capacitor to provide a time delay for the reset line of both the 8051 and the 8255 on power-up. This ensures the board starts in a known state, and is recommended on the data sheets.

#### F. CONNECTORS

#### 1. 40 Pin Header

Four, 40-pin headers are used to provide an interface with the device to be tested. The pins are set up in a 2 X 20 grid with 100 mil spacing.

#### 2. 25-pin sub-D

A 25-pin, sub-D, male connector is used to interface the board with a standard serial RS-232 port of a laptop computer.

#### IV. DESIGN ANALYSIS

#### A. OVERVIEW

A detailed description of the universal test platform's design and operation is provided in this section. The goal is to provide a stand-alone document that fully explains the wiring and operation of each section of the design.

#### **B. SERIAL INTERFACE**

The first task was to create an interface with the outside world using a RS-232 serial interface. The actual serial connection itself was rather easy in that this basic function was built into the microcontroller. The key part of this interface was to convert the TTL-level serial signals to the RS-232 levels. This could have been accomplished using one of the two major families of RS-232 drivers. The first is the 1488/1489 line driver/receiver combination. Both 148X ICs require ±12 V, which is not required elsewhere in this design. This choice also requires two IC packages, whereas the MAX232/233 family requires only one.

As this is a relatively simple serial connection, with only a transmit line(TXD) and a receive line(RXD), only one line driver and receiver are required. Maxim makes a family of line drivers and receivers on the same chip with the added benefit of requiring only a +5 V supply, instead of the ±12 V that is typically required of line drivers. This family of chips uses a technique called *dual charge-pump voltage conversion*, which uses capacitors to generate the ±10 V required for the RS-232 line drivers. The two devices used in this research are the MAX232, which use external capacitors, and the MAX233, which has internal capacitors and therefore requires less board space. The MAX232 was used on the wire wrapped board, primarily because of its availability early in the design process. For the production board, the MAX233 is used.

#### 1. MAX232

The MAX232 requires four external 1  $\mu$ F capacitors, as well as power and ground for support circuitry. The functional portion of the MAX232 contains two line drivers and two line receivers, of which one each is used. The wiring diagram for the MAX232 is shown in Figure 3.

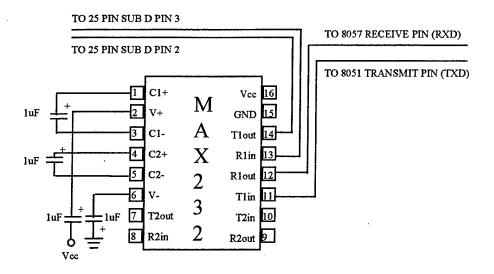


Figure 3: MAX232

#### 2. MAX233

The MAX233 is an improvement upon the MAX232 in that it requires only +5 V and ground, with no external capacitor requirement. It also contains two line drivers and two line receivers and is wired as shown in Figure 4.

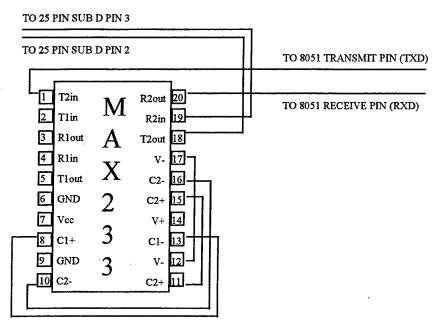


Figure 4: MAX233

#### 3. Serial connector

The output of the line driver and the input of the line receiver are wired to a standard, male, 25-pin, sub-D connector, as shown below in Figure 5. The line driver output is connected to pin 3 of the connector (received data for DTE in the RS-232 standard), and the line receiver is connected to pin 2 of the connector (transmitted data). Pin 7 (signal ground) is connected to ground.

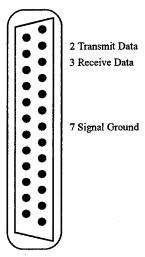


Figure 5: RS-232 Connector (minimal)

#### 4. Overall Serial Subsystem

The input of the line driver is connected to the serial transmit (TXD) line of the microcontroller and the line receiver output is connected to the serial receive (RXD) line of the microcontroller. The MAX23X receive data in (Rin) and transmit data out (Tout) are wired in accordance with the RS-232 standard, as shown above. The complete communications subsystem is shown in Figure 6.

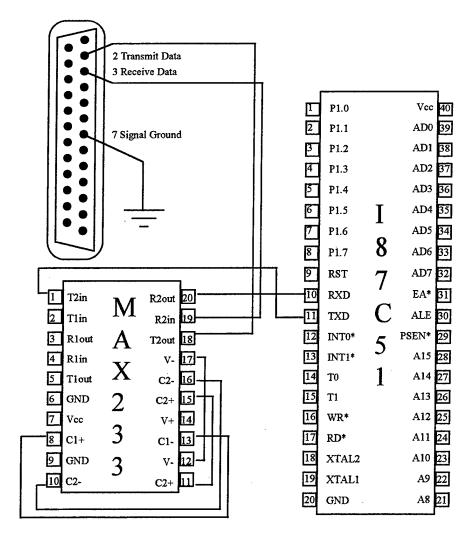


Figure 6: Complete Serial Subsystem

#### C. TIMING GENERATION

The timing generation for this system can use one of two methods, depending upon what the desired timing source is. The two choices are to use a crystal or a R/C oscillator. The difference is accuracy versus complexity and both have been used in developing the prototype board. The R/C oscillator was dismissed because it is not stable enough for serial-line baud-rate generation. When the R/C oscillator is used, the output is wired to pin 19 (XTAL1) of the microcontroller.

When a crystal is used, two additional capacitors are required, providing parallel resonance for the fundamental response mode of the crystal. When this configuration is used, the crystal is wired to pins 18 and 19 (XTAL2 and XTAL1) of the microcontroller and both pins are

grounded through capacitors, as shown in Figure 7. This method was chosen because of its simplicity and the relative tolerance crystals and capacitors show to radiation effects.

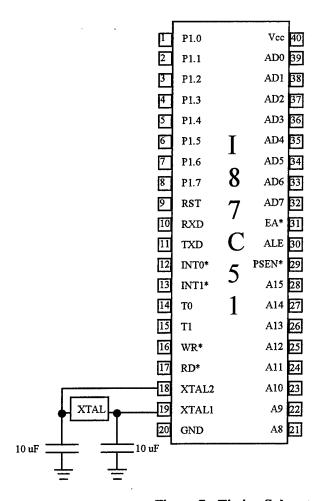


Figure 7: Timing Subsystem

#### D. MEMORY INTERFACE

#### 1. Overview

The memory subsystem is also relatively straight forward, the most difficult part of which is latching the low order address-byte so it is available while the data-byte is on the output port. The memory space is divided into eight, 8K blocks within the 64K memory space. The basic memory layout is shown in Table 2.

MEMORY LOCATIONS	USE
0000H-1FFFH	ROM SPACE
2000H-3FFFH	RAM I SPACE
4000-5FFFH	RAM 2 SPACE (PRODUCTION BOARD)
6000-7FFFH	BOARD CONTROL SPACE
8000-9FFFH	TEST SPACE 1
A000-BFFFH	TEST SPACE 2
C000-DFFFH	TEST SPACE 3
E000-FFFFH	TEST SPACE 4

Table 2: Memory Map

#### 2. XX573

Port 0 of the 8051 is multiplexed and used for both the low-order address byte and the data byte to be written or read. Therefore, the address byte must be stored and held for use during the memory access cycle. This is accomplished easily with either a XX373 or XX573 latch. The XX573 was chosen for its broadside configuration, where all input pins are on one side of the package and all output pins are on the opposite side of the package. This makes it easier for both wire wrapping and printed circuit board production, where it is desirable to keep trace and wire lengths to a minimum.

The support pins on this chip are straight forward: power, ground, output enable (OE\*), and latch enable (LE\*). The output enable was wired low, allowing the address to always be available after latching. The latch enable line is wired to the address latch enable (ALE\*) line of the microcontroller, an obvious choice.

#### 3. XX138

The XX138 is used to partition the 64K address space into eight, 8K blocks. The support pins are: power, ground, and 3 enable lines. In this design, all enable lines are asserted, allowing the selected partition to be active as long as the upper three address bits indicate that partition.

#### 4. XX08

The XX08 is used to combine the program store enable (PSEN\*) and read (RD\*) lines. This is a recommendation in many application notes [4,5] and allows the RAM to be used as both program and data memory. This facilitates the downloading of code into the RAM, which can then be run as a program. This eliminates the need to program a PROM every time a change is made in a program and allows for easy code modification with a simple monitor program. The complete memory interface is shown in Figure 8.

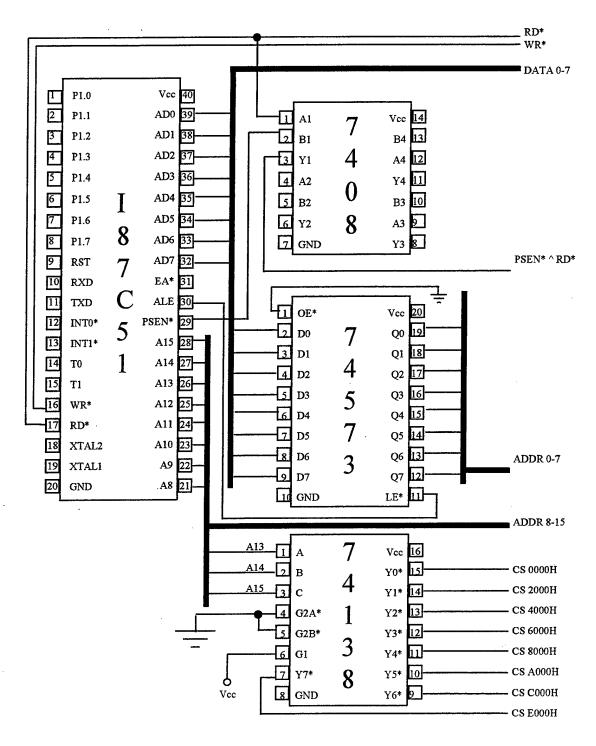


Figure 8: Memory Interface

#### E. MEMORY

#### 1. PROM (UT28F64)

The PROM interface is very straight forward. The data lines are wired directly to port 0 of the microcontroller. The low-order byte of the address is latched by the XX573, therefore address lines 0-7 are wired to the latch. The 5 high-order address bits are wired to the microcontroller address lines on port 2. The remaining pins to be interfaced are the chip select (CS\*), read (RD\*), program (PGM), and program voltage (Vpp) lines. The PROM is designed to occupy the first 8K partition of the memory space and is therefore wired to the Y0 output of the XX138. The read line could be wired to either the read (RD\*) line of the microcontroller or to the output of the XX08. Here, the output of the XX08 was chosen to minimize the lines wired directly to the microcontroller. The program and program voltage lines are wired high, as this design does not provide for programming the PROM. The PROM interface is shown in Figure 9.

#### 2. SRAM (UT67164)

The SRAM interface is very similar to that of the PROM. The four support pins are the read (RD\*), write (WR\*), chip select 1 (CS1\*), and chip select 2 (CS2) lines. The write line is wired directly to the microcontroller and the read line is wired to the XX08 to allow the SRAM to act as both program and data memory space. The chip select 1 line is wired to the Y1 output to configure the SRAM as the second 8K partition. The chip select 2 line is not needed and is, therefore, wired high to allow only the chip select 1 line to activate the SRAM. The address and data lines are wired the same as for the PROM. Only one 8K SRAM is implemented on the prototype board. The basic interface is shown in Figure 9.

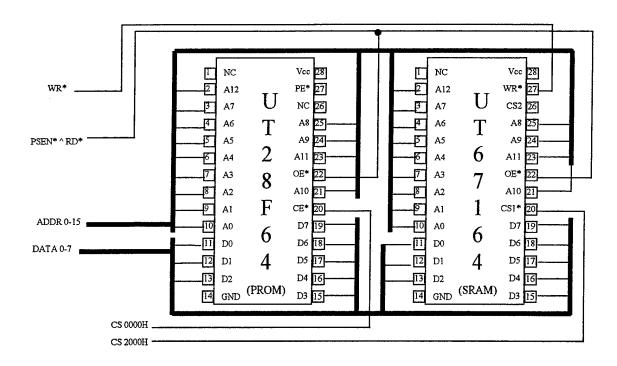


Figure 9: Memory Subsystem

#### F. PERIPHERAL INTERFACE

This section provides for additional I/O to interface with the device to be tested. Table 3 shows the memory map of the peripheral interface control space.

MEMORALIONATIO	V IS
6000-6003H	8255 #1
6007-6007H	8255 #2
6008-600BH	8255 #3
600C-600FH	8255 #4
6010H	LATCHED BYTE 0
6014H	LATCHED BYTE 1
6018H	LATCHED BYTE 2
601CH	LATCHED BYTE 3

Table 3: Peripheral Memory Map

#### 1. XX138

The XX138 is used to further subdivide the lower 32 bits of memory partition 3 (6000H-7FFFH) into 4-bit units. This is done to keep all the control board control functions within partition 3, allowing a 32K memory space for the device under test. The control inputs to this device are three address lines and three enable lines. The address lines are wired to address bits 2 to 4 of the XX573 latch, creating eight, 4-bit blocks. These blocks repeat every 32 addresses within memory partition 3 (6000H-7FFFH). The additional circuitry required to fully decode this address space is not implemented in this design.

#### 2. 8255

The 8255 interface methodology is similar to that of a simple RAM. There is an 8-bit data bus and a 2-bit address bus along with read (RD\*), write (WR\*), chip select (CS\*), and reset (RESET) lines. The data byte is wired to the microcontroller data bus, while the two address lines are wired to the lowest 2 bits on the memory-interface XX573 latch. The read, write and reset lines are all wired directly to their counterparts on the microcontroller. The remaining line to be interfaced is the chip select, which is controlled by the output of the XX138 that selects which 8255 is to be addressed. The first four outputs of the XX138 (Y0-Y3) select one of the four 8255s on the production board, or one of the two 8522s on the wire-wrapped board. The 8255s I/O interface has a total of 24 bits, which is arranged as three 8-bit ports. The address pins(A0,A1) select between ports A, B, C, and the control word. The three I/O ports are wired to the 40-pin connectors, allowing for control of the device to be tested. The 8255 interface is show in Figure 10.

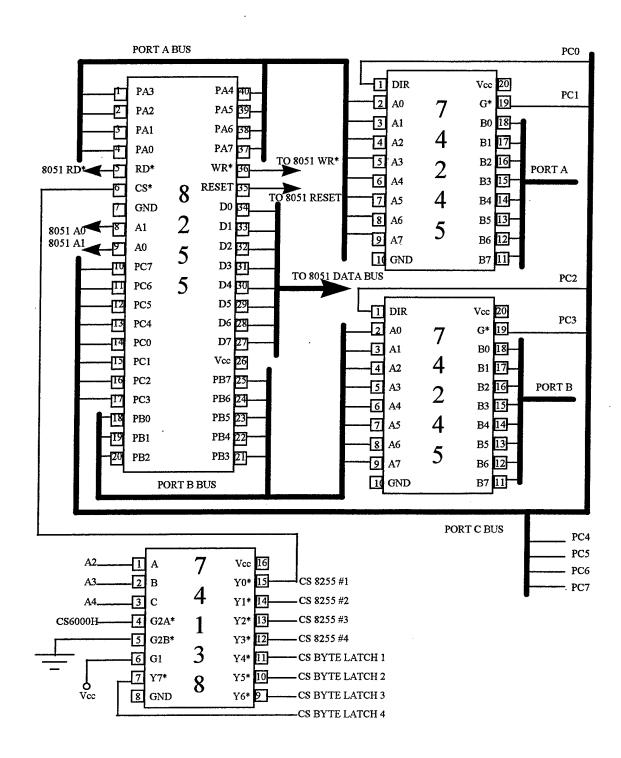


Figure 10: 8255 Interface

#### G. LATCHING / READING 32 BITS

To allow this device to test other ICs with data buses wider than 8 bits, a technique had to be developed to allow an eight-bit microcontroller to read multiple bytes. The method used here latches up to 32 bits of data, then reads the values a byte at a time from the control space.

#### 1. XX574

The purpose of the XX574 used here is two fold, it allows for latching the data as well as acting as a tri-state buffer. The XX574 flip-flop was chosen because storage is desired on transitions, not simply on levels, as with the XX573 latch. The control lines of the XX574 consist of an output enable (OE\*) and a clock input (CLK). When the CLK signal transitions from low to high, the data on the inputs is stored in the flip flops. The logic to control the clock line is discussed below. When a control space read is initiated, the output enable is activated and the stored data appears on the data bus.

#### 2. XX08

The XX08 provides the input clock to the flip-flops when a specific set of circumstances is present, mainly when A15 is high and the read line transitions from low to high.

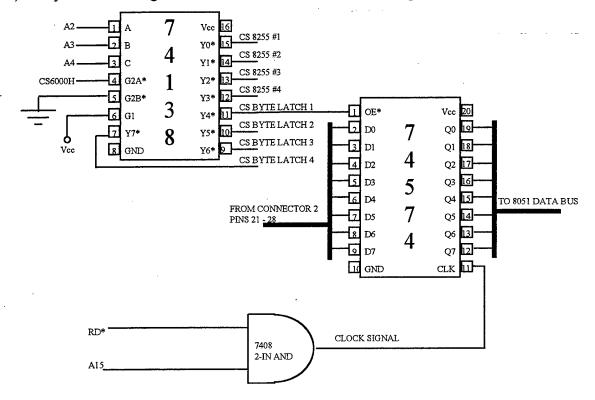


Figure 11: Byte Latch Circuitry

#### 3. Word latch

To read 32 bits, all data bits of the device under test are stored at one time and are then read a byte at a time as part of the control space. A read from the test data space (upper 32K) will cause 32 bits of data to be clocked into the XX574s (16 bits on the prototype board). These bytes can then be read as part of the control space at addresses 6010H, 6014H, 6018H, and 601CH, as determined by the XX138 described in the peripheral interface section.

#### H. RESET

The reset circuitry is relatively straight forward, a switch with a capacitor and resistor to provide an appropriate delay, as specified in the applications notes. A diagram of this circuit is shown in Figure 12.

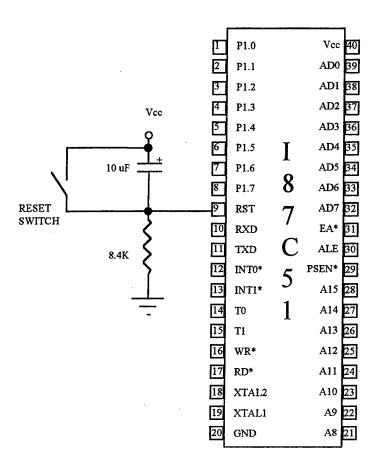


Figure 12: Reset Circuit

#### I. EXTERNAL CONNECTORS

#### 1. RS-232

The connection to the outside world is through a 25-pin, sub-D, male connector, which is compatible with most standard computer serial interfaces. There are only three pins used, thus the protocol is fairly simple. Pin 7 is used for signal ground and pins 2 and 3 are used for transmit data and receive data, respectively.

#### 2. Test Interface

The external connectors are 40-pin dip headers which are broken down by functionality. Connector 1 is the microcontroller bus interface. Connectors 2 and 3 each contain 16 bits of programmable I/O and a 16-bit latch capability, as well as 4 control bits. Connector 4 provides 32 bits of programmable I/O and some additional bit control lines.

#### a. connector 1

Connector 1 contains all the necessary lines to connect a device with an address space of up to 32Kb and an 8-bit data word. Also provided are 8 bits that can be programmed as an input or output byte. The specific signals include 16 address bits, 8 data bits, 8 I/O bits, and 4 chip selects, along with read, write, power and ground. Table 4 shows the specific pin arrangements. This connector is fully implemented on the prototype board. All signals use TTL levels and will drive TTL loads.

#### b. connector 2

Connector 2 contains two bytes that may be configured as either input or output, as well as two bytes capable of being latched by the control board. Also provided is a group of 4 bits that can be individually set and cleared, or serve as a 4-bit I/O port. The details are shown in Table 5 and are fully implemented on the prototype board.

#### c. connector 3

Connector 3 is designed to be implemented on the production board and is not on the prototype board. These signals are similar to what is provided on connector 2 and makes it possible to test a 32-bit memory device. The details are shown in Table 6.

PLS.	RENORMAN	PIN	EHNOHON
1	DATA 0	21	ADDRESS 0
2	DATA 1	22	ADDRESS 1
3	DATA 2	23	ADDRESS 2
4	DATA 3	24	ADDRESS 3
5	DATA 4	25	ADDRESS 4
6	DATA 5	26	ADDRESS 5
7	DATA 6	27	ADDRESS 6
8	DATA 7	28	ADDRESS 7
9	POWER (+5V DC)	29	GROUND
10	I/O 0 (FROM PORT 1)	30	ADDRESS 8
11	I/O 1	31	ADDRESS 9
12	I/O 2	32	ADDRESS 10
13	I/O 3	33	ADDRESS 11
14	I/O 4	34	ADDRESS 12
15	I/O 5	35	ADDRESS 13
16	I/O 6	36	ADDRESS 14
17	I/O 7	37	ADDRESS 15
18	CS A000-BFFFh	38	READ*
19	CS C000-DFFFh	39	WRITE*
20	CS E000-FFFFh	40	CS 8000-9FFFh

Table 4: Connector 1

PIN	FIINCHION	PIN	FUNCTION
1	8255 #1 PORT A 1/0 0	21	T/S DATA IN 0
2	I/O 1	22	T/S DATA IN 1
3	I/O 2	23	T/S DATA IN 2
4	I/O 3	24	T/S DATA IN 3
5	I/O 4	25	T/S DATA IN 4
6	I/O 5	26	T/S DATA IN 5
7	I/O 6	27	T/S DATA IN 6
8	I/O 7	28	T/S DATA IN 7
9	8255 #1 PORT B I/O 0	29	T/S DATA IN 8
10	. I/O 1	30	T/S DATA IN 9
11	I/O 2	31	T/S DATA IN 10
12	I/O 3	32	T/S DATA IN 11
13	I/O 4	33	T/S DATA IN 12
14	I/O 5	34	T/S DATA IN 13
15	I/O 6	35	T/S DATA IN 14
16	I/O 7	36	T/S DATA IN 15
17	8255 #1 PORT C I/O 4	37	
18	I/O 5	38	
19	I/O 6	39	
20	I/O 7	40	

Table 5: Connector 2

#### d. connector 4

Connector 4 is designed to be implemented on the production board and is not on the prototype board. These signals provide additional I/O lines that may be used to drive a 32-bit address bus on larger devices being tested. Details are shown in Table 7.

#### J. TIMING ANALYSIS

The overall timing of components for this design is straight forward, as all timing is synchronous. Analyzing the memory timing constrains of the 8051 shows that time from a read low to data valid must be within the limits of Equation 4.1.

$$t_{RLDV} = 5t_{CLCL} - 165ns$$
 Equation 4.1

Here  $t_{CLCL}$  is the clock period low transition to low transition. Operating the 8051 at a maximum clock rate of 20MHz,  $t_{CLCL}$  is 50ns and  $t_{RLDV}$  is 85 ns. For the read and write pulse widths, Equations 4.2 and 4.3 apply.

$$t_{RLRH} = 6t_{CLCL} - 100ns$$
 Equation 4.2  
 $t_{WLWH} = 6t_{CLCL} - 100ns$  Equation 4.3

The pulse widths for the read and write signals are 200 ns when the 8051 is operating at 20MHz. When operation is slowed down to 7.3728, the  $t_{\rm CLCL}$  drops to 136 ns, yielding a  $t_{\rm RLDV}$  of 513ns and a read/write pulse width of 716 ns. The RAD hard memory components have access times of 35 ns or less, allowing operation of this design at the 8051 maximum data rate.

The 8255 requires a read pulse width of 250 ns and has a 200 ns maximum requirement for data valid from read asserted. On writes, the 8255 requires only 100 ns, which falls well within the maximum speed of this design. Taking these 8255 read and write constraints into consideration, if only output functions are being utilized, a 20MHz clock may be used. However, if input from the 8255 is desired, the speed must be slowed down to 17 MHz.

PIN	HINGHON	PIN	FUNCTION
1	8255 #2 PORT A I/0 0	21	T/S DATA IN 17
2	I/O 1	22	T/S DATA IN 18
3	. I/O 2	23	T/S DATA IN 19
4	I/O 3	24	T/S DATA IN 20
5	I/O 4	25	T/S DATA IN 21
6	I/O 5	26	T/S DATA IN 22
7	I/O 6	27	T/S DATA IN 23
8	I/O 7	. 28	T/S DATA IN 24
9	8255 #2 PORT B I/O 0	29	T/S DATA IN 25
10	I/O 1	30	T/S DATA IN 26
11	I/O 2	31	T/S DATA IN 27
12	I/O 3	32	T/S DATA IN 28
13	I/O 4	33	T/S DATA IN 29
14	I/O 5	34	T/S DATA IN 30
15	I/O 6	35	T/S DATA IN 31
16	I/O 7	36	T/S DATA IN 32
17	8255 #2 PORT C I/O 4	37	
18	I/O 5	38	
19	I/O 6	39	}
20	. I/O 7	40	

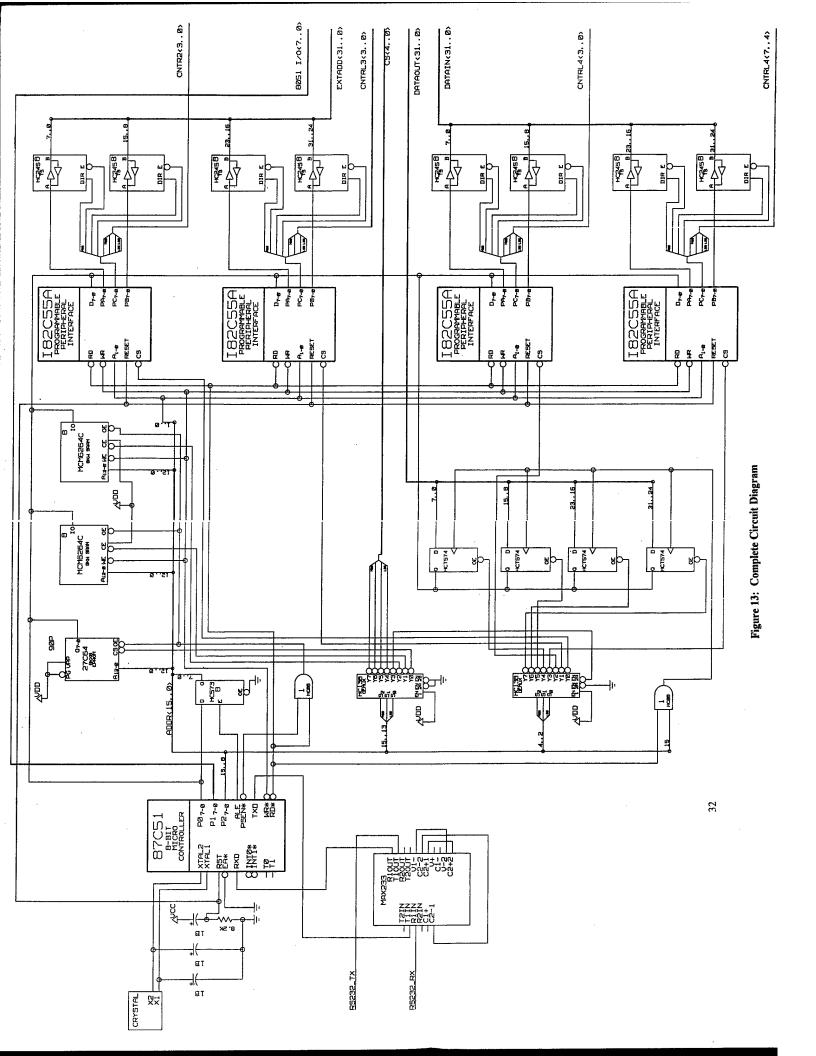
Table 6: Connector 3

PIN	FUNCTION	PIN	E E E CONTROL
1	8255 #3 PORT A I/0 0	21	8255 #4 PORT A I/0 0
2	I/O 1	22	I/O 1
3	. I/O 2	23	I/O 2
4	I/O 3	24	I/O 3
5	I/O 4	25	I/O 4
6	I/O 5	26	I/O 5
7	I/O 6	27	I/O 6
8	I/O 7	28	I/O 7
9	8255 #3 PORT B I/O 0	29	8255 #4 PORT B I/O 0
10	I/O 1	30	I/O 1
11	I/O 2	31	I/O 2
12	I/O 3	32	I/O 3
13	I/O 4	33	I/O 4
14	I/O 5	34	I/O 5
15	I/O 6	35	I/O 6
16	I/O 7	36	I/O 7
17	8255 #3 PORT C I/O 4	37	8255 #4 PORT C I/O 4
18	I/O 5	38	I/O 5
19	I/O 6	39	I/O 6
20	I/O 7	40	I/O 7

Table 7: Connector 4

### K. COMPLETE DESIGN DIAGRAM

Figure 13 shows the complete layout of this board design. Decoupling capacitors are omitted, as well as the specific connector layout, which is available elsewhere in this document.



#### V. PROGRAMMING

#### A. OVERVIEW

In order to use the test hardware to test IC devices, a test program must be written, the board configured, and a test fixture created. This chapter will deal with all of these requirements, as well as describing some of the specific tests that the hardware will run.

#### **B. BOARD CONFIGURATION**

This process consists of determining which parts of the board are to be utilized and then writing a configuration routine to set up the appropriate parameters. This initialization may be run separately or incorporated as part of the actual test program. The simplest initialization program is actually no program at all. When the board is initialized, the 8255 ports are configured as inputs and the 8051 bus is fully accessible. Any simple memory device with 8 data bits and up to 32K of address space can be connected directly to the microcontroller bus (available on connector 1) with no additional setup requirements.

The 8255 will operate in one of three basic modes, byte input, byte output, and bit-set mode. As mentioned before, for byte input mode, the data simply needs to be read from the appropriate address, as shown below in Table 8.

MEMORA EGRATION	ISB	HENTORA GLASSION	ESE
6000H	PORT A 8255 #1	600AH	PORT C 8255 #3
6001H	PORT B 8255 #1	600BH	8255 #3 CONTROL WORD
6002H	PORT C 8255 #1	600CH	PORT A 8255 #4
6003H	8255 #1 CONTROL WORD	600DH	PORT B 8255 #4
6004H	PORT A 8255 #2	600EH	PORT C 8255 #4
6005H	PORT B 8255 #2	600FH	8255 #4 CONTROL WORD
6006H	PORT C 8255 #2	6010H	LATCHED BYTE 0
6007H	8255 #2 CONTROL WORD	6014H	LATCHED BYTE 1
6008H	PORT A 8255 #3	6018H	LATCHED BYTE 2
6009Н	PORT B 8255 #3	601CH	LATCHED BYTE 3

Table 8: Memory Map

To set up the I/O mode, the appropriate byte must be written to the 8255 control word. The most common I/O type, mode 0, performs basic byte input and output. The layout of the control word is shown in Figure 14. To set up port A as output, bit 7 must be set, bits 5 and 6 need to be 00 for Mode 0, and bit 4 needs to be 0 for output. Hence, to set up the #1 8255 port A for output mode, write 1000xxxxB (here x is don't care, and B is binary) to address 6003H. Then, it is simply a matter of writing the data byte that is to be put on port A to address 6000H. Port C is broken into an upper half and a lower half and each half can be independently set for input or output. To set up the lower half of port C for output, control bit 7 must be set, bit 2 should be cleared, and bit 0 should be cleared. Hence, a control word of 1xxxx0x0B should be written to the control register. Of course, it should be noted that if ports A and C are to both be used, the control words must be combined yielding a control word of 1000x0x0B.

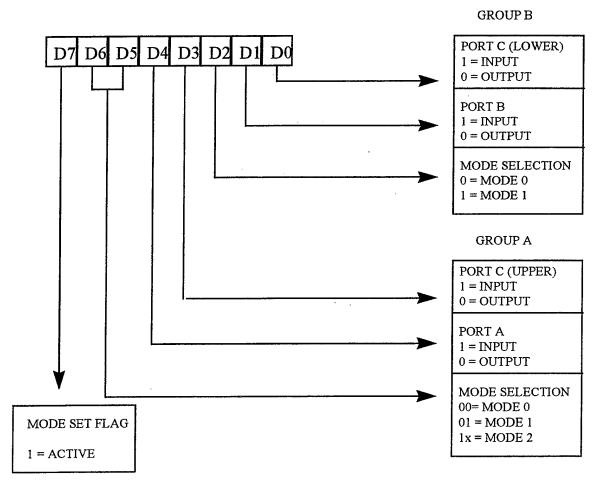


Figure 14: 8255 Control Word

#### C. ENABLING TRANCEIVERS

Once the modes of the 8255 ports are configured, the bus transceivers must be enabled and configured for the proper directions. Table 9 shows which bits of the upper C port control which transceiver functions

Port C 5it	Function
bit 7	Port A direction ( 0 = input, 1 = output
bit 6	Port A enable ( 0 = enabled)
bit 5	Port B direction (0 = input, 1=output)
bit 4	Port B enable (0 = enabled)

**Table 9: Transceiver Enables** 

To set up Port A as output, bit 7 must be set and bit 6 must be cleared, yielding a control word of 10xxxxxx. To set up Port B as input, bits 4 and 5 must be cleared. The combined control word for output on Port A and input on Port B is 1000xxxxB. It should be noted the lower half of Port C is available as a 4-bit input or output port.

#### D. PROGRAMMING

In order to actually perform tests, a program must be written. This program is written in 8051 assembly language and must be debugged, compiled, and loaded as with any assembly language program. The assembler used for this work is a shareware version called A51. Once the program is written, it must be loaded onto the test board by either RAM download or PROM program. The actual 'operating system' of this board is a monitor program called PAULMON, which was developed at Oregon State University. On top of this monitor is a front-end that will run any of the test routines written as part of this research, as well as provide instruction on how to download additional programs. The monitor occupies address space from 0000H-0FFFH in its basic form and occupies through 1FFFH if disassembler and debugger options are used. The monitor provides functions for serial I/O as well as memory editing, program downloading, and memory dumping. A listing of built-in functions is shown in Appendix A.

The easiest way to load a program is to download it via the RS-232 serial port and then run it from the monitor. For this method, address 2000H starts the RAM area. A complete description of the process is detailed below in the Vitesse section.

#### E. TEST DEVICE INTERFACE

Once the board is set up and the program is functioning, the device to be tested must be interfaced with the board. For each device to be tested, a separate test fixture must be built to interface with the test hardware connectors. For most applications, two, 40-conductor ribbon cables will carry the signals to the test fixture of the device under tested. Typically, only a socket and two 40-pin headers are required. This method was chosen for maximum flexibility, as there are so many package types and many different power configurations per package.

#### F. VITESSE

The setup for the Vitesse SRAM is very simple. It must be connected to the microcontroller bus, therefore requiring only connector 1. The layout of the IC is 8 address lines, 4 data in lines, 4 data out lines, and the usual read, write, and chip-select lines. Only the active-low enable line is used, therefore the active-high chip select line is tied high. The address lines are wired to the address 0-7 lines on connector 1, along with the read, write, and one of the chip-select lines (the 8000H line was used here). The only remaining lines are the data lines, of which it was decided to wire the inputs to data 0-3 and the outputs to data 4-7.

The program is relatively straight forward, simply write a fixed value to addresses 8000H-80FFH and then read the values back. The only small glitch in this procedure is that the data read must be ANDed with F0H before a comparison is made. The assembly language follows:

- ; Written by Duane Amsler as part of masters thesis
- ; the following program writes a value of 55H to memory locations 8000H-80FFH and then
- reads back the data in those locations. The read data is then masked with F0H to disregard
- ; the lower 4 bits, as this program is designed to test a 4-bit memory device

; initial assignments to allow output of memory locations and ASCII data

.equ Cout, 0x0030 ;Send Acc to serial port

.equ pHex16, 0x0036 ;Print Hex value of DPTR

.ORG H'2000	; start this program within the RAM space at 2000H
mov dptr, #h'3000 mov a,h'55 loopd1: movx @dptr,a inc dpt mov r7,dpl cjne r7,#0,loopd1	; set up test address to start at 8000H : us a value of 55H (01010101B) as a test pattern ; move accumulator to memory at data pointer (dptr) ; increment the data pointer ; move the lower half of the data pointer to register 7 ; if the data pointer lower byte is not 0, continue
ret	; return
.ORG H'2100	; start this program within the RAM space at 2100H
read: mov dptr,#h'8000 loopr1: movx a,@dptr anl a,#h'F0 cjne a,#h'05,error inc dptr mov r7,dpl cjne r7,#0,loopr1 ret	; start reading data from address 8000H; load the data at data pointer to the accumulator; mask out the lower 4 bits; if the value is x5, continue, else jump to error; increment the data pointer; move the lower data pointer byte to register 7; if lower data pointer is 00 exit, else continue; return to the calling program
mov a,#'' lcall cout lcall cout lcall phex16  mov a,#h'55 movx @dptr,a ajmp loopr1	: if error, call cout (will print the accumulator value, : which will not be x5H if error was called) ; load accumulator with ASCII value for space ; output the space in the accumulator ; output the value of the data pointer ( the location where ; the error occurred ; move 55 into the accumulator ; store 55 in the location where the error occurred ; jump back to the check loop

The above program was tested in RAM at location 3000H. The first routine was run from the monitor and then values written were verified by a memory dump. After the correct data was verified, a memory location was edited to a different value and the second routine was run. The value was correctly detected, corrected, and output to the laptop via the serial port.

#### VI. CONCLUSIONS

#### A. DESIGN CONCLUSIONS

The overall design of the test hardware was fairly straight forward, although designing to test up to a 32-bit device with an 8-bit microcontroller was rather challenging. The basic memory layout is widely used in applications notes and required some modification. The latching and shifting circuitry is original and may not be the most optimal solution, which will allow for future scrutiny and possible optimization of this work. It may be possible to program the 8255s to latch and hold. However, this will require additional configuration lines, which may be implemented as DIP switches, outputs from the 8051, or 8255 outputs.

#### **B. BOARD FABRICATION**

The board design is laid out in the CADENCE design tool CONCEPT, and can be converted into a GERBER file for fabrication. This will provide a reliable board that is much more elegant than the prototype board that was wire-wrapped.

#### C. COMPONENT COST

The RAD hard parts are very expensive and will require a fair amount of funding to purchase. The United Technologies VLSI parts range from \$1500-\$1900, while their commercial counterparts range from \$3-\$20. The United Technologies MSI RAD hard logic devices are all \$166, as opposed to the commercial MSI component costs of less than a dollar.

#### D. PROGRAMMING & TESTING

The initial attempt to test a Vitesse SRAM caused the microcontroller bus to fail. This may be the result of heavy loading of the bus by the part, or a faulty part. The next test will be to isolate the SRAM from the microcontroller bus and perform the tests under manual control of the 8255s. This will require the control lines be simulated with the bit set and clear capabilities of port C of the 8255. This work is ongoing.

#### E. FOLLOW-ON WORK

There are a few areas that may allow significant follow-on work. The most obvious is actually testing the LT GaAs experimental chips, as well as this board, in a radiation environment.

#### 1. Produce Professional PC Board

To improve upon system reliability and robustness, a commercially-produced PC board should be considered to both increase capabilities to 32 bits, as well as provide an aesthetically pleasing package for transport to radiation test sites.

#### 2. Use RAD Hard components

The intent of this design was to create a unit capable of testing ICs in a radiation environment. In its current configuration (with commercial parts), lead bricks must be set up around this board to shield it from radiation. This method will work, but is far from the optimal solution.

#### 3. ECC on Serial Link

The serial link currently uses a MAX233, which has no RAD hard counterparts. The 1488/1489 family also has no RAD hard counterpart. Because of this, some sort of error correcting code should be used on the RS-232 serial link. This will ensure proper data is obtained on tests. Something simple, such as a parity bit, possibly with check summing and retransmission, could be used. Further research is warranted.

#### 4. Use of a C Compiler

To aid in the development of test programs, a high-level language could be used. Although assembly language is still useful, the use of C will aid in increasing program complexity and program development speed.

#### 5. Creating a Script Language

Instead of another high-level language such as C, a scripting language could be developed to create an intuitive method for programming tests.

#### F. SUMMARY

This overall design was a valuable learning tool and should provide some functionality and utility in the future. This research should serve as a good starting point for improved designs, as well as an example of good, general-purpose test hardware.

#### LIST OF REFERENCES

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- 2. Wertz and Larson, Space Mission Analysis and Design, Kluwer Academic Publishers, Norwell, MA, 1991.
- 3. Todd R. Weatherford, Paul W. Marshall, Cheryl Dale, Andrew Peczalski, S. Baier, Dale McMorrow, Mark Twigg, and Arthur B. Campbell, "Soft Error Immune LT GaAs ICs", paper to be presented at the 18th Annual IEEE Gallium Arsenide Integrated Circuits Conference, Orlando, FL, November 3 6, 1996.
- 4. Greg Goodhue, "RAM loader program for 80C51 applications," Phillips Semiconductors Application Note AN440, June, 1993.
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#### APPENDIX A. PAULMON DOCUMENTAION

The following is the documentation file for PAULMON, and although it is a bit rough, it does contain a wealth of valuable information.

#### Introduction:

The PAULMON debugger is my attempt to make a user-friendly 8051 debugger, with enough online information that it should be unnecessary to read this doc file. PAULMOM is targeted for use by the microprocessor design course at Oregon State, but may be used by anyone (who can figure it out) for projects ranging from research to commercial products. PAULMON is free and may not be distributed for profit whatsoever.

Since I don't expect Prof's or TA's at OSU to make students aware of this documentation nor to provide it nor do I expect students to read much of it, I wrote PAULMON to be very simple and to provide lots of on-line clues about that it can do and how to go about it. I hope that you

find PAULMON to be useful and easy to use. Good Luck.

-Paul Stoffregen

(paul@ece.orst.edu)

DISCLAIMER: This is free software. As far as warranty is concerned, you get exactly what you pay for! I have tried to make this code as good as possible during the four weeks I worked on it, but nobody is perfect and portions (the single step in particular) were never well tested. USE AT YOUR OWN RISK. The assembly source is provided in case there's something you don't like.

ADDITIONAL DISCLAIMER: This doc file has lots of tyopes and other errorss, and I really don't care. PAULMON was written to be easy enough that this file ought to be unnecessary, but people ask for it nonetheless, usually before they even try to use the thing.

#### What You Will Need to use it:

PAULMON is 8051 assembly code which is intended to be burned into a 2764 EPROM, though a pair of 2732's could be used or a bigger rom can be used with the rest being empty or filled with other code. The EPROM with PAULMON should be addressed so that it is read from 0000 to 1FFF with the 8051's EA pin wired to make it read all code from external memory. PAULMON uses the built in UART in the 8051 to communicate with the user. Typically, a PC computer is used with a terminal program, an 8051 assembler, and a text editor to form a simple, low cost 8051 development system with PAULMON. A serial line receiver and driver should be used (the MAX232 is a good choice, IMHO) to interface the 8051 to the PC's serial port. Only TxD, RxD and ground are used (no handshaking) and PAULMON adapts to use whatever baud rate the computer is using (if it can with the crystal you select, see below)

PAULMON is intended to be used with RAM as well, and the default location for the beginning of the RAM is 2000 (hex), right after the EPROM, though the RAM can be used anywhere in the

range of 2000 - FFFF. The read enable signal to the RAM should be the logical OR of the RD and PSEN signals, so that read attempts to external code memory or program memory spaces will read from the RAM. (use an AND gate to do the logical OR of these signals, since they are active low!) Obviously the write enable of the RAM should be connected to the WR pin of the 8051.

Having a RAM connected in this way will allow the download command in PAULMON to write your program into the RAM (writing into the external data memory space). Then you can run your program, since read attempts from the external program memory space will read from the RAM chip.

#### How to get is set up:

Design and build your 8051 board. All that is really required is the 8051, an EPROM, a latch (74xx373), some sort of address decoding to enable the EPROM for memory access between 0000-1FFF, and a line receiver to convert the high voltage RS232 to a TTL (or CMOS) compatible signal (or else you'll toast the 8051 before it even has a chance).

To really use PAULMON, a RAM is required as well as the AND gate to allow both program and data read cycles to read the RAM memory, and a reset button to easily get back to PAULMON when your program crashes.

With just the minimal setup, set the computer's baud rate to something slow (like 1200 bps) and power up the board. Press Enter (Return) and hopefully you'll see a screenful of text from PAULMON. PAULMON does not send line feed characters, so the terminal emulator software must be configured to translate CR -> CR/LF. (PAULMON ignores LF characters is receives.) If the entire message ends up on one line, then the terminal is not translating CR -> CR/LF. After it works, you can try increasing the baud rate and COLD-BOOTING (you must turn the power off, taking the reset line high will not make PAULMON look for the new baud rate... or change the bytes where it stores the old baud rate... see the code if you're interested) If the minimal system shows no signs of life, it's time to check the wiring, usually starting by making sure you didn't swap the TxD and RxD lines.

#### The Automatic Baud Rate detection:

This code was borrowed from MDP/51 by Kei-Yong Khoo. It is run immediatly after a system reset. It waits for a <RETURN> character, and uses it to calculate the timer #1 reload value. Some modifications have been made to Khoo's code. It requires only one character. It also stores the reload value in four memory locations in internal ram (78H, 79H, 7AH, and 7BH). These four locations are unlikely to be changed during a user program's execution or while the debugger is running. When another reset occurs (without removing the power) the program looks at those four locations. If all four agree, then it uses that reload value and does not require another keypress. It is interesting to note that occasionally, with cystal values which produce exact reload values (such an 7.3728 MHz), the baud rate detection routine may not correctly calculate the reload value. Garbage will get printed all over the screen. If this happens, just switch off the power and try again. The advantage of crystals such as the 7.3728 Mhz is that they allow transmission at speeds of 9600 and 19200 baud! It is highly recomended that you use the highest possible baud rate with this debugger, as is tends to print quite a bit of text to the screen.

#### On-line Help:

By typing '?' at the main menu, a help screen summarizing the available commands is printed. Online help is also available regarding the single step run feature. This help is accessed by typing '?' just after using the 'R' command. While in the single step mode, a summary of commands is also available, again by typing '?'.

#### The <ESC> key:

The <ESC> key is supported extensively. It will abort all commands from any prompt. It will stop the list and hex dump commands in the middle of their printing. It will also interrupt the printing of text to the screen! This is useful at slow baud rates, since a full screen of text can take quite a while to print at 300 baud.

#### The Download Program command (type 'D')

This allows you to send the object code from the assembler to the external ram. The object file must be a standard Intel Hex Format file, such as the .OBJ file created by the Psuedo-Assembler, by Psuedo-Corp. The file must be sent as an ASCII transfer. The protocal such as XMODEM is used. Pressing the <ESC> key at any time will abort the transfer. Please note that most communications programs use the <ESC> key to abort their transfer. In this is the case, the first <ESC> will halt the terminal, pressing it again will abort the recieve at the 8051/31. Unlike some other debuggers, PAULMON will recognize the <ESC> key anywhere in the middle of the incoming data, not just at the beginning of a line.

#### The Run Program command (type 'R')

The run command allows you to execute your program. Two types of run are supported, Normal and Single-Step. The single step mode is explained later, as it is fairly complex. During a normal run, the quiviliant of an LCALL to your code is given. During the execution of your program, the debugger obviously has no control of the system, unless of course your program calls one of the subroutines offered by the degugger in the jump table at location 0030H. After specifying which run mode you need, the location of your program is prompted, with the current memory pointer value as the default choice. As is the case at all prompts, pressing the <ESC> key will abort the run command. It is interesting to note that the run command leaves timer #1 in auto-baud rate generation mode. If serial communication is desired at the same baud rate as that used for the debugger, timer #1 need not be given a new reload value. It is recommended that the character input and output routines from the debugger be used via the jump table.

#### The New Memory Location command (type 'N')

The debugger operates with a pointer to the data memory with which you are working. This pointer is used by the list and hex dump command. It is also the default run location. The pointer is incremented as memory is viewed or modified. Just type 'N' to change it.

#### The List command (type 'L')

This debugger gives you the ability to list your program's code directly from the computer's memory. All the 8051/31 mnemunonics are supports, as well as the names of the special function registers. Bit addressable locations are displayed using the standard syntax (e.g. PWS.2 or 20.5), but individual bit location names are not supported (e.g. SCON.0 will print in place of RI). Obviously, the original labels used in the source code cannot be printed, instead the memory locations are displayed. Other special Intel assembly formats, such as \$ and CALL are not

supported. However, the list command can provide a reassuring look at the program directly from the memory.

The Hex Dump command (type 'H')

By typing 'H', the next 256 bytes of ram are dumped to the screen in hex and ascii. The <ESC> key may be pressed to abort the printout.

The Edit command (type 'E')

This command allows you to change the values of memory locations in the external ram. Each location's old value is shown. If <ESC> is pressed, the current location's value is not changed.

#### The Jump Table:

Desipte the use of the word "jump", the user must LCALL to these locations! The individual locations contain jumps to the subroutines, which all terminate with a RET. The table provides the user with a memory location to call to that WILL NOT CHANGE if the debugger is reassembled. The routines available are:

0030:	Cout	-Sends the byte in Acc to the serial port.
0032:	Cin	-Waits for a character from the serial port, returned in Acc.
0034:	pHex	-Prints the two digit hex value in Acc to the serial port.
0036:	pHex16	-Prints the four digit hex value in DPTR to the serial port.
0038:	pString	-Prints the string in code memory pointed to by DPTR to the serial port.
		The string must terminate with 00H or a high bit set
003A:	gHex	-Gets a two digit hex value from the serial port, returned in Acc
003 <b>C</b> :	gHex16	Gets a four digit hex value from the serial port, returned in DPTR
003E:	Esc	-Checks to see if the <esc> key is waiting in SBUF. Clears the buffer if it</esc>
		is, and returns with the carry set. Otherwise, leaves SBUF untouched, and
		returns with C=0.

0040: Upper -Converts character in Acc to uppercase if it is lowercase

0042: Init -Automatic baud rate detection.

The memory location can be placed directly in your code, or an EQU can be used to make your code more readable. For example:

Program:.EQU	gHex16, 003AH	;this make the code nice
MOV	DPTR, #StrLoc	;load DPTR
LCALL	gHex16	;print the DPTR
MOV	A,#13	
LCALL	0030H	;print a <ret></ret>
LCALL	0038H	print the string

RET StrLoc: .DB "This is my String.", 0

Most of these routines leave the registers unchanged, however, it is a good idea to consult the source code just to be sure... In particular, the phex routine DESTROYS the contents of Acc, so beware. (this has cause some people some grief, who had assumed the phex would leave Acc unchanged. If you want it unchanged, the original .ASM file is provided for you to modify) The Single-Step Run:

[This part was never written, and the single step run code is somewhat buggy, primarily due to a lack of available beta testers... so docs were never written, but PAULMON ought to give you enough clues to figure it out if you try.]

### APPENDIX B. 8051 PROGRAMMERS REFERENCE

### PROGRAMMER'S GUIDE AND INSTRUCTION SET

#### **Memory Organization**

#### **Program Memory**

The 80C51 has separate address spaces for program and data memory. The Program memory can be up to 64k bytes long. The lower 4k can reside on-chip. Figure 1 shows a map of the 80C51 program memory.

The 80C51 can address up to 64k bytes of data memory to the chip. The MOVX instruction is used to access the external data memory.

The 80C51 has 128 bytes of on-chip RAM, plus a number of Special Function Registers (SFRs). The lower 128 bytes of RAM can be accessed either by direct addressing (MOV data addr) or by indirect addressing (MOV @Ri). Figure 2 shows the Data Memory organization.

#### **Direct and Indirect Address Area**

The 128 bytes of RAM which can be accessed by both direct and indirect addressing can be divided into three segments as listed below and shown in Figure 3.

- Register Banks 0-3: Locations 0 through 1FH (32 bytes). The device after reset defaults to register bank 0. To use the other register banks, the user must select them in software. Each register bank contains eight 1-byte registers 0 through 7. Reset initializes the stack pointer to location 07H, and it is incremented once to start from location 08H, which is the first register (R0) of the second register bank. Thus, in order to use more than one register bank, the SP should be initialized to a different location of the RAM where it is not used for data storage (i.e., the higher part of the RAM).
- 2. Bit Addressable Area: 16 bytes have been assigned for this segment, 20H-2FH.

- Each one of the 128 bits of this segment can be directly addressed (0-7FH). The bits can be referred to in two ways, both of which are acceptable by most assemblers. One way is to refer to their address (i.e., 0-7FH). The other way is with reference to bytes 20H to 2FH. Thus, bits 0-7 can also be referred to as bits 20.0-20.7, and bits 8-FH are the same as 21.0-21.7, and so on. Each of the 16 bytes in this segment can also be addressed as a byte.
- Scratch Pad Area: 30H through 7FH are available to the user as data RAM. However, if the stack pointer has been initialized to this area, enough bytes should be left aside to prevent SP data destruction.

Figure 2 shows the different segments of the on-chip RAM.

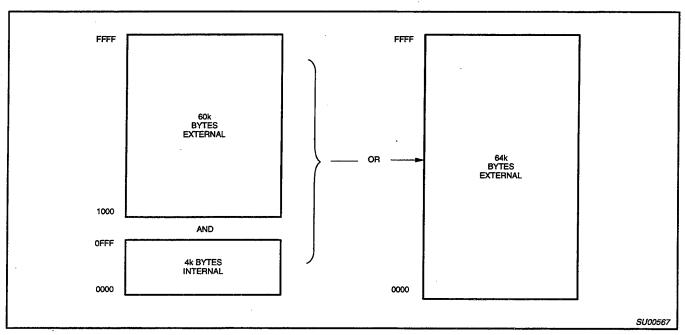


Figure 1. 80C51 Program Memory

1

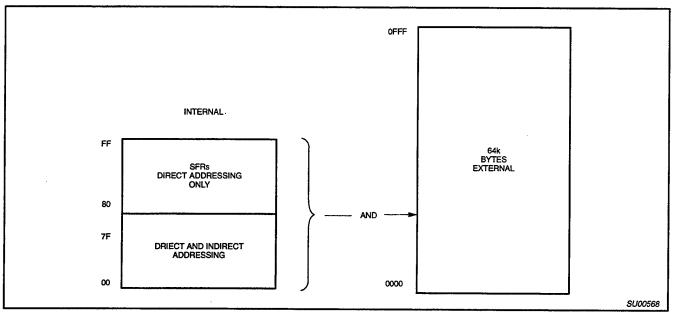


Figure 2. 80C51 Data Memory

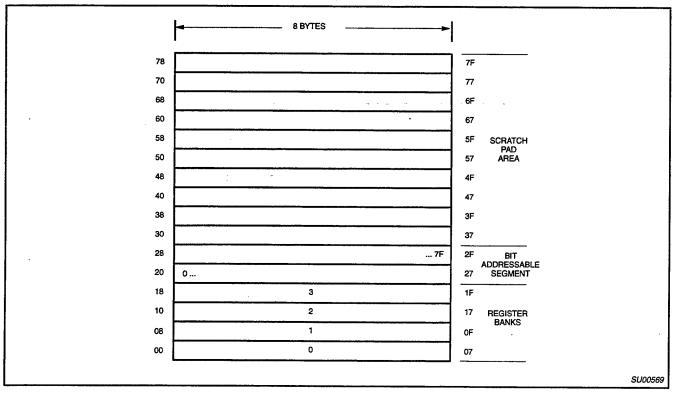


Figure 3. 128 Bytes of RAM Direct and Indirect Addressable

Table 1. 80C51 Special Function Registers

SYMBOL	DESCRIPTION DIRECT ADDRESS MSB BIT ADDRESS, SYMBOL, OR ALTERNATIVE PORT FUNCTION MSB LSB					RESET VALUE					
ACC*	Accumulator	E0H	E7	E6	E5	E4	E3	E2	E1	E0	00H
B*	B register	FOH	F7	F6	F5	F4	F3	F2	F1	F0	00H
DPTR	Data pointer (2 bytes)										
DPH	Data pointer high	83H	l								оон
DPL	Data pointer low	82H									00Н
	,		AF	AE	AD	AC	AB	AA	<b>A</b> 9	A8	j
IE*	Interrupt enable	A8H	EA		_	ES	ET1	EX1	ET0	EX0	0х000000В
			BF	BE	BD	ВС	BB	ВА	<b>B</b> 9	B8	
IP*	Interrupt priority	B8H	_		_	PS	PT1	PX1	PT0	PX0	ж000000B
			87	86	85	84	83	82	81	80	
P0*	Port 0	80H	AD7	AD6	AD5	AD4	AD3	AD2	AD1	AD0	FFH
			97	96	95	94	93	92	91	90	
P1*	Port 1	90H	-		<del>-</del>	94	T	92	T2EX	T2	FFII
F1,	Porti	30N	<del></del>	-	<u> </u>		<u> </u>		LIZEX	12	FFH
· :			A7	. <b>A</b> 6	<b>A</b> 5	<b>A4</b>	<b>A3</b>	<b>A</b> 2	A1	AO	
P2*	Port 2	A0H	A15	A14	A13	A12	A11	A10	A9	A8	FFH
						•		·	•		
			B7	<b>B</b> 6	B5	B4	В3	B2	B1	B0	
P3*	Port 3	вон	RD	WR	T1	ТО	INT1	INTO	TxD	Rxd	FFH
PCON1	Power control	87H	SMOD	-	_	-	GF1	GF0	PD	IDL	0xxxxxxB
			D7	D6	D5	D4	D3	D2	D1	D0	
PSW*	Program status word	DOH	CY	AC	F0	RS1	RS0	O۷	_	Р	00H
SBUF	Serial data buffer	99H							·		xxxxxxxxB
i			9F	9E	9D	9C	9B	9A	99	98	
SCON*	Serial controller	98H	SM0	SM1	SM2	REN	TB8	RB8	TI	RI	00H
SP	Stack pointer	81H									07H
			8F	8E	8D	8C	8B	8A	89	88	
TCON*	Timer control	88H	TF1	TR1	TF0	TR0	IE1	IT1	IE0	IT0	
тно	Timer high 0	8CH									00H
TH1	Timer high 1	8DH									00H
TLO	Timer low 0	8AH									00H
TL1	Timer low 1	8BH									00H
TMOD	Timer mode	89H	GATE	C/T	M1	MO	GATE	C/T	M1	MO	00H

3

### NOTES:

<sup>\*</sup> Bit addressable

<sup>1.</sup> Bits GF1, GF0, PD, and IDL of the PCON register are not implemented on the NMOS 8051/8031.

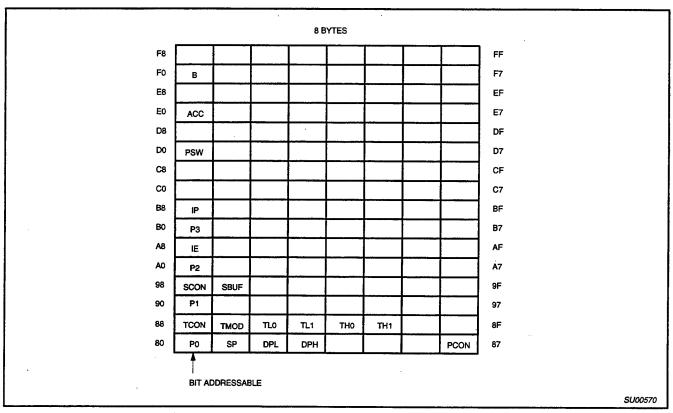


Figure 4. SFR Memory Map

Those SFRs that have their bits assigned for various functions are listed in this section. A brief description of each bit is provided for quick reference. For more detailed information refer to the Architecture Chapter of this book.

#### PSW: PROGRAM STATUS WORD. BIT ADDRESSABLE.

CY	AC	F0	RS1	RS0	OV	_	P
CY	PSW.7	Carr	y Flag.	• " "			
AC	PSW.6	Auxi	liary Carry	Flag.			
F0	PSW.5	Flag	0 available	e to the use	er for gene	ral purpose	e.
RS1	PSW.4	Řegi	ster Bank	selector bit	1 (SEE N	OTE 1).	
RS0	PSW.3	Regi	ster Bank	selector bit	0 (SEE N	OTE 1).	
OV	PSW.2	Over	flow Flag.				
<u>-</u> .	PSW.1	Usab	le as a ge	neral purpo	ose flag.		
P	PSW.0		y flag. Set/ ccumulato		hardware	each instru	ction cycle

#### NOTE:

<sup>1.</sup> The value presented by RS0 and RS1 selects the corresponding register bank.

RS1	RS0	REGISTER BANK	ADDRESS
0	0	0	00H-07H
0	1	1	08H-0FH
1	0	2	10H-17H
1	1	3	18H-1FH

#### PCON: POWER CONTROL REGISTER. NOT BIT ADDRESSABLE.

SMOD	_	-	-	GF1	GF0	PD	IDL

SMOD Double baud rate bit. If Timer 1 is used to generate baud rate and SMOD = 1, the baud rate is doubled when the Serial Port is used in modes 1, 2, or 3.

- Not implemented, reserved for future use.\*
- Not implemented reserved for future use.\*
- Not implemented reserved for future use.\*
- GF1 General purpose flag bit.
- GF0 General purpose flag bit.
- PD Power Down Bit. Setting this bit activates Power Down operation in the 80C51. (Available only in CMOS.)
- IDL Idle mode bit. Setting this bit activates Idle Mode operation in the 80C51. (Available only in CMOS.)

If 1s are written to PD and IDL at the same time, PD takes precedence.

<sup>\*</sup> User software should not write 1s to reserved bits. These bits may be used in future 8051 products to invoke new features.

#### **INTERRUPTS:**

To use any of the interrupts in the 80C51 Family, the following three steps must be taken.

- 1. Set the EA (enable all) bit in the IE register to 1.
- 2. Set the corresponding individual interrupt enable bit in the IE register to 1.
- 3. Begin the interrupt service routine at the corresponding Vector Address of that interrupt. See Table below.

INTERRUPT SOURCE	VECTOR ADDRESS
IE0	0003H
TF0	000BH
IE1	0013H
TF1	001BH
RI & TI	. 0023H

In addition, for external interrupts, pins INTO and INT1 (P3.2 and P3.3) must be set to 1, and depending on whether the interrupt is to be level or transition activated, bits ITO or IT1 in the TCON register may need to be set to 1.

ITx = 0 level activated

ITx = 1 transition activated

#### IE: INTERRUPT ENABLE REGISTER. BIT ADDRESSABLE.

If the bit is 0, the corresponding interrupt is disabled. If the bit is 1, the corresponding interrupt is enabled.

EA	_		ES	ET1	EX1	ET0	EX0	
EA	IE.7		Disables all interrupts. If $EA = 0$ , no interrupt will be ackn individually enabled or disabled by setting or clearing its					
_	IE.6	Not i	mplement	ed, reserve	ed for futur	e use.*		
_	IE.5	Not i	mplement	ed, reserve	ed for futur	e use.*		
ES	IE.4	Enat	ole or disal	ole the seri	ial port inte	errupt.		
ET1	IE.3	Enal	ole or disat	ole the Tim	er 1 overfi	ow interrup	ot.	
EX1	IE.2	Enat	ole or disat	ole Externa	al Interrupt	1.		
ET0	IE.1	Enat	ole or disat	ole the Tim	er 0 overfl	ow interrup	ot.	
EX0	IE.0	Enat	ole or disat	ole Externa	al Interrupt	0.		

User software should not write 1s to reserved bits. These bits may be used in future 80C51 products to invoke new features.

#### **ASSIGNING HIGHER PRIORITY TO ONE OR MORE INTERRUPTS:**

In order to assign higher priority to an interrupt the corresponding bit in the IP register must be set to 1.

Remember that while an interrupt service is in progress, it cannot be interrupted by a lower or same level interrupt.

#### **PRIORITY WITHIN LEVEL:**

Priority within level is only to resolve simultaneous requests of the same priority level.

From high to low, interrupt sources are listed below:

IE0

TF0

IE1

TF1

RI or TI

#### IP: INTERRUPT PRIORITY REGISTER. BIT ADDRESSABLE.

If the bit is 0, the corresponding interrupt has a lower priority and if the bit is 1 the corresponding interrupt has a higher priority.

_	_	_	PS	PT1	PX1	PT0	PX0
_	IP.7	Not i	mplement	ed, reserve	ed for futur	e use.*	
_	IP.6	Not i	mplement	ed, reserve	ed for futur	e use.*	
_	IP.5	Not i	mplement	ed, reserve	ed for futur	e use.*	
PS	IP.4	Defir	nes the Se	rial Port int	terrupt prio	rity level.	
PT1	IP.3	Defir	nes the Tir	ner 1 interr	upt priority	level.	
PX1	IP.2	Defir	nes Extern	al Interrupt	t 1 priority I	evel.	
PT0	IP.1	Defir	es the Tir	ner 0 interr	upt priority	level.	
PX0	IP.0	Defir	es the Ex	ternal Inter	rupt 0 prio	rity level.	

<sup>\*</sup> User software should not write 1s to reserved bits. These bits may be used in future 80C51 products to invoke new features.

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#### TCON: TIMER/COUNTER CONTROL REGISTER. BIT ADDRESSABLE.

TF1	TR1	TF0	TRO.	IE1	IT1	IE0	IT0	
TF1	TCON.7		er 1 overflor essor vecto	-	•			ounter 1 overflows. Cleared by hardware as
TR1	TCON.6	Time	er 1 run cor	ntrol bit. Se	et/cleared l	by software	to turn Tir	mer/Counter 1 ON/OFF.
TF0	TCON.5		er 0 overflov essor vecto	•	•		ne Timer/C	ounter 0 overflows. Cleared by hardware as
TR0	TCON.4	Time	er 0 run cor	ntrol bit. Se	et/cleared b	oy software	to turn Tir	ner/Counter 0 ON/OFF.
IE1	TCON.3		rnal Interru ware when		_	•	when Ext	ernal Interrupt edge is detected. Cleared by
IT1	TCON.2	Inter Inter		control bit	. Set/clear	ed by softw	are to spe	cify falling edge/low level triggered External
IE0	TCON.1		rnal Interru ware when		-	-	when Exte	ernal Interrupt edge detected. Cleared by
ITO .	TCON.0	Inter Inter		control bit	. Set/clear	ed by softv	vare to spe	cify falling edge/low level triggered External

#### TMOD: TIMER/COUNTER MODE CONTROL REGISTER. NOT BIT ADDRESSABLE.

GATE	C/T	M1	MO	GATE	C/T	M1	МО
	Tin	ner 1			Tir	mer 0	

GATE When TRx (in TCON) is set and GATE = 1, TIMER/COUNTERx will run only while INTx pin is high (hardware control).

When GATE = 0, TIMER/COUNTERx will run only while TRx = 1 (software control).

C/T Timer or Counter selector. Cleared for Timer operation (input from internal system clock). Set for Counter operation

(input from Tx input pin).

M1 Mode selector bit. (NOTE 1)

M0 Mode selector bit. (NOTE 1)

#### NOTE 1:

М1	MO	Operating Mode	
0	0	0 13-bit Timer (8048 compatible)	
0	1	1 16-bit Timer/Counter	
1	0	2 8-bit Auto-Reload Timer/Counter	
1	. 1	3 (Timer 0) TL0 is an 8-bit Timer/Counter of control bits. TH0 is an8-bit Timer and is c	
1	1	3 (Timer 1) Timer/Counter 1 stopped.	

8

#### **TIMER SET-UP**

Tables 2 through 5 give some values for TMOD which can be used to set up Timer 0 in different modes.

It is assumed that only one timer is being used at a time. If it is desired to run Timers 0 and 1 simultaneously, in any mode, the value in TMOD for Timer 0 must be ORed with the value shown for Timer 1 (Tables 5 and 6).

For example, if it is desired to run Timer 0 in mode 1 GATE (external control), and Timer 1 in mode 2 COUNTER, then the value that must be loaded into TMOD is 69H (09H from Table 2 ORed with 60H from Table 5).

Moreover, it is assumed that the user, at this point, is not ready to turn the timers on and will do that at a different point in the program by setting bit TRx (in TCON) to 1.

#### **TIMER/COUNTER 0**

Table 2. As a Timer:

		. TN	IOD
MODE	TIMER 0 FUNCTION	INTERNAL CONTROL (NOTE 1)	EXTERNAL CONTROL (NOTE 2)
0	13-bit Timer	00H	08H
1	16-bit Timer	01H	09H
2	8-bit Auto-Reload	02H	0AH
3	Two 8-bit Timers	03H	0BH

#### Table 3. As a Counter:

		TN	IOD
MODE	COUNTER 0 FUNCTION	INTERNAL CONTROL (NOTE 1)	EXTERNAL CONTROL (NOTE 2)
0	13-bit Timer	04H	0CH
1	16-bit Timer	05H	0DH
2 ·	8-bit Auto-Reload	06H	0EH
3	One 8-bit Counter	07H	0FH

#### NOTES:

1. The timer is turned ON/OFF by setting/clearing bit TR0 in the software.

<sup>2.</sup> The Timer is turned ON/OFF by the 1-to-0 transition on INTO (P3.2) when TRO = 1 (hardware control).

#### **TIMER/COUNTER 1**

Table 4. As a Timer:

		TM	IOD
MODE	TIMER 1 FUNCTION	INTERNAL CONTROL (NOTE 1)	EXTERNAL CONTROL (NOTE 2)
0	13-bit Timer	00H	80H
1	16-bit Timer	10H	90H
2	8-bit Auto-Reload	20H	АОН
3	Does not run	30H	вон

#### Table 5. As a Counter:

		TA	IOD
MODE	COUNTER 1 FUNCTION	INTERNAL CONTROL (NOTE 1)	EXTERNAL CONTROL (NOTE 2)
0	13-bit Timer	40H	C0H
1	16-bit Timer	50H	D0H
2	8-bit Auto-Reload	60H	E0H
3	Not available		_

The timer is turned ON/OFF by setting/clearing bit TR1 in the software.
 The Timer is turned ON/OFF by the 1-to-0 transition on INT1 (P3.2) when TR1 = 1 (hardware control).

#### SCON: SERIAL PORT CONTROL REGISTER, BIT ADDRESSABLE.

SM0	SM1	SM2	REN	TB8	RB8	TI	RI			
SM0	SCON.7	7 Seria	al Port mod	le specifie	r. (NOTE 1	)				
SM1	SCON.6	Seria	Serial Port mode specifier. (NOTE 1)							
SM2	SCON.5	RI w	Enables the multiprocessor communication feature in modes $2 \& 3$ . In mode $2 \text{ or } 3$ , if SM2 is set to 1 tt RI will not be activated if the received 9th data bit (RB8) is 0. In mode 1, if SM2 = 1 then RI will not activated if a valid stop bit was not received. In mode 0, SM2 should be 0. (See Table 6.)							
REN	SCON.4	Set/0	Cleared by	software to	o Enable/D	isable rec	eption.			
TB8	SCON.3	The s	9th bit that	will be trai	nsmitted in	modes 2	& 3. Set/Cl			
RB8	SCON.2		odes 2 & 3, ved. In mo				ived. In mo			
TI	SCON.1				•		nd of the 8t / software.			
RI	SCON.0		eive interruj bit time in t		•					

#### NOTE 1:

SMO	SM1	Mode	Description	Baud Rate
0	0 -	0 -	Shift Register	F <sub>OSC.</sub> /12
0	1	1	8-bit UART	Variable
1	0	2	9-bit UART	F <sub>OSC.</sub> /64 or F <sub>OSC.</sub> /32
1	1	3	9-bit UART	Variable

#### **SERIAL PORT SET-UP:**

#### Table 6.

MODE	SCON	SM2 VARIATION
0 1 2 3	10H 50H 90H D0H	Single Processor Environment (SM2 = 0)
0 1 2 3	NA 70H B0H F0H	Multiprocessor Environment (SM2 = 1)

#### **GENERATING BAUD RATES**

#### Serial Port in Mode 0:

Mode 0 has a fixed baud rate which is 1/12 of the oscillator frequency. To run the serial port in this mode none of the Timer/Counters need to be set up. Only the SCON register needs to be defined.

Baud Rate = 
$$\frac{\text{Osc Freq}}{12}$$

#### Serial Port in Mode 1:

Mode 1 has a variable baud rate. The baud rate is generated by Timer 1.

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### **USING TIMER/COUNTER 1 TO GENERATE BAUD RATES:**

For this purpose, Timer 1 is used in mode 2 (Auto-Reload). Refer to Timer Setup section of this chapter.

Baud Rate = 
$$\frac{K}{32}$$
 Osc Freq [256 (TH1)]

If SMOD = 0, then K = 1.

If SMOD = 1, then K = 2 (SMOD is in the PCON register).

Most of the time the user knows the baud rate and needs to know the reload value for TH1.

TH1 = 256 
$$\frac{K}{384}$$
 baud rate

TH1 must be an integer value. Rounding off TH1 to the nearest integer may not produce the desired baud rate. In this case, the user may have to choose another crystal frequency.

Since the PCON register is not bit addressable, one way to set the bit is logical ORing the PCON register (i.e., ORL PCON,#80H). The address of PCON is 87H.

### **SERIAL PORT IN MODE 2:**

The baud rate is fixed in this mode and is 1/32 or 1/64 of the oscillator frequency, depending on the value of the SMOD bit in the PCON register.

In this mode none of the Timers are used and the clock comes from the internal phase 2 clock.

SMOD = 1, Baud Rate = 1/32 Osc Freq.

SMOD = 0, Baud Rate = 1/64 Osc Freq.

To set the SMOD bit: ORL PCON,#80H. The address of PCON is 87H.

### **SERIAL PORT IN MODE 3:**

The baud rate in mode 3 is variable and sets up exactly the same as in mode 1.

### **80C51 FAMILY INSTRUCTION SET**

Table 7. 80C51 Instruction Set Summary

		Interrupt Respor	nse T	īme: F	Refer t	o Hardware Desci	ription (	Chapt	er.		
		Inst	ructio	ons th	at Af	ect Flag Settings	<sub>S</sub> (1)				
		Instruction		Flag	g	Instruction		Flag	l		
		ADD ADDC SUBB MUL DIV DA RRC RLC SETB C	X	OV X X X X	AC X X X	CLR C CPL C ANL C,bit ANL C,/bit ORL C,bit ORL C,/bit MOV C,bit CJNE	C 0 X X X X X X X	OV	AC	••	
e that opera	ations on SFR byte a					215 (i.e., the PSW			PSW	/) will also affect fla	ag settings.
Rn	Register R7-R0	of the currently sel	lecte	d Reg	ister B	_					
Rn direct	8-bit internal data	-	ss. Th	nis cou	uld be	ank.			(0-12	7) or a SFR [i.e., I	I/O port,
	8-bit internal data control register, s	a location's addres	ss. Th . (128	nis cou 8-255)	uld be ].	ank. an Internal Data F	RAM lo	cation			I/O port,
direct	8-bit internal data control register, s 8-bit internal data	a location's addres status register, etc	ss. Th . (128 -255)	nis cou 8-255) addre	uld be ].	ank. an Internal Data F	RAM lo	cation			I/O port,
direct @Ri	8-bit internal data control register, s 8-bit internal data 8-bit constant inc	a location's addresstatus register, etc a RAM location (0-	ss. Th . (128 -255) action	nis cou 8-255) addre	uld be ].	ank. an Internal Data F	RAM lo	cation			I/O port,
direct @Ri #data	8-bit internal data control register, s 8-bit internal data 8-bit constant ind 16-bit constant in	a location's address status register, etc a RAM location (0- cluded in the instru- ncluded in the instru- naddress. Used by	ss. The contraction (1255) action ruction	nis cou 8-255) addre n.	uld be i]. essed	ank. an Internal Data F indirectly through	RAM loo	cation	or RO.		
direct  @Ri  #data  #data 16	8-bit internal data control register, s 8-bit internal data 8-bit constant ind 16-bit constant in 16-bit destination Memory address 11-bit destination	a location's address status register, etc a RAM location (0- cluded in the instru- ncluded in the instru- n address. Used by space.	ss. The (128 -255) action ruction y LCA	nis cou 8-255) addre a. on ALL ar	uld be i]. essed nd LJM	ank. an Internal Data F indirectly through  MP. A branch can I  MP. The branch wi	RAM loo registe	cation r R1 c	or R0. withir		gram

	MNEMONIC	DESCRIPTION	BYTE	OSCILLATOR PERIOD
ARITHME	TIC OPERATIONS		***	
ADD	A,Rn	Add register to Accumulator	1	12
ADD	A,direct	Add direct byte to Accumulator	2	12
ADD	A,@Ri	Add indirect RAM to Accumulator	1	12
ADD	A,#data	Add immediate data to Accumulator	2	12
ADDC	A,Rn	Add register to Accumulator with carry	1	12
ADDC	A,direct	Add direct byte to Accumulator with carry	2	12
ADDC	A,@Ri	Add indirect RAM to Accumulator with carry	1	12
ADDC	A,#data	Add immediate data to A <sub>CC</sub> with carry	2	12
SUBB	A,Rn	Subtract Register from A <sub>CC</sub> with borrow	1	12
SUBB	A,direct	Subtract direct byte from A <sub>CC</sub> with borrow	2	12
SUBB	A,@Ri	Subtract indirect RAM from A <sub>CC</sub> with borrow	1	12
SUBB	A,#data	Subtract immediate data from A <sub>CC</sub> with borrow	2	12
INC	Α	Increment Accumulator	1	12
INC	Rn	Increment register	1	12

Direct Addressed bit in Internal Data RAM or Special Function Register.

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bit

Table 7. 80C51 Instruction Set Summary (Continued)

	MNEMONIC	DESCRIPTION	BYTE	OSCILLATOR PERIOD
ARITHME	TIC OPERATIONS (Co	ntinued)		
INC	direct	Increment direct byte	2	12
INC	@Ri	Increment indirect RAM	1	12
DEC	Α	Decrement Accumulator	1	12
DEC	Rn	Decrement Register	1	12
DEC	direct	Decrement direct byte	2	12
DEC	@Ri	Decrement indirect RAM	1	12
INC.	DPTR	Increment Data Pointer	1	24
MUL	AB	Multiply A and B	1	48
DIV	AB	Divide A by B	1	48
DA	Α	Decimal Adjust Accumulator	1	12
LOGICAL	OPERATIONS			
ANL	A,Rn	AND Register to Accumulator	1	12
ANL	A,direct	AND direct byte to Accumulator	2	12
ANL	A,@Ri	AND indirect RAM to Accumulator	1	12
ANL	A,#data	AND immediate data to Accumulator	2	12
ANL	direct,A	AND Accumulator to direct byte	2	12
ANL	direct,#data	AND immediate data to direct byte	3	24
ORL	A,Rn	OR register to Accumulator	1 .	12
ORL	A,direct	OR direct byte to Accumulator	2	12
ORL	A,@Ri	OR indirect RAM to Accumulator	1	12
ORL	A,#data	OR immediate data to Accumulator	2	12
ORL	direct,A	OR Accumulator to direct byte	2	12
ORL	direct,#data	OR immediate data to direct byte	3	24
XRL	A,Rn	Exclusive-OR register to Accumulator	1	12
XRL	A,direct	Exclusive-OR direct byte to Accumulator	2	12
XRL	A,@Ri	Exclusive-OR indirect RAM to Accumulator	1	12
XRL	A,#data	Exclusive-OR immediate data to Accumulator	2	12
XRL	direct,A	Exclusive-OR Accumulator to direct byte	2	12
XRL	direct,#data	Exclusive-OR immediate data to direct byte	3	24
CLR	Α	Clear Accumulator	1	12
CPL	Α	Complement Accumulator	1	12
RL	Α	Rotate Accumulator left	1	12
RLC	Α	Rotate Accumulator left through the carry	1	12
RR	Α	Rotate Accumulator right	1	12
RRC	Α	Rotate Accumulator right through the carry	1	12
SWAP	Α	Swap nibbles within the Accumulator	1	12
ATA TRA	NSFER		•	
MOV	A,Rn	Move register to Accumulator	1	12
MOV	A,direct	Move direct byte to Accumulator	2	12
MOV	A,@Ri	Move indirect RAM to Accumulator	1	12

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Table 7. 80C51 Instruction Set Summary (Continued)

	MNEMONIC	DESCRIPTION	ВҮТЕ	OSCILLATOR PERIOD
DATA TRA	NSFER (Continued)			Western Co.
MOV	A,#data	Move immediate data to Accumulator	2	12
MOV	Rn,A	Move Accumulator to register	1	12
MOV	Rn,direct	Move direct byte to register	2	24
MOV	RN,#data	Move immediate data to register	2	12
MOV	direct,A	Move Accumulator to direct byte	2	12
MOV	direct,Rn	Move register to direct byte	2	24
MOV	direct,direct	Move direct byte to direct	3	24
MOV	direct,@Ri	Move indirect RAM to direct byte	2	24
MOV	direct,#data	Move immediate data to direct byte	3	24
моу	@Ri,A	Move Accumulator to indirect RAM	1	12
MOV	@Ri,direct	Move direct byte to indirect RAM	2	24
MOV	@Ri,#data	Move immediate data to indirect RAM	2	12
MOV	DPTR,#data16	Load Data Pointer with a 16-bit constant	3	24
MOVC	A,@A+DPTR	Move Code byte relative to DPTR to A <sub>CC</sub>	1	24
MOVC	A,@A+PC	Move Code byte relative to PC to A <sub>CC</sub>	1	24
MOVX	A,@Ri	Move external RAM (8-bit addr) to A <sub>CC</sub>	1	24
MOVX .	A,@DPTR	Move external RAM (16-bit addr) to A <sub>CC</sub>	1	24
MOVX	A,@Ri,A	Move A <sub>CC</sub> to external RAM (8-bit addr)	1	24
MOVX	@DPTR,A	Move A <sub>CC</sub> to external RAM (16-bit addr)	1	24
PUSH	direct	Push direct byte onto stack	2	24
POP	direct	Pop direct byte from stack	2	24
KCH	A,Rn	Exchange register with Accumulator	1	12
XCH	A,direct	Exchange direct byte with Accumulator	2	12
XCH	A,@Ri	Exchange indirect RAM with Accumulator	1	12
KCHD	A,@Ri	Exchange low-order digit indirect RAM with A <sub>CC</sub>	1	12
OOLEAN	VARIABLE MANIPULAT	TION		
CLR	С	Clear carry	1	12
CLR	bit	Clear direct bit	2	12
SETB	С	Set carry	1	12
SETB	bit	Set direct bit	2	12
PL	С	Complement carry	1	12
CPL	bit .	Complement direct bit	2	12
NL .	C,bit	AND direct bit to carry	2	24
NL	C,/bit	AND complement of direct bit to carry	2	24
RL	C,bit	OR direct bit to carry	2	24
DRL	C,/bit	OR complement of direct bit to carry	2	24
VOV	C,bit	Move direct bit to carry	2	12
VOV	bit,C	Move carry to direct bit	2	24
С	rel	Jump if carry is set	2	24
NC	rel	Jump if carry not set	2	24

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Table 7. 80C51 Instruction Set Summary (Continued)

	MNEMONIC	DESCRIPTION	BYTE	OSCILLATOR PERIOD
BOOLEAN	VARIABLE MANIPULA	ATION (Continued)		
JB	rel	Jump if direct bit is set	3	24
JNB	rel	Jump if direct bit is not set	3	24
JBC	bit,rel	Jump if direct bit is set and clear bit	3	24
PROGRAM	BRANCHING	•		
ACALL	addr11	Absolute subroutine call	2	24
LCALL	addr16	Long subroutine call	3	24
RET		Return from subroutine	1	24
RETI		Return from interrupt	1	24
AJMP	addr11	Absolute jump	2	24
LJMP	addr16	Long jump	<b>3</b> .	24
SJMP	rel	Short jump (relative addr)	2	24
JMP	@A+DPTR	Jump indirect relative to the DPTR	1	24
JZ	rel	Jump if Accumulator is zero	2	24
JNZ	rel	Jump if Accumulator is not zero	· 2	24
CJNE	A,direct,rel	Compare direct byte to A <sub>CC</sub> and jump if not equal	3	24
CJNE	A,#data,rel	Compare immediate to A <sub>CC</sub> and jump if not equal	3	24
CJNE	RN,#data,rel	Compare immediate to register and jump if not equal	3	24
CJNE	@Ri,#data,rel	Compare immediate to indirect and jump if not equal	3	24
DJNZ	Rn,rel	Decrement register and jump if not zero	2	24
DJNZ	direct,rel	Decrement direct byte and jump if not zero	3	24
NOP		No operation	1	12

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### **INSTRUCTION DEFINITIONS**

#### ACALL addr11

**Function:** 

**Absolute Call** 

**Description:** 

ACALL unconditionally calls a subroutine located at the indicated address. The instruction increments the PC twice to obtain the address of the following instruction, then pushes the 16-bit result onto the stack (low-order byte first) and increments the Stack Pointer twice. The destination address is obtained by successively concatenating the five high-order bits of the incremented PC, opcode bits 7-5, and the second byte of the instruction. The subroutine called must therefore start within the same 2k block of the program memory as the first byte of the instruction following ACALL. No flags are affected.

Example:

Initially SP equals 07H. The label "SUBRTN" is at program memory location 0345 H. After executing the

instruction,

ACALL SUBRTN

at location 0123H, SP will contain 09H, internal RAM locations 08H and 09H will contain 25H and 01H,

respectively, and the PC will contain 0345H.

Bytes: 2

Cycles: 2

**Encoding:** 

a10a9 a8 1 0 0 0 1

a7 a6 a5 a4 a3 a2 a1 a0

Operation:

**ACALL** 

 $\begin{aligned} (PC) &\leftarrow (PC) + 2 \\ (SP) &\leftarrow (SP) + 1 \\ (SP) &\leftarrow (PC_{7-0}) \\ (SP) &\leftarrow (SP) + 1 \\ (SP) &\leftarrow (PC_{15-8}) \end{aligned}$ 

(PC<sub>10-0</sub>) ← page address

#### ADD A,<src-byte>

Function:

Add

**Description:** 

ADD adds the byte variable indicated to the Accumulator, leaving the result in the Accumulator. The carry and auxiliary-carry flags are set, respectively, if there is a carry-out from bit 7 or bit 3, and cleared otherwise. When adding unsigned integers, the carry flag indicates an overflow occurred.

OV is set if there is a carry-out of bit 6 but not out of bit 7, or a carry-out of bit 7 but not bit 6; otherwise OV is cleared. When adding signed integers, OV indicates a negative number produced as the sum of two positive operands, or a positive sum from two negative operands.

Four source operand addressing modes are allowed: register, direct, register-indirect, or immediate.

Example:

The Accumulator holds 0C3H (11000011B) and register 0 holds 0AAH (10101010B). The instruction,

will leave 6DH (01101101B) in the Accumulator with the AC flag cleared and both the Carry flag and OV

set to 1.

ADD A,Rn

1 Bytes: Cycles:

0 1 0 0 r r **Encoding:** 

Operation: ADD

 $(A) \leftarrow (A) + (R_n)$ 

ADD A, direct

Bytes: 2

**Cycles:** 1

0 1 0 0 direct address **Encoding:** 

Operation:

ADD

 $(A) \leftarrow (A) + (direct)$ 

ADD A,@Ri

Bytes: 1 Cycles: 1

**Encoding:** 

0 0 0 1 1 1 i

ADD Operation:

 $(A) \leftarrow (A) + ((R_i))$ 

ADD A,#data

Bytes: 2 Cycles:

0 0 1 0 0 0 immediate data **Encoding:** 

Operation: ADD

 $(A) \leftarrow (A) + \#data$ 

### ADDC A,<src-byte>

Function:

Add with Carry

**Description:** 

ADDC simultaneously adds the byte variable indicated, the carry flag and the Accumulator contents, leaving the result in the Accumulator. The carry and auxiliary-carry flags are set, respectively, if there is a carry-out from bit 7 or bit 3, and cleared otherwise. When adding unsigned integers, the carry flag indicates an overflow occurred.

OV is set if there is a carry-out of bit 6 but not out of bit 7, or a carry-out of bit 7 but not out of bit 6; otherwise OV is cleared. When adding signed integers, OV indicates a negative number produced as the sum of two positive operands, or a positive sum from two negative operands.

Four source operand addressing modes are allowed: register, direct, register-indirect, or immediate.

Example:

The Accumulator holds 0C3H (11000011B) and register 0 holds 0AAH (10101010B) with the carry flag set.

The instruction,

ADDC A,R0

will leave 6EH (01101110B) in the Accumulator with AC cleared and both the Carry flag and OV set to 1.

ADDC A,Rn

Bytes: 1
Cycles: 1

**Encoding:** 

0 0 1 1 1 r r r

Operation:

**ADDC** 

 $(A) \leftarrow (A) + (C) + (R_n)$ 

ADDC A, direct

Bytes: 2 Cycles: 1

**Encoding:** 

0 0 1 1 0 1 0 1

direct address

Operation:

ADDC

 $(A) \leftarrow (A) + (C) + (direct)$ 

ADDC A,@Ri

Bytes: 1 Cycles: 1

**Encoding:** 

0 0 1 1 0 1 1 i

Operation:

**ADDC** 

 $(A) \leftarrow (A) + (C) + ((R_i))$ 

ADDC A,#data

Bytes: 2 Cycles: 1

**Encoding:** 

0 0 1 1 0 1 0 0

immediate data

Operation:

ADDC

 $(A) \leftarrow (A) + (C) + \#data$ 

# 80C51 family programmer's guide and instruction set

AJMP addr11

Function: Absolute Jump

Description: AJMP transfers program execution to the indicated address, which is formed at run-time by concatenating

the high-order five bits of the PC (after incrementing the PC twice), opcode bits 7-5, and the second byte of the instruction. The destination must therefore be within the same 2k block of program memory as the

a3 a2 a1 a0

first byte of the instruction following AJMP.

**Example:** The label "JMPADR" is at program memory location 0123H. The instruction,

AJMP JMPADR

is at location 0345H and will load the PC with 0123H.

Bytes: 2

Cycles: 2

Encoding: and as

a10 a9 a8 0 0 0 0 1 a7 a6 a5 a4

Operation: A

AJMP

 $(PC) \leftarrow (PC) + 2$ 

(PC<sub>10-0</sub>) ← page address

## ANL <dest-byte>,<src-byte>

Function: Logical-AND for byte variables

Description: ANL performs the bitwise logical-AND operation between the variables indicated and stores the results in

the destination variable. No flags are affected.

The two operands allow six addressing mode combinations. When the destination is the Accumulator, the source can use register, direct, register-indirect, or immediate addressing; when the destination is a direct address, the source can be the Accumulator or immediate data.

Note: When this instruction is used to modify an output port, the value used as the original port data will be read from the output data latch, not the input pins

be read from the output data latch, not the input pins.

Example: If the Accumulator holds 0C3H (11000011B) and register 0 holds 55H (01010101B) then the instruction,

ANL A,RO

will leave 41H (01000001B) in the Accumulator.

When the destination is a directly addressed byte, this instruction will clear combinations of bits in any RAM location or hardware register. The mask byte determining the pattern of bits to be cleared would either be a constant contained in the instruction or a value computed in the Accumulator at run-time. The instruction,

ANL P1,#01110011B

will clear bits 7, 3, and 2 of output port 1.

# 80C51 Family

ANL A,Rn **Bytes:** 1 **Cycles:** 1 0 0 1 r r **Encoding:** Operation: ANL  $(A) \leftarrow (A) \land (R_n)$ ANL A, direct Bytes: 2 Cycles: 1 0 0 1 0 direct address 1 0 1 **Encoding:** Operation: **ANL**  $(A) \leftarrow (A) \land (direct)$ ANL A,@Ri **Bytes:** 1. **Cycles:** 1 0 1 0 1 0 1 1 i **Encoding:** ANL Operation:  $(\mathsf{A}) \leftarrow (\mathsf{A}) \wedge ((\mathsf{R}_i))$ ANL A,#data 2 Bytes: 1 **Cycles:** 0 0 1 0 0 0 immediate data 1 **Encoding: ANL** Operation:  $(A) \leftarrow (A) \land \#data$ ANL direct,A Bytes: 2 Cycles: 1 0 direct address 1 **Encoding:** Operation: ANL  $(A) \leftarrow \langle direct \rangle \land (A)$ ANL direct,#data Bytes: 3 Cycles: 2 0 1 0 1 0 0 direct address immediate data **Encoding:** Operation: ANL  $(direct) \leftarrow (direct) \land \#data$ 

## ANL C,<src-bit>

**Function:** 

Logical-AND for bit variables

**Description:** 

If the Boolean value of the source bit is a logical 0 then clear the carry flag; otherwise leave the carry flag in its current state. A slash ("/") preceding the operand in the assembly language indicates that the logical complement of the addressed bit is used as the source value, but the source bit itself is not affected. No

other flags are affected.

Only direct addressing is allowed for the source operand.

**Example:** 

Set the carry flag if, and only if, P1.0 = 1, ACC.7 = 1, and OV = 0: MOV C,P1.0 ;LOAD CARRY WITH INPUT PIN STATE

ANL

C,ACC.7;AND CARRY WITH ACCUM. BIT 7

ANL

**ANL** 

C,/OV ;AND WITH INVERSE OF OVERFLOW FLAG

ANL C,bit

Bytes: 2 2 Cycles:

**Encoding:** 

0 0 0 0 1 0

bit address

Operation:

 $(C) \leftarrow (C) \land (bit)$ 

ANL C,/bit

**Bytes:** 2 2

Cycles:

1 0

bit address

**Encoding:** Operation:

 $(C) \leftarrow (C) \land (bit)$ 

### CJNE <dest-byte>,<src-byte>,rel

**Function:** 

Compare and Jump if Not Equal

**Description:** 

CJNE compares the magnitudes of the first two operands, and branches if their values are not equal. The branch destination is computed by adding the signed relative-displacement in the last instruction byte to the PC, after incrementing the PC to the start of the next instruction. The carry flag is set if the unsigned integer value of <dest-byte> is less than the unsigned integer value of <src-byte>; otherwise, the carry is cleared. Neither operand is affected.

The first two operands allow four addressing mode combinations: the Accumulator may be compared with any directly addressed byte or immediate data, and any indirect RAM location or working register can be compared with an immediate constant.

Example:

The Accumulator contains 34H. Register 7 contains 56H. The first instruction in the sequence,

CJNE	R7,#60H,NOT_EQ	
;	···· ;	R7 = 60H.
NOT_EQ JC	REQ_LOW ;	IF R7 < 60H.
:	:	R7 > 60H.

sets the carry flag and branches to the instruction at label NOT\_EQ. By testing the carry flag, this instruction determines whether R7 is greater or less than 60H.

If the data being presented to Port 1 is also 34H, then the instruction,

WAIT: CJNE A,P1,WAIT

clears the carry flag and continues with the next instruction in sequence, since the Accumulator does equal the data read from P1. (If some other value was being input on P1, the program will loop at this point until the P1 data changes to 34H.)

## CJNE A, direct, rel

Bytes: 3

Cycles: 2

Encoding:

0 ,	1	1	0	1	0	1	

direct address

rel. address

Operation:

$$(PC) \leftarrow (PC) + 3$$
  
IF (A) < > (direct)

THEN.

$$(C) \leftarrow 1$$

**ELSE** 

$$(C) \leftarrow 0$$

```
CJNE A,#data,rei
         Bytes:
                    3
        Cycles:
                    2
                                                  0
                                                            immediate data
                                                                                   rel. address
                             1 1
                                           1
                                               0
    Encoding:
    Operation:
                    (PC) \leftarrow (PC) + 3
                    IF (A) < > data
                    THÈŃ
                                   (PC) ← (PC) + relative offset
                    IF (A) < data
                   THEN
                                   (C) ← 1
                   ELSE
                                   (C) \leftarrow 0
CJNE Rn,#data,rei
        Bytes:
                   3
                   2
       Cycles:
                        0
                                                            immediate data
                                                                                   rel. address
                             1
    Encoding:
    Operation:
                    (PC) \leftarrow (PC) + 3
                   IF(R_n) < > data
                   THEN
                                   (PC) ← (PC) + relative offset
                   IF (R<sub>n</sub>) < data
THEN
                                   (C) \leftarrow 1
                   ELSE
                                   (C) \leftarrow 0
CJNE @Ri,#data,rel
        Bytes:
                   3
       Cycles:
                   2
                        0 1 1
                                         1
                                              1 i
                                                            immediate data
                                                                                   rel. address
    Encoding:
    Operation:
                   (PC) \leftarrow (PC) + 3
                   IF ((R_i)) < > data
                   THEN
                                   (PC) ← (PC) + relative offset
                   IF ((R_i)) < data
                   THÈN
                                   (C) \leftarrow 1
                   ELSE
                                   (C) \leftarrow 0
```

CLR A

Function: Clear Accumulator

Description: The Accumulator is cleared (all bits reset to zero). No flags are affected.

Example: The Accumulator contains 5CH (01011100B). The instruction,

CLR A

will leave the Accumulator set to 00H (0000000B).

Bytes: 1 Cycles: 1

Cycles:

Encoding: 1 1 1 0 0 1 0 0

Operation: CLR

 $(A) \leftarrow 0$ 

CLR bit

Function: Clear bit

Description: The indicated bit is cleared (reset to zero). No other flags are affected. CLR can operate on the carry flag

or any directly addressable bit.

**Example:** Port 1 has previously been written with 5DH (01011101B). The instruction,

CLR P1.2

will leave the port set to 59H (01011001B).

CLR C

Bytes: 1

Cycles: 1

Encoding: 1 1 0 0 0 0 1 1

Operation: CLR

(C) ← 0

CLR bit

Bytes: 2

Cycles: 1

Encoding: 1 1 0 0 0 0 1 0 bit address

Operation: CLR

(bit)  $\leftarrow$  0

#### CPL Α

Function: Complement Accumulator

**Description:** Each bit of the Accumulator is logically complemented (one's complement). Bits which previously

contained a one are changed to a zero and vice-versa. No flags are affected.

The Accumulator contains 5CH (01011100B). The instruction, Example:

CPL A

will leave the Accumulator set to 0A3H (10100011B).

Bytes: Cycles: 1

1 1 0 0 0 **Encoding:** 

Operation: **CPL** 

 $(A) \leftarrow (A)$ 

#### CPL bit

Complement bit **Function:** 

The bit variable specified is complemented. A bit which had been a one is changed to zero and **Description:** 

vice-versa. No other flags are affected. CLR can operate on the carry or any directly addressable bit.

Note: When this instruction is used to modify an output pin, the value used as the original data will be read

from the output data latch, not the input pin.

Port 1 has previously been written with 5DH (01011101B). The instruction sequence, **Example:** 

> **CPL** P1.1 **CPL** P1.2

will leave the port set to 5BH (01011011B).

### CPL C

Bytes:

Cycles: 1

0 1 1 0 1 1 **Encoding:** 

Operation: **CPL** 

 $(c) \leftarrow (c)$ 

### CPL bit

Bytes: 2 Cycles: 1

**Encoding:** 

1	0	1	1	0	0	1	0	

bit address

Operation:

**CPL** 

(bit)  $\leftarrow$  (bit)

#### DA A

**Function:** 

Decimal-adjust Accumulator for Addition

**Description:** 

DA A adjusts the eight-bit value in the Accumulator resulting from the earlier addition of two variable (each in packed-BCD format), producing two four-bit digits. Any ADD or ADDC instruction may have been used to perform the addition.

If Accumulator bits 3-0 are greater than nine (xxx1010-xxx1111), or if the AC flag is one, six is added to the Accumulator, producing the proper BCD digit in the low-order nibble. This internal addition would set the carry flag if a carry-out of the low-order four-bit field propagated through all high-order bits, but it would not clear the carry flag otherwise.

If the carry flag is now set, or if the four high-order bits now exceed nine (1010xxx-111xxxx), these high-order bits are incremented by six, producing the proper BCD digit in the high-order nibble. Again, this would set the carry flag if there was a carry-out of the high-order bits, but wouldn't clear the carry. The carry flag thus indicates if the sum of the original two BCD variables is greater than 100, allowing multiple precision decimal addition. OV is not affected.

All of this occurs during the one instruction cycle. Essentially, this instruction performs the decimal conversion by adding 00H, 06H, 60H, or 66H to the Accumulator, depending on initial Accumulator and PSW conditions.

Note: DA A cannot simply convert a hexadecimal number in the Accumulator to BCD notation, nor does DA A apply to decimal subtraction.

#### Example:

The Accumulator holds the value 56H (01010110B) representing the packed BCD digits of the decimal number 56. Register 3 contains the value 67H (01100111B) representing the packed BCD digits of the decimal number 67. The carry flag is set.. The instruction sequence,

ADDC A,R3 DA A

will first perform a standard two's-complement binary addition, resulting in the value 0BEH (10111110B) in the Accumulator. The carry and auxiliary carry flags will be cleared.

The Decimal Adjust instruction will then alter the Accumulator to the value 24H (00100100B), indicating the packed BCD digits of the decimal number 24, the low-order two digits of the decimal sum of 56, 67, and the carry-in. The carry flag will be set by the Decimal Adjust instruction, indicating that a decimal overflow occurred. The true sum 56, 67, and 1 is 124.

BCD variables can be incremented or decremented by adding 01H or 99H. If the Accumulator initially holds 30H (representing the digits of 30 decimal), the the instruction sequence,

ADD A,#99H DA A

will leave the carry set and 29H in the Accumulator, since 30 + 99 = 129. The low-order byte of the sum can be interpreted to mean 30 - 1 = 29.

Bytes: 1

Cycles: 1

Encoding:

1 1 0 1 0 1	0 0

Operation: DA

-contents of Accumulator are BCD

IF  $[[(A_{3-0}) > 9] \lor [(AC) = 1]]$ THEN $(A_{3-0}) \leftarrow (A_{3-0}) + 6$ 

IF  $[[(A_{7-4}) > 9] \lor [(C) = 1]]$ THEN $(A_{7-4}) \leftarrow (A_{7-4}) + 6$ 

DEC	) i	ovte

Function:

Decrement

**Description:** 

The variable indicated is decremented by 1. An original value of 00H will underflow to 0FFH. No flags are affected. Four operand addressing modes are allowed: accumulator, register, direct, or register-indirect.

Note: When this instruction is used to modify an output port, the value used as the original data will be read from the output data latch, not the input pin.

Example:

Register 0 contains 7FH (01111111B). Internal RAM locations 7EH and 7FH contain 00H and 40H,

respectively. The instruction sequence,

DEC @R0 DEC R0 DEC @R0

will leave register 0 set to 7EH and internal RAM locations 7EH and 7FH set to 0FFH and 3FH.

DEC A

Bytes: 1 Cycles: 1

Encoding:

0 0 0 1 0 1 0 0

Operation:

DEC (A)  $\leftarrow$  (A) -1

DEC Rn

Bytes: 1
Cycles: 1

Encoding:

0 0 0 1 1 r r r

Operation:

 $(R_n) \leftarrow (R_n) - 1$ 

DEC

**DEC** direct

Bytes: 2 Cycles: 1

**Encoding:** 

0 0 0 1 0 1 0 1

direct address

Operation:

DEC

 $(direct) \leftarrow (direct) - 1$ 

DEC @Ri

Bytes: 1
Cycles: 1

**Encoding:** 

0 0 0 1 0 1 1 i

Operation: [

DEC

 $((\mathsf{R}_i)) \leftarrow ((\mathsf{R}_i)) - 1$ 

DIV AB

**Function:** 

Divide

**Description:** 

DIV AB divides the unsigned eight-bit integer in the Accumulator by the unsigned eight-bit integer in

register B

The Accumulator receives the integer part of the quotient; register B receives the integer remainder. The

carry and OV flags will be cleared.

Exception: if B had originally contained 00H, the values returned in the Accumulator and B-register will be

undefined and the overflow flag will be set. The carry flag is cleared in any case.

Example:

The Accumulator contains 251 (0FBH or 11111011B) and B contains 18 (12H or 00010010B). The

instruction,

DIV AB

will leave 13 in the Accumulator (0DH or 00001101B) and the value 17 (11H or 00010001B) in B, since

 $251 = (13 \times 18) + 17$ . Carry and  $\dot{OV}$  will both be cleared.

Bytes: 1

Cycles:

Encoding:

1 0 0 0 0 1 0 0

Operation:

DIV

 $(A)_{15-8} \leftarrow (A)/(B)$ 

(B)<sub>7-0</sub>

### DJNZ <byte>,<rel-addr>

Function:

Decrement and Jump if Not Zero

**Description:** 

DJNZ decrements the location indicated by 1, and branches to the address indicated by the second operand if the resulting value is not zero. An original value of 00H will underflow to 0FFH. No flags are affected. The branch destination would be computed by adding the signed relative-displacement value in the last instruction byte to the PC, after incrementing the PC to the first byte of the following instruction.

The location decremented may be a register or directly addressed byte.

Note: When this instruction is used to modify an output port, the value used as the original port data will be read from the output data latch, not the input pins.

**Example:** 

Internal RAM locations 40H, 50H, and 60H contain the values 01H, 70H, and 15H, respectively. The instruction sequence,

DJNZ 40H,LABEL\_1 DJNZ 50H,LABEL\_2 DJNZ 60H,LABEL\_3

will cause a jump to the instruction at LABEL\_2 with the values 00h, 6FH, and 15H in the three RAM locations. The first jump was *not* taken because the result was zero.

This instruction provides a simple was of executing a program loop a given number of times, or for adding a moderate time delay (from 2 to 512 machine cycles) with a single instruction. The instruction sequence,

MOV R2,# E: CPL P1.7

TOGGLE: CPL P1

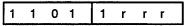
DJNZ R2,TOGGLE

will toggle P1.7 eight times, causing four output pulses to appear at bit 7 of output Port 1. Each pulse will last three machine cycles, two for DJNZ and one to alter the pin.

DJNZ Rn,rel

Bytes: 2 Cycles: 2

**Encoding:** 



rel. address

Operation:

DJNZ

 $(PC) \leftarrow (PC) + 2$   $(R_n) \leftarrow (R_n) - 1$ IF  $(R_n) > 0$  or  $(R_n) < 0$ THEN

 $(PC) \leftarrow (PC) + rel$ 

#### DJNZ direct,rel

Bytes: 3

Cycles: 2

**Encoding:** 

1	1	0	1	0	1	0	1

direct data

rel. address

Operation: DJNZ

(PC) ← (PC) + 2 (direct) ← (direct) – 1 IF (direct) > 0 or (direct) < 0 THEN (PC) ← (PC) + rel INC <byte>

**Function:** 

Increment

**Description:** 

INC increments the indicated variable by 1. An original value of 0FFH will overflow to 00H. No flags are

affected. Three addressing modes are allowed: register, direct, or register-indirect.

Note: When this instruction is used to modify an output port, the value used as the original port data will

be read from the output data latch, not the input pins.

**Example:** 

Register 0 contains 7EH (01111110B). Internal RAM locations 7EH and 7FH contain 0FFH and 40H,

respectively. The instruction sequence,

INC @R0 INC R0

INC R0 INC @R0

will leave register 0 set to 7FH and internal RAM locations 7EH and 7FH holding (respectively) 00H and

41H.

INC A

Bytes: 1 Cycles: 1

**Encoding:** 

0 0 0 0 0 1 0 0

Operation: INC

 $(A) \leftarrow (A) + 1$ 

INC Rn

Bytes: 1 Cycles: 1

Encoding: 0

0 0 0 0 1 r r r

Operation: INC

 $(R_n) \leftarrow (R_n) + 1$ 

INC direct

Bytes: 2 Cycles: 1

**Encoding:** 

0 0 0 0 0 1 0 1

direct address

Operation:

INC

 $(direct) \leftarrow (direct) + 1$ 

INC @Ri

Bytes: 1
Cycles: 1

**Encoding:** 

0 0 0 0 0 1 1 i

Operation:

INC

 $((R_i)) \leftarrow ((R_i)) + 1$ 

INC DPTR

Function: Increment Data Pointer

**Description:** Increment the 16-bit data pointer by 1. A 16-bit increment (modulo 2<sup>16</sup>) is performed; an overflow of the

low-order byte of the data pointer (DPL) from 0FFH to 00H will increment the high-order byte (DPH). No

flags are affected.

This is the only 16-bit register which can be incremented.

**Example:** Registers DPH and DPL contain 12H and 0FEH, respectively. The instruction sequence,

INC DPTR INC DPTR INC DPTR

will change DPH and DPL to 13H and 01H.

Bytes: 1

Cycles: 2

Encoding: 1 0 1 0 0 0 1 1

Operation: INC

 $(DPTR) \leftarrow (DPTR) + 1$ 

#### JB bit,ref

Function: Jump if Bit set

Description: If the indicated bit is a one, jump to the address indicated; otherwise proceed with the next instruction. The

branch destination is computed by adding the signed relative-displacement in the third instruction byte to the PC, after incrementing the PC to the first byte of the next instruction. The bit tested is not modified. No

flags are affected.

Example: The data present at input port 1 is 11001010B. The Accumulator holds 56 (01010110B). The instruction

sequence,

JB P1.2,LABEL1 JB ACC.2,LABEL2

will cause program execution to branch to the instruction at label LABEL2.

Bytes: 3

Cycles: 2

Encoding: 0 0 1 0 0 0 0 0 bit address rel. address

Operation: JB

(PC) ← (PC) + 3 IF (bit) = 1 THEN

 $(PC) \leftarrow (PC) + rel$ 

**JBC** bit,rel

Function:

Jump if Bit is set and Clear bit

**Description:** 

If the indicated bit is a one, branch to the address indicated; otherwise proceed with the next instruction. The bit will not be cleared if it is already a zero. The branch destination is computed by adding the signed relative-displacement in the third instruction byte to the PC, after incrementing the PC to the first byte of the next instruction. No flags are affected.

Note: When this instruction is used to test an output pin, the value used as the original data will read from the output data latch, not the input pin.

Example:

The Accumulator holds 56H (01010110B). The instruction sequence,

**JBC** ACC.3,LABEL1 **JBC** ACC.2,LABEL2

will cause program execution to continue at the instruction identified by the LABEL2, with the Accumulator

modified to 52H (01010010B).

Bytes: 3 2 Cycles:

**Encoding:** 

0	0	0	1	0	0	0	0	
								_

bit address

rel. address

Operation:

**JBC** 

 $(PC) \leftarrow (PC) + 3$ IF (bit) = 1THEN (bit)  $\leftarrow$  0  $(PC) \leftarrow (PC) + rel$ 

JC rel

**Function:** 

Jump if Carry is set

**Description:** 

If the carry flag is set, branch to the address indicated; otherwise proceed with the next instruction. The branch destination is computed by adding the signed relative-displacement in the second instruction byte to the PC, after incrementing the PC twice. No flags are affected.

Example:

The carry flag is cleared. The instruction sequence,

JC LABEL1 CPL C JC

will set the carry and cause program execution to continue at the instruction identified by the label

rei. address

LABEL2.

2 Bytes: 2

**Cycles:** 

Operation:

0 1 0 0 **Encoding:** 

0 0

JC  $(PC) \leftarrow (PC) + 2$ IF(C) = 1THEN

 $(PC) \leftarrow (PC) + rel$ 

0 0

#### **JMP @A+DPTR**

**Function:** 

Jump indirect

**Description:** 

Add the eight-bit unsigned contents of the Accumulator with the sixteen-bit data pointer, and load the resulting sum to the program counter. This will be the address for subsequent instruction fetches. Sixteen-bit addition is performed (modulo 216): a carry-out from the low-order eight bits propagates through the higher-order bits. Neither the Accumulator nor the Data Pointer is altered. No flags are affected.

Example:

An even number from 0 to 6 is in the Accumulator. The following sequence of instructions will branch to one of four AJMP instructions in a jump table starting at JMP\_TBL:

> MOV DPTR,#JMP\_TBL

**JMP** 

@A+DPTR

JMP\_TBL:

**AJMP** LABEL0 **AJMP** LABEL1 LABEL2

**AJMP** AJMP LABEL3

If the Accumulator equals 04H when starting this sequence, execution will jump to label LABEL2. Remember that AJMP is a two-byte instruction, so the jump instructions start at every other address.

Bytes: 1 2

Cycles:

**Encoding:** 

0 0 0 1 1 1 1 1

Operation:

**JMP** 

 $(PC) \leftarrow (A) + (DPTR)$ 

### JNB bit,rel

**Function:** 

Jump if Bit Not set

**Description:** 

If the indicated bit is a zero, branch to the indicated address; otherwise proceed with the next instruction. The branch destination is computed by adding the signed relative-displacement in the third instruction byte to the PC, after incrementing the PC to the first byte of the next instruction. The bit tested is not modified. No flags are affected.

**Example:** 

The data present at input port 1 is 11001010B. The Accumulator holds 56H (01010110B). The instruction

sequence,

JNB P1.3,LABEL1 JNB ACC.3,LABEL2

will cause program execution to continue at the instruction at label LABEL2.

Bytes: 3 2

Cycles:

**Encoding:** 

0 0 1 0 0 0 0 1

bit address

rel. address

Operation:

**JNB** 

 $(PC) \leftarrow (PC) + 3$ IF (bit) = 0THEN

 $(PC) \leftarrow (PC) + rel$ 

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JNC rel

**Function:** 

Jump if Carry Not set

**Description:** 

If the carry flag is a zero, branch to the address indicated; otherwise proceed with the next instruction. The branch destination is computed by adding the signed relative-displacement in the second instruction byte to the PC, after incrementing the PC twice to point to the next instruction. The carry flag is not modified.

**Example:** 

The carry flag is set. The instruction sequence,

JNC LABEL1 CPL C JNC LABEL2

will clear the carry and cause program execution to continue at the instruction identified by the label

ARFI 2

Bytes: 2 Cycles: 2

Encoding:

0 1 0 1 0 0 0 0

rel. address

Operation:

JNC

(PC) ← (PC) + 2 IF (C) = 0 THEN (PC) ← (PC) + rel

JNZ rel

Function:

Jump if Accumulator Not Zero

**Description:** 

If any bit of the Accumulator is a one, branch to the indicated address; otherwise proceed with the next instruction. The branch destination is computed by adding the signed relative-displacement in the second instruction byte to the PC, after incrementing the PC twice. The Accumulator is not modified. No flags are affected.

**Example:** 

The Accumulator originally holds 00H. The instruction sequence,

JNZ LABEL1 INC A JNZ LABEL2

will set the Accumulator to 01H and continue at label LABEL2.

Bytes: 2 Cycles: 2

**Encoding:** 

0 1 1 1 0 0 0 0

rel. address

Operation:

JNZ

 $(PC) \leftarrow (PC) + 2$ 

IFA≠0

THEN (PC)  $\leftarrow$  (PC) + rel

JΖ rel

**Function:** 

Jump if Accumulator Zero

**Description:** 

If all bits of the Accumulator are zero, branch to the indicated address; otherwise proceed with the next instruction. The branch destination is computed by adding the signed relative-displacement in the second instruction byte to the PC, after incrementing the PC twice. The Accumulator is not modified. No flags are affected.

**Example:** 

The Accumulator originally holds 01H. The instruction sequence,

JΖ LABEL1 DEC JZ LABEL2

will change the Accumulator to 00H and cause program execution to continue at the instruction identified

by the label LABEL2.

Bytes: 2 Cycles: 2

**Encoding:** 

1 1 0 0 0 0 rel. address

Operation:

JΖ

0

 $(PC) \leftarrow (PC) + 2$ 

IF A = 0

THEN (PC)  $\leftarrow$  (PC) + rel

#### **LCALL** addr16

**Function:** 

Long Call

**Description:** 

LCALL calls a subroutine located at the indicated address. The instruction adds three to the program counter to generate the address of the next instruction and then pushes the 16-bit result onto the stack (low byte first), incrementing the Stack Pointer by two. The high-order and low-order bytes of the PC are then loaded, respectively, with the second and third bytes of the LCALL instruction. Program execution continues with the instruction at this address. The subroutine may therefore begin anywhere in the full 64k-byte program memory address space. No flags are affected.

Example:

Initially the Stack Pointer equals 07H. The label "SUBRTN" is assigned to program memory location

1234H. After executing the instruction,

LCALL SUBRTN

at location 0123H, the Stack Pointer will contain 09H, internal RAM locations 08H and 09H will contain

26H and 01H, and the PC will contain 1235H.

Bytes: 3 Cycles: 2

**Encoding:** 

0 0 0 1 0 0 1 0

addr15-addr8

addr7-addr0

Operation:

**LCALL** 

 $(PC) \leftarrow (PC) + 3$  $(SP) \leftarrow (SP) + 1$  $((SP)) \leftarrow (PC_{7-0})$  $(SP) \leftarrow (SP) + 1$  $((SP)) \leftarrow (PC_{15-8})$  $(PC) \leftarrow addr_{15-0}$ 

LJMP addr16 (Implemented in 87C751 and 87C752 for in-circuit emulation only.)

Function: Long Jump

Description: LJMP causes an unconditional branch to the indicated address, by loading the high-order and low-order

bytes of the PC (respectively) with the second and third instruction bytes. The destination may therefore

be anywhere in the full 64k program memory address space. No flags are affected.

**Example:** The label "JMPADR" is assigned to the instruction at program memory location 1234H. The instruction,

LJMP JMPADR

at location 0123H will load the program counter with 1234H.

Bytes: 3 Cycles: 2

Encoding: 0 0 0 0 0 1 0 addr15-addr8 addr7-addr0

Operation: LJMP

 $(PC) \leftarrow addr_{15-0}$ 

## MOV <dest-byte>,<src-byte>

Function: Move byte variable

Description: The byte variable indicated by the second operand is copied into the location specified by the first

operand. The source byte is not affected. No other register or flag is affected.

This is by far the most flexible operation. Fifteen combinations of source and destination addressing

modes are allowed.

Example: Internal RAM location 30H holds 40H. The value of RAM location 40H is 10H. The data present at input

port 1 is 11001010B (0CAH). The instruction sequence,

MOV R0,#30H ;R0 < = 30H MOV A,@R0 ;A < = 40H MOV R1,A ;R1 < = 40H MOV B,@R1 ;B < = 10H

MOV @R1,P1 ;RAM (40H) < = 0CAH

MOV P2,P1 ;P2 #0CAH

leaves the value 30H in register 0, 40H in both the Accumulator and register 1, 10H in register B, and

0CAH (11001010B) both in RAM location 40H and output on port 2.

MOV A,Rn

Bytes: 1 Cycles: 1

Encoding: 1 1 1 0 1 r r r

Operation: MOV

 $(A) \leftarrow (R_n)$ 

\*MOV A, direct Bytes: 2 Cycles: 1 1 1 0 1 direct address **Encoding:** MOV Operation:  $(A) \leftarrow (direct)$ MOV A,@Ri Bytes: 1 **Cycles:** 1 1 1 0 1 0 1 1 i **Encoding:** Operation: MOV  $(A) \leftarrow ((R_i))$ MOV A,#data Bytes: 2 Cycles: 1 0 1 1 1 1 0 0 immediate data **Encoding:** Operation: MOV (A) ← #data MOV Rn,A Bytes: 1 **Cycles:** 1 1 1 r r **Encoding:** MOV Operation:  $(R_n) \leftarrow (A)$ MOV Rn, direct Bytes: 2 Cycles: 2 0 1 0 direct address  $\mathbf{r}$ **Encoding:** Operation: MOV  $(R_n) \leftarrow (direct)$ MOV Rn,#data Bytes: 2 Cycles: 0 1 1 immediate data **Encoding:** 

\*MOV A,ACC is not a valid instruction.

MOV

 $(R_n) \leftarrow \#data$ 

Operation:

# 80C51 Family

MOV direct,A Bytes: 2 Cycles: 1 1 0 1 1 1 1 0 1 direct address **Encoding:** Operation: MOV  $(direct) \leftarrow (A)$ MOV direct,Rn Bytes: 2 Cycles: 2 direct address 0 0 0 r **Encoding:** Operation: MOV  $(direct) \leftarrow \ (R_n)$ MOV direct, direct Bytes: 3 **Cycles:** 2 1 0 0 0 0 1 dir. addr. (src) dir. addr. (dest) **Encoding:** Operation: MOV  $(direct) \leftarrow (direct)$ MOV direct,@Ri **Bytes: Cycles:** 2 1 0 0 0 1 1 i direct address **Encoding:** Operation: MOV  $(direct) \leftarrow ((R_i))$ MOV direct,#data Bytes: 3 Cycles: 2 0 1 1 0 1 0 1 direct address immediate data 1 **Encoding:** Operation: MOV (direct) ← #data MOV @Ri,A 1 Bytes: Cycles: 1 1 1 1 1 0 1 1 i **Encoding:** Operation: MOV  $((R_i)) \leftarrow (A)$ 

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MOV @Ri,direct

Bytes: 2 Cycles: 2

**Encoding:** 

								-
1	0	1	0	0	1	1	i	
					_			

direct address

Operation: MOV

 $((R_i)) \leftarrow (direct)$ 

MOV @Ri,#data

Bytes: 2 Cycles: 1

**Encoding:** 

0 1 1 1 0 1 1 i

immediate data

Operation:

MOV

 $((R_i)) \leftarrow \#data$ 

### MOV <dest-bit>,<src-bit>

Function: Move bit data

Description: The Boolean variable indicated by the second operand is copied into the location specified by the first

operand. One of the operands must be the carry flag; the other may be any directly addressable bit. No

other register or flag is affected.

Example: The carry flag is originally set. The data present at input Port 3 is 11000101B. The data previously written

to output Port 1 is 35H (00110101B). The instruction sequence,

MOV P1.3,C MOV C,P3.3 MOV P1.2,C

will leave the carry cleared and change Port 1 to 39H (00111001B).

MOV C,bit

Bytes: 2

Cycles: 1

1 0 1 0 0 0 1 0

bit address

Encoding: Operation:

MOV

 $(C) \leftarrow (bit)$ 

MOV bit,C

Bytes: 2 Cycles: 2

**Encoding:** 

1 0 0 1 0 0 1 0

bit address

Operation:

MOV

 $(bit) \leftarrow (C)$ 

### MOV DPTR,#data16

Function: Lo

Load Data Pointer with a 16-bit constant

Description:

The Data Pointer is loaded with the 16-bit constant indicated. The 16-bit constant is loaded into the second and third bytes of the instruction. The second byte (DPH) is the high-order byte, while the third

byte (DPL) holds the low-order byte. No flags are affected.

This is the only instruction which moves 16 bits of data at once.

Example: The instruction,

MOV DPTR,#1234H

will load the value 1234H into the Data Pointer; DPH will hold 12H and DPL will hold 34H.

Bytes: 3
Cycles: 2

Encoding:

1 0 0 1 0 0 0 0

immed. data15-8

immed, data7-0

Operation:

MOV

 $(DPTR) \leftarrow (\#data_{15-0})$ 

DPH ☐ DPL ← #data<sub>15-8</sub>☐ #data<sub>7-0</sub>

### MOVC A,@A+<base-reg>

**Function:** 

Move Code byte

**Description:** 

The MOVC instructions load the Accumulator with a code byte, or constant from program memory. The address of the byte fetched is the sum of the original unsigned eight-bit Accumulator contents and the contents of a sixteen-bit base register, which may be either the Data Pointer or the PC. In the latter case, the PC is incremented to the address of the following instruction before being added with the Accumulator; otherwise the base register is not altered. Sixteen-bit addition is performed so a carry-out from the low-order eight bits may propagate through higher-order bits. No flags are affected.

**Example:** 

A value between 0 and 3 is in the Accumulator. The following instructions will translate the value in the Accumulator to one of four values defined by the DB (define byte) directive:

REL\_PC: INC A
MOVC A,@A+PC
RET
DB 66H
DB 77H
DB 88H
DB 99H

1 1

If the subroutine is called with the Accumulator equal to 01H, it will return with 77H in the Accumulator. The INC A before the MOVC instruction is needed to "get around" the RET instruction above the table. If several bytes of code separated the MOVC from the table, the corresponding number would be added to the Accumulator instead.

#### MOVC A,@A+DPTR

Bytes: 1

Cycles: 2

Encoding: 1 0 0 1 0 0

Operation:

MOVC

 $(A) \leftarrow ((A) + (DPTR))$ 

# 80C51 family programmer's guide and instruction set

MOVC A,@A+PC

Bytes: 1

Cycles: 2

**Encoding:** 

				_					
1	0	0	0	0	0	1	1		
		_	_						

Operation: MOVC

 $(PC) \leftarrow (PC) + 1$  $(A) \leftarrow ((A) + (PC))$ 

# MOVX <dest-byte>,<src-byte> (Not implemented in the 8XC752 or 8XC752)

Function:

Move External

Description:

The MOVX instructions transfer data between the Accumulator and a byte of external data memory, hence the "X" appended to MOV. There are two types of instructions, differing in whether they provide an eight-bit or sixteen-bit indirect address to the external data RAM.

In the first type, the contents of R0 or R1 in the current register bank provide an eight-bit address multiplexed with data on P0. Eight bits are sufficient for external I/O expansion decoding or for a relatively small RAM array. For somewhat larger arrays, port pins can be used to output higher-order address bits. These pins would be controlled by an output instruction preceding the MOVX.

In the second type of MOVX instruction, The Data Pointer generates a sixteen-bit address. P2 outputs the high-order eight address bits (the contents of DPH) while P0 multiplexes the low-order eight bits (DPL) with data. The P2 Special Function Register retains its previous contents while the P2 output buffers are emitting the contents of DPH. This form is faster and more efficient when accessing very large data arrays (up to 64k bytes), since no additional instructions are needed to set up the output ports.

It is possible in some situations to mix the two MOVX types. A large RAM array with its high-order address lines driven by P2 can be addressed via the Data Pointer, or with code to output high-order address bits to P2 followed by a MOVX instruction using R0 or R1.

**Example:** 

An external 256 byte RAM using multiplexed address/data lines is connected to the 8051 Port 0. Port 3 provides control lines for the external RAM. Ports 1 and 2 are used for normal I/O. Registers 0 and 1 contain 12H and 34H. Location 34H of the external RAM holds the value 56H. The instruction sequence,

MOVX A,@R1 MOVX @R0,A

copies the value 56H into both the Accumulator and external RAM location 12H.

### MOVX A.@Ri

Bytes: 1

Cycles: 2

Encoding: 1 1 1 0 0 0 1 i

Operation: MOVX

 $(A) \leftarrow \ ((R_i))$ 

### MOVX A,@DPTR

Bytes: 1 Cycles: 2

Encoding: 1 1 1 0 0 0 0 0

Operation: MOVX

 $(A) \leftarrow ((DPTR))$ 

# 80C51 Family

MOVX @Ri,A

Bytes: 1 Cycles: 2

Encoding:

1 1 1 1 0 0 1 i

Operation: MOVX

 $((R_i)) \leftarrow (A)$ 

MOVX @DPTR,A

Bytes: 1 Cycles: 2

Encoding:

1 1 1 1 0 0 0 0

Operation: MOVX

 $((DPTR)) \leftarrow (A)$ 

#### MUL AB

Function: Multiply

Description: MUL AB multiplies the unsigned eight-bit integers in the Accumulator and register B. The low-order byte

of the sixteen-bit product is left in the Accumulator, and the high-order byte in B. If the product is greater

than 255 (OFFH) the overflow flag is set; otherwise it is cleared. The carry flag is always cleared.

Example: Originally the Accumulator holds the value 80 (50H). Register B holds the value 160 (0A0H). The

instruction,

MUL AB

will give the product 12,800 (3200H), so B is changed to 32H (00110010B) and the Accumulator is

cleared. The overflow flag is set, carry is cleared.

Bytes: 1

Cycles: 4

**Encoding:** 

1 0 1 0 0 1 0 0

Operation: M

MUL

 $(A)_{7-0} \leftarrow (A) \times (B)$ 

 $(B)_{15-8}$ 

### NOP

Function: No Operation

Description: Execution continues at the following instruction. Other than the PC, no registers or flags are affected.

**Example:** It is desired to produce a low-going output pulse on bit 7 of Port 2 lasting exactly 5 cycles. A simple

SETB/CLR sequence would generate a one-cycle pulse, so four additional cycles must be inserted. This

may be done (assuming are enabled) with the instruction sequence,

CLR P2.7

NOP NOP

NOP

NOP SETB P2.7

SETB P2

Bytes: 1

Cycles: 1

Encoding: 0

0 0 0 0 0 0 0 0

Operation: NOP

 $(PC) \leftarrow (PC) + 1$ 

## ORL <dest-byte>,<src-byte>

Function: Logical-OR for byte variables

Description: ORL performs the bitwise logical-OR operation between the indicated variables, storing the results in the

destination byte. No flags are affected.

The two operands allow six addressing mode combinations. When the destination is the Accumulator, the source can use register, direct, register-indirect, or immediate addressing; when the destination is a direct address, the source can be the Accumulator or immediate data.

Note: When this instruction is used to modify an output port, the value used as the original port data will be read from the output data latch, not the input pine.

be read from the output data latch, not the input pins.

Example: If the Accumulator holds 0C3H (11000011B) and R0 holds 55H (01010101B) then the instruction,

ORL A,R0

will leave the Accumulator holding the value 0D7H (11010111B).

When the destination is a directly addressed byte, the instruction can set combinations of bits in any RAM location or hardware register. The pattern of bits to be set is determined by a mask byte, which may be either a constant data value in the instruction or a variable computed in the Accumulator at run-time. The

instruction,

ORL P1,#00110010B

will set bits 5, 4, and 1 of output Port 1.

ORL A,Rn.

Bytes: 1 Cycles: 1

Encoding: 0 1 0 0 1 r r r

Operation: ORL

 $(A) \leftarrow (A) \vee (R_n)$ 

# 80C51 Family

ORL A, direct Bytes: 2 Cycles: 1 0 1 0 0 0 1 0 1 direct address **Encoding:** Operation: **ORL**  $(A) \leftarrow (A) \lor (direct)$ ORL A,@Ri Bytes: **Cycles:** 1 1 0 0 0 1 1 i **Encoding:** Operation: **ORL**  $(A) \leftarrow (A) \lor ((R_i))$ ORL A,#data Bytes: 2 Cycles: 1 immediate data 1 0 0 1 0 0 **Encoding: ORL** Operation:  $(A) \leftarrow (A) \lor \#data$ ORL direct,A Bytes: 2 **Cycles:** 1 0 0 0 0 0 0 direct address 1 1 **Encoding:** Operation: **ORL**  $(direct) \leftarrow (direct) \lor (A)$ ORL direct,#data Bytes: 3 Cycles: 2 0 1 0 0 direct address immediate data **Encoding:** Operation: ORL (direct) ← (direct) ∨ #data

ORL C,<src-bit>

Function: Logical-OR for bit variables

Description: Set the carry flag if the Boolean value is a logical 1; leave the carry in its current state otherwise. A slash

("/") preceding the operand in the assembly language indicates that the logical complement of the addressed bit is used as the source value, but the source bit itself is not affected. No other flags are

affected.

**Example:** Set the carry flag if and only if P1.0 = 1, ACC.7 = 1, or OV = 0:

ORL C,P1.0 ;LOAD CARRY WITH INPUT PIN P10
ORL C,ACC.7 ;OR CARRY WITH THE ACC. BIT 7
ORL C,/OV ;OR CARRY WITH THE INVERSE OF OV.

ORL C,bit

Bytes: 2 Cycles: 2

**Encoding:** 0 1 1 1 0 0 1 0 bit address

Operation: ORL

 $(C) \leftarrow (C) \lor (bit)$ 

ORL C,/bit

Bytes: 2 Cycles: 2

Encoding: 1 0 1 0 0 0 0 0 bit address

Operation: ORL

 $(C) \leftarrow (C) \lor (\overline{bit})$ 

POP direct

**Function:** 

Pop from stack

**Description:** 

The contents of the internal RAM location addressed by the Stack Pointer is read, and the Stack Pointer is decremented by one. The value read is then transferred to the directly addressed byte indicated. No flags

are affected.

Example:

The Stack Pointer originally contains the value 32H, and internal RAM locations 30H through 32H contain

the values 20H, 23H, and 01H, respectively. The instruction sequence,

POP DPH POP DPL

will leave the Stack Pointer equal to the value 30H and the Data Pointer set to 0123H. At this point the

instruction,

POP SP

will leave the Stack Pointer set to 20H. Note that in this special case the Stack Pointer was decremented

to 2FH before being loaded with the value popped (20H).

2 Bytes: 2 Cycles:

**Encoding:** 

0 0 0 0 direct address

Operation:

POP

 $(direct) \leftarrow ((SP))$  $(SP) \leftarrow (SP) - 1$ 

#### **PUSH** direct

**Function:** 

Push onto stack

**Description:** 

The Stack Pointer is incremented by one. The contents of the indicated variable is then copied into the

internal RAM location addressed by the Stack Pointer. Otherwise no flags are affected.

Example:

On entering an interrupt routine the Stack Pointer contains 09H. The Data Pointer holds the value 0123H.

The instruction sequence,

PUSH DPL PUSH DPH

will leave the Stack Pointer set to 0BH and store 23H and 01H in internal RAM locations 0AH and 0BH.

respectively.

Bytes: 2

**Cycles:** 2

**Encoding:** 

								_
1	1	0	0	0	0	0	0	

direct address

Operation:

**PUSH** 

 $(SP) \leftarrow (SP) + 1$  $((SP)) \leftarrow (direct)$ 

### RET

**Function:** Return from subroutine

RET pops the high- and low-order bytes of the PC successively from the stack, decrementing the Stack **Description:** 

Pointer by two. Program execution continues at the resulting address, generally the instruction

immediately following an ACALL or LCALL. No flags are affected.

The Stack Pointer originally contains the value 0BH. Internal RAM locations 0AH and 0BH contain the Example:

values 23H and 01H, respectively. The instruction,

will leave the Stack Pointer equal to the value 09H. Program execution will continue at location 0123H.

Bytes: 2 Cycles:

1 0 0 0 0 0 0 1 **Encoding:** 

Operation: RET

 $(PC_{15-8}) \leftarrow ((SP))$  $(SP) \leftarrow (SP) - 1$  $(PC_{7-0}) \leftarrow ((SP))$  $(SP) \leftarrow (SP) - 1$ 

### **RETI**

Function: Return from interrupt

RETI pops the high- and low-order bytes of the PC successively from the stack, and restores the interrupt **Description:** 

logic to accept additional interrupts at the same priority level as the one just processed. The Stack Pointer is left decremented by two. No other registers are affected; the PSW is not automatically restored to its pre-interrupt status. Program execution continues at the resulting address, which is generally the instruction immediately after the point at which the interrupt request was detected. If a lower- or same-level interrupt has been pending when the RETI instruction is executed, that one instruction will be

executed before the pending interrupt is processed.

The Stack Pointer originally contains the value 0BH. An interrupt was detected during the instruction Example:

ending at location 0122H. Internal RAM locations 0AH and 0BH contain the values 23H and 01H,

respectively. The instruction,

RETI

will leave the Stack Pointer equal to 09H and return program execution to location 0123H.

Bytes: 1

Cycles: 2

0 1 **Encoding:** 

0

Operation: **RETI** 

 $(PC_{15-8}) \leftarrow ((SP))$  $(SP) \leftarrow (SP) - 1$ 

 $(PC_{7-0}) \leftarrow ((SP))$ 

 $(SP) \leftarrow (SP) - 1$ 

### RL A

Function: Rotate Accumulator Left

Description: The eight bits in the Accumulator are rotated one bit to the left. Bit 7 is rotated into the bit 0 position. No

flags are affected.

Example: The Accumulator holds the value 0C5H (11000101B). The instruction,

RL A

leaves the Accumulator holding the value 8BH (10001011B) with the carry unaffected.

Bytes: 1 Cycles: 1

Encoding: 0 0 1 0 0 0 1 1

Operation: RL

 $(A_{n+1}) \leftarrow (A_n), n = 0 - 6$ 

 $(A0) \leftarrow (A7)$ 

### RLC A

Function: Rotate Accumulator Left through the Carry flag

Description: The eight bits in the Accumulator and the carry flag are together rotated one bit to the left. Bit 7 moves into

the carry flag; the original state of the carry flag moves into the bit 0 position. No other flags are affected.

Example: The Accumulator holds the value 0C5H (11000101B), and the carry is zero. The instruction,

RLC A

leaves the Accumulator holding the value 8AH (10001010B) with the carry set.

Bytes: 1
Cycles: 1

Encoding: 0 0 1 1 0 0 1 1

Operation: RLC

 $(A_{n+1}) \leftarrow (A_n), n = 0 - 6$ 

 $(A0) \leftarrow (C)$  $(C) \leftarrow (A7)$ 

### RR A

Function: Rotate Accumulator Right

Description: The eight bits in the Accumulator are rotated one bit to the right. Bit 0 is rotated into the bit 7 position. No

flags are affected.

**Example:** The Accumulator holds the value 0C5H (11000101B). The instruction,

RR A

leaves the Accumulator holding the value 0E2H (11100010B) with the carry unaffected.

Bytes: 1 Cycles: 1

Encoding: 0 0 0 0 0 1 1

Operation: RR

 $(A_n) \leftarrow (A_{n+1}), n = 0 - 6$ 

 $(A7) \leftarrow (A0)$ 

### RRC A

Function: Rotate Accumulator Right through the Carry flag

Description: The eight bits in the Accumulator and the carry flag are together rotated one bit to the right. Bit 0 moves

into the carry flag; the original state of the carry flag moves into the bit 7 position. No other flags are

affected.

Example: The Accumulator holds the value 0C5H (11000101B), and the carry is zero. The instruction,

RRC A

leaves the Accumulator holding the value 62 (01100010B) with the carry set.

Bytes: 1 Cycles: 1

Encoding: 0 0 0 1 0 0 1 1

Operation: RRC

 $(A_n) \leftarrow (A_{n+1}), n = 0 - 6$ 

 $(A7) \leftarrow (C)$  $(C) \leftarrow (A0)$ 

# 80C51 family programmer's guide and instruction set

SETB <bit>

Function:

Set Bit

**Description:** 

SETB sets the indicated bit to one. SETB can operate on the carry flag or any directly addressable bit. No

other flags are affected.

**Example:** 

The carry flag is cleared. Output Port 1 has been written with the value 34H (00110100B). The

instructions,

SETB C SETB P1.0

will leave the carry flag set to 1 and change the data output on Port 1 to 35H (00110101B).

SETB C

Bytes:

hralan.

Cycles: 1

**Encoding:** 

1 1 0 1 0 0 1 1

Operation:

SETB

 $(C) \leftarrow 1$ 

SETB bit

Bytes: 2 Cycles: 1

**Encoding:** 

1 1 0 1 0 0 1 0

bit address

Operation:

SETB

(bit) ← 1

### SJMP rel

Function:

Short Jump

**Description:** 

Program control branches unconditionally to the address indicated. The branch destination is computed by adding the signed displacement in the second instruction byte to the PC, after incrementing the PC twice. Therefore, the range of destinations allowed is from 128 bytes preceding this instruction to 127

bytes following it.

Example:

The label "RELADR" is assigned to an instruction at program memory location 0123H. The instruction,

SJMP RELADR

will assemble into location 0100H. After the instruction is executed, the PC will contain the value 0123H.

(*Note:* Under the above conditions the instruction following SJMP will be at 102H. Therefore, the displacement byte of the instruction will be the relative offset (0123H-0102H) = 21H. Put another way, an

SJMP with a displacement of 0FEH would be a one-instruction infinite loop.)

Bytes: 2

Cycles: Encoding:

0000000

rel. address

Operation:

SJMP

2

 $(PC) \leftarrow (PC) + 2$   $(PC) \leftarrow (PC) + rel$ 

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### SUBB A, <src-byte>

**Function:** 

Subtract with borrow

**Description:** 

SUBB subtracts the indicated variable and the carry flag together from the Accumulator, leaving the result in the Accumulator. SUBB sets the carry (borrow) flag if a borrow is needed for bit 7, and clears C otherwise. (If C was set *before* executing a SUBB instruction, this indicates that a borrow was needed for the previous step in a multiple precision subtraction, so the carry is subtracted from the Accumulator along with the source operand.) AC is set if a borrow is needed for bit 3, and cleared otherwise. OV is set if a borrow is needed into bit 6, but not into bit 7, or into bit 7, but not bit 6.

When subtracting signed integers OV indicates a negative number produced when a negative value is subtracted from a positive value, or a positive result when a positive number is subtracted from a negative

number.

The source operand allows four addressing modes: register, direct, register-indirect, or immediate.

Example:

The Accumulator holds 0C9H (11001001B), register 2 holds 54H (01010100B), and the carry flag is set.

The instruction, SUBB A,R2

will leave the value 74H (01110100B) in the Accumulator, with the carry flag and AC cleared but OV set.

Notice that 0C9H minus 54H is 75H The difference between this and the above result is due to the carry (borrow) flag being set before the operation. If the state of the carry is not known before starting a single

or multiple-precision subtraction, it should be explicitly cleared by a CLR C instruction

SUBB A,Rn

Bytes: 1 Cycles: 1

Encoding:

1001 1 r r r

Operation:

SUBB

 $(A) \leftarrow (A) - (C) - (R_n)$ 

SUBB A, direct

Bytes: 2 Cycles: 1

**Encoding:** 

1 0 0 1 0 1 0 1

direct address

Operation:

SUBB

 $(A) \leftarrow (A) - (C) - (direct)$ 

SUBB A,@Ri

Bytes: 1 Cycles: 1

**Encoding:** 

1								
i	1	0	0	1	0	1	1	i
	١.	•	·	•		•		

Operation:

SUBB

**SUBB** 

 $(A) \leftarrow (A) - (C) - (R_i)$ 

SUBB A,#data

Bytes: 2 Cycles: 1

**Encoding:** 

_							
1	0	0	1	0	1	0	0

immediate data

Operation:

 $(A) \leftarrow (A) - (C) - (\#data)$ 

# 80C51 family programmer's guide and instruction set

### SWAP A

Function: Swap nibbles within the Accumulator

Description: SWAP A interchanges the low- and high-order nibbles (four-bit fields) of the Accumulator (bits 3-0 and bits

7-4). The operation can also be thought of as a four-bit rotate instruction. No flags are affected.

Example: The Accumulator holds the value 0C5H (11000101B). The instruction,

SWAP A

leaves the Accumulator holding the value 5CH (01011100B).

Bytes: 1 Cycles: 1

Encoding: 1 1 0 0 0 1 0 0

Operation: SWAP

 $(A_{3-0}) \rightleftarrows (A_{7-4})$ 

### XCH A,<byte>

Function: Exchange Accumulator with byte variable

**Description:** XCH loads the Accumulator with the contents of the indicated variable, at the same time writing the

original Accumulator contents to the indicated variable. The source/destination operand can use register,

direct, or register-indirect addressing.

Example: R0 contains the address 20H. The Accumulator holds the value 3FH (00111111B). Internal RAM location

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20H holds the value 75H (01110101B). The instruction,

XCH A,@R0

will leave the RAM location 20H holding the values 3FH (00111111B) and 75H (01110101B) in the

Accumulator.

XCH A,Rn

Bytes: 1
Cycles: 1

**Encoding:** 1 1 0 0 1 r r r

Operation: XCH

 $(A) \rightleftharpoons (R_n)$ 

XCH A, direct

Bytes: 2 Cycles: 1

Encoding: 1 1 0 0 0 1 0 1 direct address

Operation:

XCH

XCH A,@Ri

Bytes: 1 Cycles: 1

Encoding: 1 1 0 0 0 1 1 i

Operation: XCH

 $(A) \rightleftharpoons ((R_i))$ 

# 80C51 family programmer's guide and instruction set

### XCHD A,@Ri

**Function:** 

**Exchange Digit** 

Description:

XCHD exchanges the low-order nibble of the Accumulator (bits 3-0), generally representing a hexadecimal or BCD digit, with that of the internal RAM location indirectly addressed by the specified register. The high-order nibbles (bits 7-4) of each register are not affected. No flags are affected.

Example:

R0 contains the address 20H. The Accumulator holds the value 36H (00110110B). Internal RAM location

20H holds the value 75H (01110101B). The instruction,

XCHD A,@R0

will leave RAM location 20H holding the value 76H (01110110B) and 35H (00110101B) in the Accumulator.

Bytes: 1
Cycles: 1

**Encoding:** 

1 1 0 1 0 1 1 i

Operation:

XCHD

 $(A_{3-0}) \rightleftarrows ((Ri_{3-0}))$ 

### XRL <dest-byte>,<src-byte>

Function:

Logical Exclusive-OR for byte variables

**Description:** 

XRL performs the bitwise logical Exclusive-OR operation between the indicated variables, storing the results in the destination. No flags are affected.

The two operands allow six addressing mode combinations. When the destination is the Accumulator, the source can use register, direct, register-indirect, or immediate addressing; when the destination is a direct

address, the source can be the Accumulator or immediate data.

(Note: When this instruction is used to modify an output port, the value used as the original port data will

be read from the output data latch, not the input pins.)

Example:

If the Accumulator holds 0C3H (11000011B) and register 0 holds 0AAH (10101010B) then the instruction,

XRL A,R0

will leave the Accumulator holding the value 69H (01101001B).

When the destination is a directly addressed byte, this instruction can complement combinations of bits in any RAM location or hardware register. The pattern of bits to be complemented is then determined by a mask byte, either a constant contained in the instruction or a variable computed in the Accumulator at run-time. The instruction,

XRL P1,#00110001B

will complement bits 5, 4, and 0 of output Port 1.

## 80C51 family programmer's guide and instruction set

## 80C51 Family

XRL A,Rn

**Bytes:** 1 Cycles: 1

**Encoding:** 

0 1 1 0 r r r

Operation:

 $(A) \leftarrow (A) \lor (R_n)$ 

XRL A,direct

**Bytes:** 2 1 Cycles:

**Encoding:** 

0

1 0 0 1 0 1 1

direct address

Operation:

**XRL** 

 $(A) \leftarrow (A) \lor (direct)$ 

XRL A,@Ri

Bytes: 1

Cycles: 1

**Encoding:** 

0 1 1 0 0 1 1 i

Operation:

**XRL** 

 $(A) \leftarrow (A) \lor (R_i)$ 

XRL A,#data

Bytes: 2

1 Cycles:

**Encoding:** 

0 0 0 0 1 1 0 1

immediate data

Operation:

**XRL** 

 $(A) \leftarrow (A) \rightarrow \#data$ 

XRL direct,A

Bytes: 2 1

Cycles:

1 0 0

direct address

**Encoding:** Operation:

 $(direct) \leftarrow (direct) \lor (A)$ 

XRL direct,#data

3 Bytes: Cycles:

**Encoding:** 

0 1 0 0 1

direct address

immediate data

Operation:

 $(direct) \leftarrow (direct) \lor #data$ 

## APPENDIX C. DATASHEETS

The following Pages include manufacturer data sheets from the following companies:

- UTMC
  - UT69RH051
  - UT28F64
  - UT67164
- MAXIM
  - MAX 232
  - MAX 233
- Harris
  - HS-82C55ARH

# Military Standard Products UT69RH051 MicroController

**Product Brief** 



March 199

### **FEATURES**

- ☐ Three 16-bit timer/counters
  - High speed output
  - Compare/capture
  - Pulse width modulator
  - Watchdog timer capabilities
- ☐ 256 bytes of on-chip data RAM
- ☐ 32 programmable I/O lines
- ☐ 7 interrupt sources
- Programmable serial channel with:
  - Framing error detection
  - Automatic address recognition
- ☐ TTL and CMOS compatible logic levels
- ☐ 64K external data and program memory space
- ☐ MCS®-51 fully compatible instruction set

- ☐ Flexible clock operation
  - 1Hz to 20MHz with external clock
  - 2MHz to 20MHz using internal oscillator with external crystal
- ☐ Radiation-hardened process and design; total dose irradiation testing MIL-STD-883 Method 1019
  - Total dose: 1.0E6 rads(Si)
  - Single event upset: <25.6E-6 errors/device-day
  - Latchup immune
- Post-radiation AC/DC performance characteristics guaranteed to MIL-STD-883 Method 1019 testing at 1.0E6 rads (Si)
- ☐ Built on low-power, 1.2µ CMOS process
- ☐ Packaging options:
  - 40-pin DIP
  - 44-lead flatpack

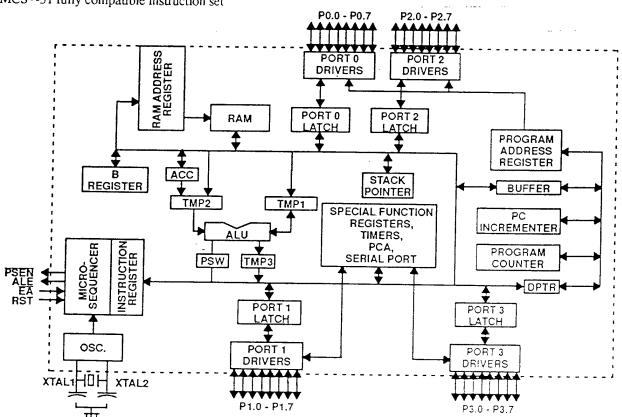


Figure 1. UT69RH051 MicroController Block Diagram

### 1.0 INTRODUCTION

The UT69RH051 is a radiation-tolerant 8-bit microcontroller that is pin equivalent to the Intel 8XC51FC microcontroller. The UT69RH051's static design allows operation from 1Hz to 20MHz. This product brief will describe hardware and software interfaces to the UT69RH051.

### 2.0 SIGNAL DESCRIPTION

V<sub>DD</sub>: +5V Supply voltage

VSS: Circuit Ground

Port 0 (P0.0 - P0.7): Port 0 is an 8-bit port. Its pins are used as the low-order multiplexed address and data bus during accesses to external program and data memory. Port 0 pins use strong internal pullups when emitting 1's, and are TTL compatible.

Port 1 (P1.0 - P1.7): Port 1 is an 8-bit bidirectional I/O port with internal pullups. The output buffers can drive TTL loads. When the Port 1 pins have 1's written to them, they are pulled high by the internal pullups and can be used as inputs in this state. As inputs, any pins that are externally pulled low will source current because of the pullups. In addition, Port 1 pins have the alternate uses shown in table 1.

Port 2 (P2.0 - P2.7): Port 2 is an 8-bit port. Its pins are used as the high-order address bus during accesses to external Program Memory and during accesses to external Data Memory that uses 16-bit addresses (i.e., MOVX@DPTR). It uses strong internal pullups when emitting 1's in this mode. During operations that do not require a 16-bit address, Port 2 emits the contents of the P2 Special Function Registers (SFR). The pins have internal pullups and can drive TTL loads.

Port 3 (p3.0 - p3.7): Port3 is an 8-bit bidirectional I/O port with internal pullups. The output buffers can drive TTL loads. When the Port 3 pins have 1's written to them, they are pulled high by the internal pullups and can be used as inputs in this state. As inputs, any pins that are externally pulled low will source current because of the pullups. In addition, Port 3 pins have the alternate uses shown in table 2.

Table 1. Port 1 Alternate Functions

Port Pin	Alternate Name	Alternate Function
P1.0	T2	External clock input to Timer/ Counter 2
P1.1	T2EX	Timer/Counter 2 Capture/Reload trigger and direction control
P1.2	ECI	External count input to PCA
P1.3	CEX0	External I/O for PCA capture/compare Module 0
P1.4	CEX1	External I/O for PCA capture/ compare Module 1
P1.5	CEX2	External I/O for PCA capture/ compare Module 2
P1.6	CEX3	External I/O for PCA capture/ compare Module 3
P1.7	CEX4	External I/O for PCA capture/ compare Module 4

Table 2. Port 3 Alternate Functions

Port Pin	Alternate Name	Alternate Function
P3.0	RXD	Serial port input
P3.1	TXD	Serial port output
P3.2	ĪNTO	External interrupt 0
P3.3	ĪNTĪ	External interrupt 1
P3.4	TO	External clock input for Timer 0
P3.5	TI	External clock input for Timer 1
P3.6	WR	External Data Memory write strobe
P3.7	RD	External Data Memory read strobe

RST: Reset Input. A high on this input for one oscillator period while the oscillator is running resets the device. All ports and SFRs reset to their default conditions. Internal data memory is undefined after reset. Program execution begins within 12 oscillator periods (one machine cycle) after the RST signal is brought low. RST contains an internal pulldown resistor to allow implementing power-up reset with only an external capacitor.

ALE: Address Latch Enable. The ALE output is a pulse for latching the low byte of the address during accesses to external memory. In normal operation the ALE pulse is output every sixth oscillator cycle and may be used for external timing or clocking. However, during each access to external Data Memory (MOVX instruction), one ALE pulse is skipped.

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**PSEN:** Program Store Enable. This active low signal is the read strobe to the external program memory. PSEN is activated every sixth oscillator cycle except that two PSEN activations are skipped during external data memory accesses.

EA: External Access Enable. This pin should be strapped to V<sub>SS</sub> (Ground) for the UT69RH051.

XTAL1: Input to the inverting oscillator amplifier.

XTAL2: Output from the inverting oscillator amplifier.

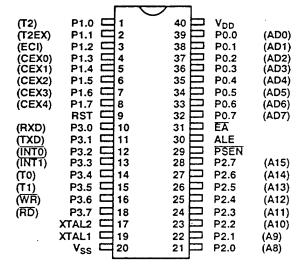


Figure 2. UT69RH051 Pin Connections

### 2.1 Hardware/Software Interface

### 2.1.1 Memory

The UT69RH051 has a separate address space for Program and Data Memory. Internally the UT69RH051 contains 256 bytes of Data Memory. It can address up to 64Kbytes of external Data Memory and 64Kbytes of external Program Memory.

### 2.1.1.1 Program Memory

There is no internal program memory in the UT69RH051. All program memory is accessed as external through ports P0 and P2. The  $\overline{EA}$  pin must be tied to  $V_{SS}$  (ground) to enable access to external locations  $0000_H$  through 7FFFH.

### 2.1.1.2 Data Memory

The UT69RH051 implements 256 bytes of internal data RAM. The upper 128 bytes of this RAM occupy a parallel address space to the SFRs. The CPU determines if the internal access to an address above 7FH is to the upper 128 bytes of RAM or to the SFR space by the addressing mode of the instruction. If direct addressing is used, the access is to the SFR space. If indirect addressing is used, the access i to the internal RAM. Stack operations are indirectly addressed so the upper portion of RAM can be used as stack space. Figure 3 shows the organization of the internal Data Memory.

The first 32 bytes are reserved for four register banks of eight bytes each. The processor uses one of the four banks as its working registers depending on the RS1 and RS0 bits in the PSW SFR. At reset, bank 0 is selected. If four registe banks are not required, use the unused banks as general purpose scratch pad memory. The next 16 bytes (128 bits) are individually bit addressable. The remaining bytes are byte addressable and can be used as general purpose scratch pad memory. For addresses 0 - 7F<sub>H</sub>, use either direct or indirect addressing. For addresses larger than 7F<sub>H</sub>, use only indirect addressing.

In addition to the internal Data Memory, the processor can access 64 Kbytes of external Data Memory. The MOVX instruction accesses external Data Memory.

### 2.1.2 Special Function Registers

Table 3 contains the SFR memory map. Unoccupied addresses are not implemented on the device. Read accesses to these addresses will return unknown values and write accesses will have no effect.

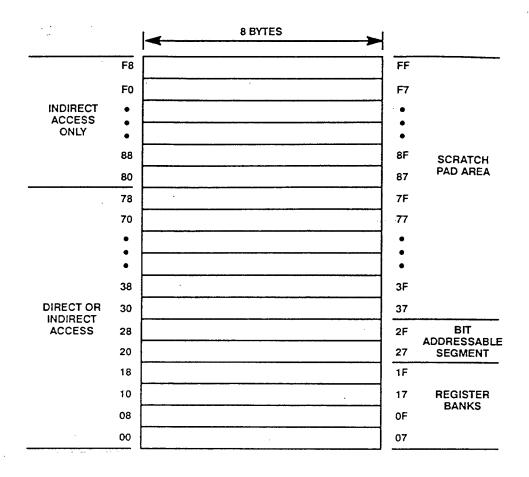


Figure 3. Internal Data Memory Organization

### 2.1.3 Reset

The reset input is the RST pin. To reset, hold a the RST pin high for a minimum of 24 oscillator period while the oscillator is running. The CPU generates an internal reset from the external signal. The ports pins are driven to the reset state as soon as a valid high is detected on the RST pin.

While RST is high, PSEN, ALE, and the port pins are pulled weakly high. All SFRs are reset to their reset values as shown in table 3. The internal Data Memory content is indeterminate.

The processor will begin operation one machine cycle after the RST line is brought low. A memory access occurs immediately after the RST line is brought low, but the data is not brought into the processor. The memory access repeats on the next machine cycle and actual processing begins at that time.

### 2.1.4 Instruction Set

The instruction set for the UT69RH051 is compatible to the Intel MCS-51 instruction set used on the 8XC51FC.

Table 3. SFR Memory Registers

à									
F8		CH 00000000	CCAP0H XXXXXXXX	CCAPIH XXXXXXXX	CCAP2H XXXXXXXX	CCAP3H XXXXXXXX	CCAP4H XXXXXXXX		FF
F0	B 00000000								F7
E8		CL 00000000	CCAP0L XXXXXXXX	CCAP1L XXXXXXXX	CCAP2L XXXXXXXX	CCAP3L XXXXXXXX	CCAP4L XXXXXXXX		EF
E0	ACC 00000000		·						E7
D8	CCON 00X00000	CMOD OOXXX000	CCAPM0 X00000000	CCAPM1 X00000000	CCAPM2 X00000000	CCAPM3 X00000000	CCAPM4 X00000000	-	DF
D0	PSW 00000000								D7
C8	T2CON 00000000	T2MOD XXXXXX00	RCAP2L 00000000	RCAP2H 00000000	TL2 00000000	TH2 00000000			CF
<b>C</b> 0									C7
B8	IP X0000000	SADEN 00000000							BF
<b>B</b> 0	P3 11111111							IPH X00000000	В7
A8	IE 00000000	SADDR 00000000							AF
<b>A</b> 0	P2 11111111								A7
98	SCON 00000000	SBUF XXXXXXXX							9F
90	P1 11111111								97
88	TCON 00000000	TMOD 00000000	TL0 00000000	TL1 00000000	TH0 00000000	TH1 00000000			8F
80	P0 11111111	SP 00000111	DPL 00000000	DPH 00000000				PCON 00XX00XX	87

- Notes:
  1. Values shown are the reset values of the registers.
  2. X = undefined.

### 3.0 RADIATION HARDNESS

The UT69RH051 incorporates special design and layout features which allow operation in high-level radiation environments. UTMC has developed special low-temperature processing techniques designed to enhance the total-dose radiation hardness of both the gate oxide and the field oxide while maintaining the

circuit density and reliability. For transient radiation hardness and latchup immunity, UTMC builds all radiation-hardened products on epitaxial wafers using an advanced twin-tub CMOS process. In addition, UTMC pays special attention to power and ground distribution during the design phase, minimizing dose-rate upset caused by rail collapse.

### RADIATION HARDNESS DESIGN SPECIFICATIONS 1

PARAMETER	CONDITION	MINIMUM	UNIT
Total Dose	+25°C per MIL-STD-883 Method 1019	1.0E6	rads(Si)
Dose Rate Upset	≤4µs pulsewidth	1.0E8	rads(Si)/sec
Dose Rate Survival	20ns pulsewidth	1.0E10	rads(Si)/sec
LET Threshold	-55°C to +125°C	36	MeV- cm <sup>2</sup> /mg
Neutron Fluence	1MeV equivalent	1.0E14	n/cm <sup>2</sup>

#### Note:

### 4.0 ABSOLUTE MAXIMUM RATINGS 1

(Referenced to  $V_{SS}$ )

SYMBOL	PARAMETER	LIMITS	UNITS
$V_{\mathrm{DD}}$	DC Supply Voltage	-0.5 to 7.0	V
$V_{\mathrm{I/O}}$	Voltage on Any Pin	-0.5 to V <sub>DD</sub> +3V	V
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C
$P_{D}$	Maximum Power Dissipation	750	mW
$T_{J}$	Maximum Junction Temperature	175	°C
$\Theta_{ m JC}$	Thermal Resistance, Junction-to-Case <sup>2</sup>	10	°C/W
II	DC Input Current	± 10	mA

### Notes:

2. Test per MIL-STD-883, Method 1012.

<sup>1.</sup> The UT69RH051 will not latchup during radiation exposure under recommended operating conditions.

<sup>1.</sup> Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions beyond limits indicated in the operational sections of this specification is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### 6.0 DC ELECTRICAL CHARACTERISTICS (Pre/Post-Radiation)\*

 $V_{DD} = 5.0V \pm 10\%$ ; TA = -55°C < T<sub>C</sub> < +125°C)

SYMBOL	PARAMETER	CONDITION	MINIMUM	MAXIMUM	UNIT
V <sub>IL</sub>	Low-level Input Voltage		-0.5	.8	V
$V_{IH}$	High-level Input Voltage (except XTAL2, RST, EA)		2.0	V <sub>DD</sub> +0.3	V
$V_{IH1}$	High-level Input Voltage (XTAL, RST)		3.85	V <sub>DD</sub> +0.3	V
V <sub>OL</sub>	Low-level Output Voltage <sup>1</sup>	$I_{OL} = 100\mu A$		0.3	V
	(Ports 1, 2 and 3)	$I_{OL} = 1.6$ mA		0.45	V
		$I_{OL} = 3.5$ mA		1.0	V
V <sub>OL1</sub>	Low-level Output Voltage <sup>1</sup>	$I_{OL} = 200\mu A$		0.3	V
	(Port 0, ALE/PROG, PSEN)	$I_{OL} = 3.2$ mA		0.45	V
		$I_{OL} = 7.0 \text{mA}$		1.0	V
V <sub>OH</sub>	High-level Output Voltage	$I_{OH} = -10\mu A$	4.2		V
	(Ports 1, 2, and 3 ALE/PROG and PSEN)	$I_{OH} = -30\mu A$	3.8		V
		$I_{OH} = -60\mu A$	3.0		,V
V <sub>OH1</sub>	High-level Output Voltage	$I_{OH} = -200 \mu A$	4.2		V
·	(Port 0 in External Bus Mode)	$I_{OH} = -3.2$ mA	3.8		V
		$I_{OH} = -7.0 \text{mA}$	3.0		V
I <sub>IL</sub>	Logical 0 Input Current (Ports 1, 2, and 3)	$V_{\rm IN} = 0.45 V$		-50	μА
I <sub>LI</sub>	Input Leakage Current (Port 0)	$V_{IN} = V_{IL}$ or $V_{IH}$		± 10	μА
$I_{TL}$	Logical 1 to 0 Transition Current (Ports 1, 2, and 3)	$V_{IN} = 2V$		-650	μА
C <sub>IO</sub>	Pin Capacitance	@ 1MHZ, 25°C		10	pF
I <sub>CC</sub>	Power Supply Current: (Running at 16MHz)	Note 2		52	mA

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Post-radiation performance guaranteed at 25°C per MIL-STD-883.

1. Under steady state (non-transient) conditions, IOL must be limited externally as follows:

Maximum I<sub>OL</sub> per port pin: Maximum I<sub>OL</sub> per 8-bit port-

10mA

Port 0:

Ports 1, 2, & 3:

26mA 15mA

Maximum total  $I_{\mbox{\scriptsize OL}}$  for all output pins:

71mA

If  $I_{OL}$  exceeds the test condition,  $V_{OL}$  may exceed the related specification. Pins are not guaranteed to sink current greater than the listed test conditions.

2. See figures 4, 5, and 6 for test conditions.

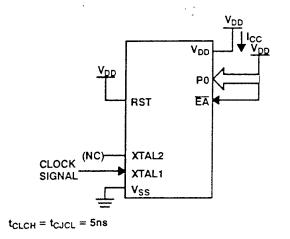


Figure 4. I<sub>DD</sub> Test Condition, Active Mode All other pins disconnected

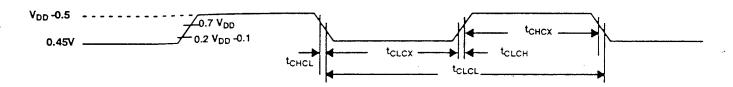


Figure 5. Clock Signal Waveform for  $I_{CC}$  Tests in Active and Idle Modes  $t_{CLCH}$  =  $t_{CHCL}$  = 5ns

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# 7.0 AC CHARACTERISTICS READ CYCLE (Post-Radiation)\* $(V_{DD} = 5.0V \pm 10\%; -55^{\circ}C < T_{C} < +125^{\circ}C)$

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SYMBOL	PARAMETER	MINIMUM	MAXIMUM	רואט
t <sub>CLCL</sub>	Clock Period	50		ns
1/t <sub>CLCL</sub>	Oscillator Frequency		16	MH
tLHILL	ALE Pulse Width	2 t <sub>CLCL</sub> -40		пѕ
t <sub>AVLL</sub>	Address Valid to ALE Low	t <sub>CLCL</sub> -40		ns
tLLAX	Address Hold after ALE Low	t <sub>CLCL</sub> -30		ns
t <sub>LLIV</sub>	ALE Low to Valid Instruction In		4 t <sub>CLCL</sub> -100	ns
tLLPL	ALE Low to PSEN Low	t <sub>CLCL</sub> -30		ns
t <sub>PLPH</sub>	PSEN Pulse Width	3 t <sub>CLCL</sub> -45		ns
t <sub>PLIV</sub>	PSEN Low to Valid Instruction In		3 t <sub>CLCL</sub> -105	ns
t <sub>PXIX</sub>	Input Instruction Hold after PSEN	0		ns
t <sub>PXIZ</sub>	Input Instruction Float After PSEN		t <sub>CLCL</sub> -25	ns
t <sub>AVIV</sub>	Address to Valid Instruction In		5 t <sub>CLCL</sub> -105	ns
tPLAZ	PSEN Low to Address Float		10	ns
tRLRH	RD Pulse Width	6 t <sub>CLCL</sub> -100		ns
twLWH	WR Pulse Width	6 t <sub>CLCL</sub> -100		ns
t <sub>RLDV</sub>	RD Low to Valid Data In		5 t <sub>CLCL</sub> -165	ns
t <sub>RHDX</sub>	Data Hold After RD	0		ns
tRHDZ	Data Float After RD		2 t <sub>CLCL</sub> -60	ns
tLLDV	ALE Low Valid Data In		8 t <sub>CLCL</sub> -150	ns
t <sub>AVDV</sub>	Address to Valid Data In		9 t <sub>CLCL</sub> -165	ns
t <sub>LLWL</sub>	ALE Low to RD or WR Low	3 t <sub>CLCL</sub> -50	3 t <sub>CLCL</sub> +50	ns
t <sub>AVWL</sub>	Address Valid to WR Low	4 t <sub>CLCL</sub> -130		ns
t <sub>QVWX</sub>	Data Valid Before WR	t <sub>CLCL</sub> -50		ns
twHQX	Data Hold After WR	t <sub>CLCL</sub> -50		ns
t <sub>QVWH</sub>	Data Valid to WR High	7 t <sub>CLCL</sub> -150		ns
t <sub>RLAZ</sub>	RD Low to Address Float		0	ns
t <sub>WHLH</sub>	· RD or WR High to ALE High	t <sub>CLCI</sub> 40	t <sub>CLCL</sub> +40	ns

Note:
• Post-radiation performance guaranteed at 25°C per MIL-STD-883 Method 1019 at 1.0E6 rads(Si).

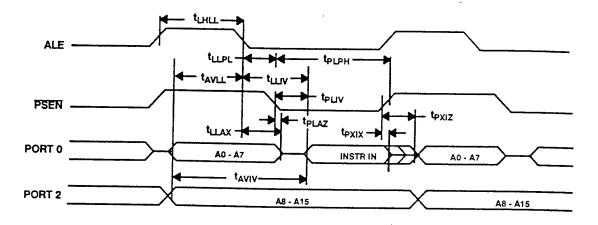


Figure 6. External Program Memory Read Timing Waveforms

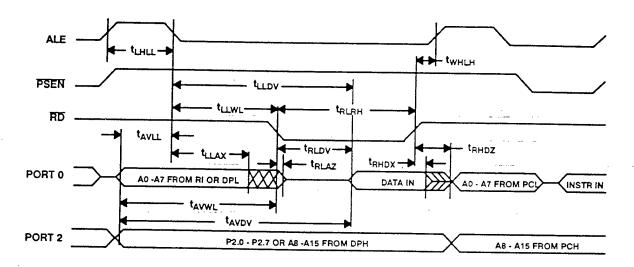


Figure 7. External Data Memory Read Cycle Waveforms

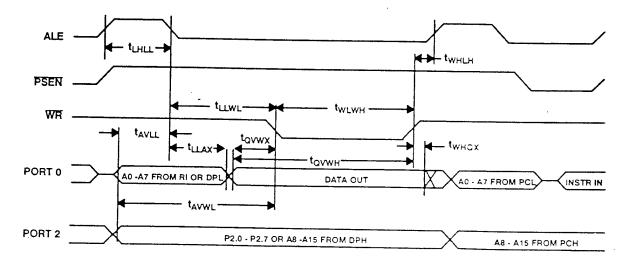


Figure 8. External Data Memory Write Cycle Waveforms

## 8.0 SERIAL PORT TIMING CHARACTERISTICS

 $(V_{DD} = 5.0V \pm 10\%; -55^{\circ}C < T_{C} < +125^{\circ}C)$ 

SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNIT
txlxl	Serial Port Clock Period	12 t <sub>CLCL</sub> -10	12 t <sub>CLCL</sub> +10	ns
tQVXH	Output Data Setup to Clock Rising Edge	10 t <sub>CLCL</sub> -133		ns
t <sub>XHQX</sub>	Output Data Hold after Clock Rising Edge	2 t <sub>CLCL</sub> -70		ns
tXHDX	Input Data Hold after Clock Rising Edge	0		ns
t <sub>XHDV</sub>	Clock Rising Edge to Input Data Valid		10 t <sub>CLCL</sub> -133	ns

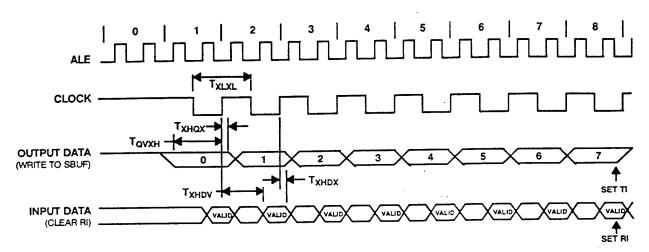


Figure 9. Serial Port Timing Waveforms

## 9.0 EXTERNAL CLOCK DRIVE TIMING CHARACTERISTICS

SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNIT
1/t <sub>CLCL</sub>	Oscillator Frequency		16	MHz
t <sub>CHCX</sub>	High Time	20		ns
tclcx	Low Time	20		ns
t <sub>CLCH</sub>	Rise Time		20	ns
<sup>‡</sup> CHCL	Fall Time		20	ns

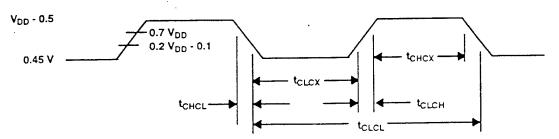


Figure 10. External Clock Drive Timing Waveforms

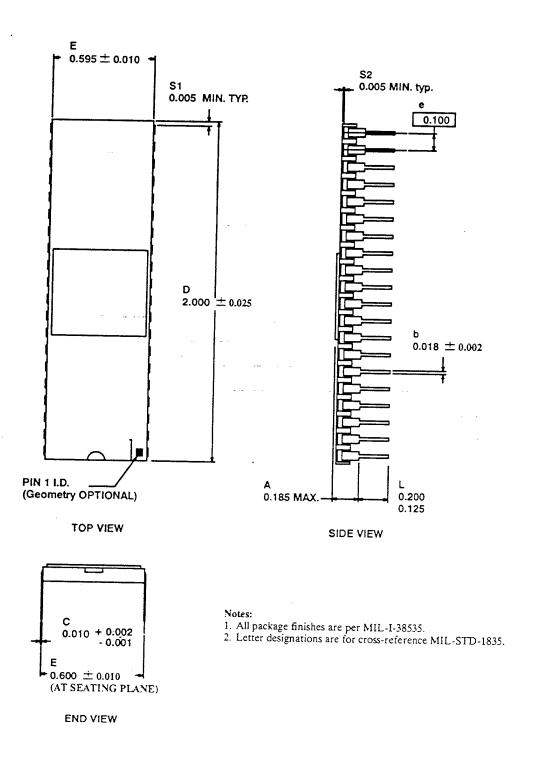


Figure 11. 40-pin Side-Brazed DIP

TBD

Figure 12. 44-Lead Flatpack

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# APPENDIX A Difference Between Intel 8XC51FC and UTMC69RH051

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There are a few areas in which the UT69RH051 differs from the 8XC51FC. These differences will be covered in this section. In this discussion, 8XC51FC will be used generically to refer to all speed grades of the Intel 8XC51FC family, including the 20MHz 8XC51FC-1.

### 1.0 RESET

The UT69RH051 requires the RST input to be held high for at least 24 oscillator periods to guarantee the reset is completed in the chip. Also, the port pins are reset asynchronously as soon as the RST pin is pulled high. On the UT69RH051 all portions of the chip are reset synchronously when the RST pin is high during a rising edge of the input clock. When coming out of reset, the 8XC51FC takes 1 to 2 machine cycles to begin driving ALE and PSEN immediately after the RST is removed but the access during the first machine cycle after reset is ignored by the processor. The second cycle will repeat the access and processing will begin.

### 2.0 POWER SAVING MODES OF OPERATION

### 2.1 Idle Mode

Idle mode and the corresponding control bit in the PCON SFR have not been implemented in the UT69RH051. Setting the idle control bit will have no effect.

### 2.2 Power Down Mode

Power down mode and the corresponding control bit in the PCON register have not been implemented in the UT69RH051. Setting the power down control bit will have no effect. Also, the Power Off Flag in the PCON has not been implemented.

### 3.0 ON CIRCUIT EMULATION

The On Circuit Emulation mode of operation in the 8XC51FC has not been implemented in the UT69RH051.

### 4.0 OPERATING CONDITIONS

The operating voltage range for the 8XC51FC is  $5V \pm 20\%$ . The operating temperature range is  $0^{\circ}$  to  $70^{\circ}$ C. On the UT69RH051, the operating voltage range is  $5V \pm 10\%$ . The operating temperature range is  $-55^{\circ}$  to  $+125^{\circ}$ C.

# APPENDIX B Impact of External Program ROM

The 8051 family of microcontrollers, including the 8XC51FC, use ports 0 and 2 to access external memory. In implementations with external program memory, these two

ports are dedicated to the program ROM interface and can not be used as Input/Output ports. The UT69RH051 uses external program ROM, so ports 0 and 2 will not be available for I/O.

Military Standard Products

# UT28F64 Radiation-Hardened 8K x 8 PROM

**Preliminary Data Sheet** 



May 1994

### **FEATURES**

□ Programmable, read-only, asynchronous, radiationhardened, 8K x 8 memory

- Supported by industry standard programmers
- ☐ 35ns maximum address access time (-55 °C to +125 °C)
- ☐ TTL/CMOS compatible input and output levels
- ☐ Three-state data bus
- Low operating and standby current
  - Operating: 140mA maximum @28.5MHz
  - Standby: 1mA maximum (post-rad)
  - Derating: 5mA/MHz
- ☐ Radiation-hardened process and design; total dose irradiation testing to MIL-STD-883, Method 1019
  - Total dose: 1.0E6 rads(Si)
  - Single event effects: Latchup threshold 80 MeV-cm<sup>2</sup>/mg (min)
  - Dose rate upset: 1.0E8 rads(Si)/sec
  - Dose rate survival: 1.0E10 rads(Si)/sec
  - Neutron fluence: 1.0E14 n/cm<sup>2</sup>

- ☐ QML Q & V compliant part (check factory for availability)
  - AC and DC testing at factory

- Packaging options:
  - 28-pin 100-mil center DIP (0.600 x 1.4)
  - 28-lead 50-mil center flatpack (0.700 x 0.75)
  - 28-lead 50-mil center flatpack (0.490 x 0.74)
- $\square$  V<sub>DD</sub>: 5.0 volts  $\pm 10\%$

### PRODUCT DESCRIPTION

The UT28F64 amorphous silicon anti-fuse PROM is a high performance, asynchronous, radiation-hardened, 8K x 8 programmable memory device. The UT28F64 PROM features fully asychronous operation requiring no external clocks or timing strobes. An advanced radiation-hardened twin-well CMOS process technology is used to implement the UT28F64. The combination of radiation-hardness, fast access time, and low power consumption make the UT28F64 ideal for high speed systems designed for operation in radiation environments.

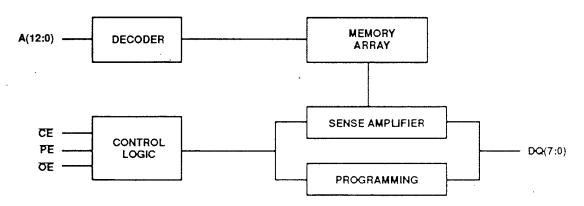
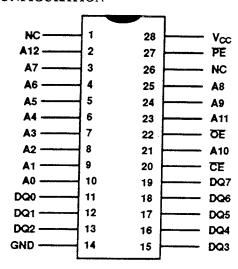


Figure 1. PROM Block Diagram

### **DEVICE OPERATION**

The UT28F64 has three control inputs: Chip Enable ( $\overline{\text{CE}}$ ), Program Enable ( $\overline{\text{PE}}$ ), and Output Enable ( $\overline{\text{OE}}$ ); thirteen address inputs, A(12:0); and eight bidirectional data lines, DQ(7:0).  $\overline{\text{CE}}$  is the device enable input that controls chip selection, active, and standby modes. Asserting  $\overline{\text{CE}}$  causes  $I_{DD}$  to rise to its active value and decodes the fifteen address inputs to select one of 8,192 words in the memory.  $\overline{\text{PE}}$  controls program and read operations. During a read cycle,  $\overline{\text{OE}}$  must be asserted to enable the outputs.

### PIN CONFIGURATION



### PIN NAMES

A(12:0)	Address
CE	Chip Enable
ŌĒ	Output Enable
PE	Program Enable
DQ(7:0)	Data Input/Data Output

Table 1. Device Operation Truth Table 1

ŌĒ	PE	CE	I/O MODE	MODE
X	1	1	Three-state	Standby
0	1	0	Data Out	Read
1	0	0	Data In	Program
1	1	0	Three-state	Read <sup>2</sup>

#### Notes:

- 1. "X" is defined as a "don't care" condition.
- 2. Device active; outputs disabled.

### ABSOLUTE MAXIMUM RATINGS 1

(Referenced to VSS)

SYMBOL	PARAMETER	LIMITS	UNITS
$V_{ m DD}$	DC supply voltage	-0.3 to 7.0	V
$V_{\mathrm{I/O}}$	Voltage on any pin	$-0.5$ to $(V_{DD} + 0.5)$	V
$T_{STG}$	Storage temperature	-65 to +150	°C
$P_{D}$	Maximum power dissipation	1.5	W
$T_{\mathbf{J}}$	Maximum junction temperature	+175	°C
$\Theta_{ m JC}$	Thermal resistance, junction-to-case <sup>2</sup>	10	°C/W
$I_{\mathfrak{l}}$	DC input current	± 10	mA

### Notes:

1. Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions beyond limits indicated in the operational sections of this specification is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS	UNITS
$V_{\mathrm{DD}}$	Positive supply voltage	4.5 to 5.5	V
$T_{C}$	Case temperature range	-55 to +125	°C
V <sub>IN</sub>	DC input voltage	0 to V <sub>DD</sub>	V

### DC ELECTRICAL CHARACTERISTICS (Pre/Post-Radiation)\*

 $(V_{DD} = 5.0V \pm 10\%; -55^{\circ}C < T_{C} < +125^{\circ}C)$ 

SYMBOL	PARAMETER	CONDITION	MINIMUM	MAXIMUM	UNIT
V <sub>IH</sub>	High-level input voltage	(CMOS)	3.5		V
$V_{IH}$	High-level input voltage	(TTL)	2.2		V
$V_{IL}$	Low-level input voltage	(CMOS)		1.5	V
$V_{IL}$	Low-level input voltage	(TTL)		0.8	V
V <sub>OL</sub>	Low-level output voltage	$I_{OL} = 200\mu A, V_{DD} = 4.5V$ (CMOS)		$V_{SS} + 0.05$	V
$V_{OL}$	Low-level output voltage	$I_{OL} = 4.0 \text{mA}, V_{DD} = 4.5 \text{V} (TTL)$		0.4	V
V <sub>OH</sub>	High-level output voltage	$I_{OH} = -200 \mu A, V_{DD} = 4.5 V$ (CMOS)	V <sub>DD</sub> - 0.05		V -
$V_{OH}$	High-level output voltage	$I_{OH} = -400 \mu A, V_{DD} = 4.5 V (TTL)$	2.4		V
C <sub>IN</sub> <sup>1</sup>	Input capacitance	$f = 1 \text{MHz} @ 0 \text{V}, V_{\text{DD}} = 4.5 \text{V}$		15	pF
C <sub>IO</sub> <sup>1</sup>	Bidirectional I/O capacitance	$f = 1 \text{MHz} @ 0 \text{V}, V_{\text{DD}} = 4.5 \text{V}$		20	pF
$I_{IN}$	Input leakage current	$V_{IN} = V_{DD}$ and $V_{SS}$	-10	10	μΑ
I <sub>OZ</sub>	Three-state output leakage current	$V_O = V_{DD}$ and $V_{SS}$ $V_{DD} = 5.5V$ $\overline{OE} = 5.5V$	-10	10	μΑ
I <sub>OS</sub> <sup>2,3</sup>	Short-circuit output current	$V_{DD} = 5.5V, V_{O} = V_{DD}$ $V_{DD} = 5.5V, V_{O} = 0V$	-90	90	mA mA
I <sub>DD</sub> (OP) <sup>4</sup>	Supply current operating @28.5MHz	CMOS inputs (i.e., $I_{OUT} = 0$ ) $V_{DD} = 5.5V$		140	mA
I <sub>DD</sub> (SB) pre-rad	Supply current standby	CMOS inputs (i.e., $I_{OUT} = 0$ ) $\overline{CE} = V_{DD} - 0.5$ , $V_{DD} = 5.5V$		100	μА
I <sub>DD</sub> (SB) post-rad	Supply current standby	CMOS inputs (i.e., $I_{OUT} = 0$ ) $\overline{CE} = V_{DD} - 0.5$ , $V_{DD} = 5.5V$		1	mA

- Notes:

  \* Post-radiation performance guaranteed at 25°C per MIL-STD-883 Method 1019 at 1.0E6 rads(Si).

  1. Measured only for initial qualification, and after process or design changes that could affect input output capacitance.

  2. Supplied as a design limit but not guaranteed or tested.

  3. Not more than one output may be shorted at a time for maximum duration of one second.

  4. Guaranteed by device characterization.

### READ CYCLE

A combination of  $\overline{PE}$  greater than  $V_{III}(min)$ , and  $\overline{CE}$  less than  $V_{III}(max)$  defines a read cycle. Read access time is measured from the latter of device enable, output enable, or valid address to valid data output.

An address access read is initiated by a change in address inputs while the chip is enabled with  $\overline{OE}$  asserted and  $\overline{PE}$  deasserted. Valid data appears on data output, DQ(7:0), after the specified  $t_{AVQV}$  is satisfied. Outputs remain active throughout the entire cycle. As long as device enable and output enable are active, the address inputs may change at a rate equal to the minimum read cycle time.

The chip enable-controlled access is initiated by  $\overline{CE}$  goir active while  $\overline{OE}$  remains asserted,  $\overline{PE}$  remains deasserte and the addresses remain stable for the entire cycle. After the specified  $t_{ELQV}$  is satisfied, the eight-bit word address by A(12:0) is accessed and appears at the data outputs DQ(7:0).

Output enable-controlled access is initiated by  $\overline{OE}$  going active while  $\overline{CE}$  is asserted,  $\overline{PE}$  is deasserted, and the addresses are stable. Read access time is  $t_{GLQV}$  unless  $t_{AVQV}$  or  $t_{ELQV}$  have not been satisfied.

# AC CHARACTERISTICS READ CYCLE (Post-Radiation)\* $(V_{DD} = 5.0V \pm 10\%; -55^{\circ}C < T_{C} < +125^{\circ}C)$

SYMBOL	PARAMETER	28F	64-35	28F	64-45	UNII
		MIN	MAX	MIN	MAX	
t <sub>AVAV</sub>	Read cycle time	35		45		ns
t <sub>AVQV</sub>	Read access time		35		45	ns
t <sub>AXQX</sub>	Output hold time	0		0		ns
t <sub>GLQX</sub>	OE-controlled output enable time	0		0		ns
t <sub>GLQV</sub>	OE-controlled output enable time		15		20	ns
t <sub>GHQZ</sub>	OE-controlled output three-state time		15		- 20	ns
<sup>t</sup> ELQX	CE-controlled output enable time	0		0		ns
t <sub>ELQV</sub>	CE-controlled access time		35		45	ns
t <sub>EHQZ</sub>	CE-controlled output three-state time		15		20	ns

### Notes:

<sup>\*</sup> Post-radiation performance guaranteed at 25°C per MIL-STD-883 Method 1019 at 1.0E6 rads(Si).

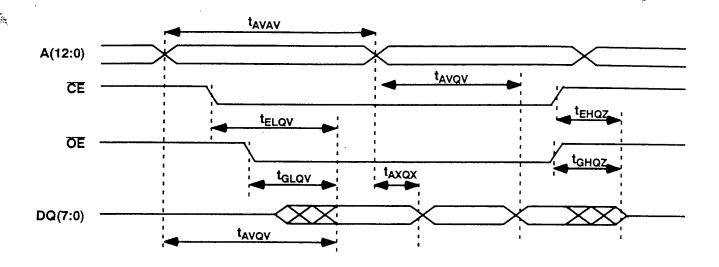


Figure 2. PROM Read Cycle

### **RADIATION HARDNESS**

The UT28F64 PROM incorporates special design and layout features which allow operation in high-level radiation environments. UTMC has developed special low-temperature processing techniques designed to enhance the total-dose radiation hardness of both the gate oxide and the field oxide while maintaining the

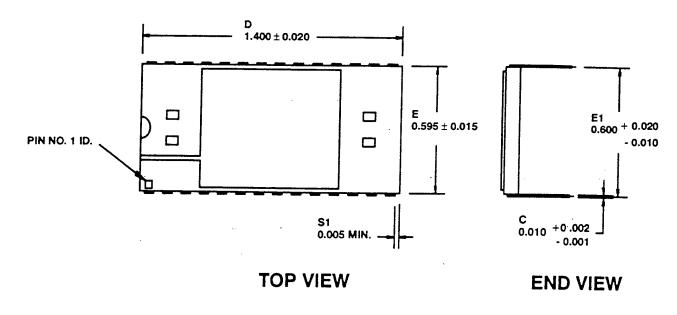
circuit density and reliability. For transient radiation hardness and latchup immunity, UTMC builds all radiation-hardened products on epitaxial wafers using an advanced twin-tub CMOS process. In addition, UTMC pays special attention to power and ground distribution during the design phase, minimizing dose-rate upset caused by rail collapse.

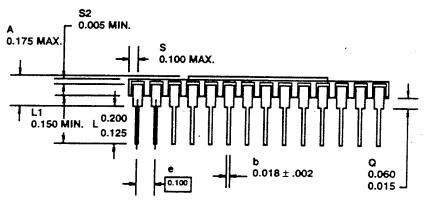
### RADIATION HARDNESS DESIGN SPECIFICATIONS 1

PARAMETER	CONDITION	MINIMUM	UNIT
Total Dose	+25°C per MIL-STD-883 Method 1019	1.0E6	rads(Si)
Dose Rate Upset	≤ 4µs pulsewidth	1.0E8	rads(Si)/sec
Dose Rate Survival	20ns pulsewidth	1.0E10	rads(Si)/sec
LET Threshold	-55°C to +125°C	80	MeV-cm <sup>2</sup> /mg
Neutron Fluence	1MeV equivalent	1.0E14	n/cm <sup>2</sup>

### Notes:

1. The PROM will not latchup during radiation exposure under recommended operating conditions.



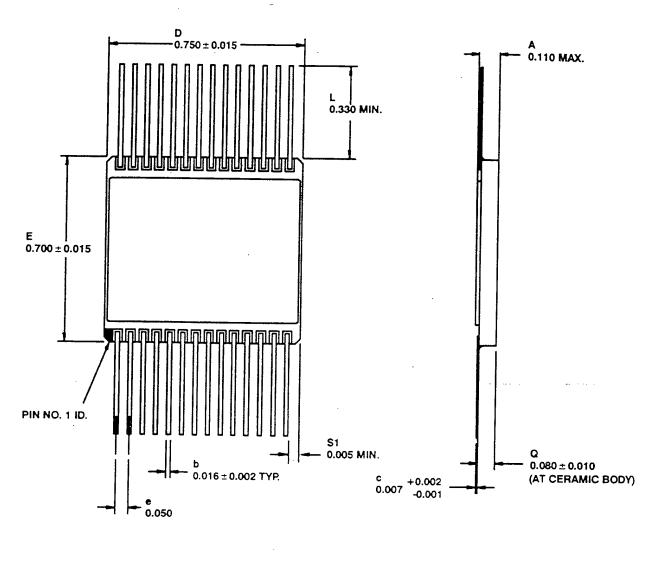


SIDE VIEW

### Notes:

- 1. Seal ring to be electrically isolated.
- 2. All exposed metalized areas to be plated per MIL-I-38535.
- 3. Ceramic to be opaque.
- 4. Dimension letters refer to MIL-STD-1835.

Figure 3. 28-Pin 100-mil Center DIP (0.600 x 1.4)

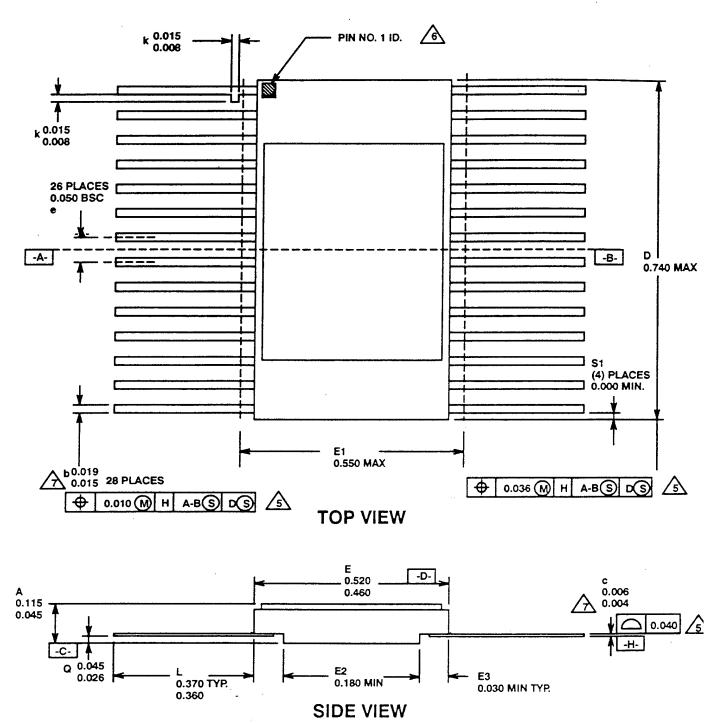


**TOP VIEW** 

SIDE VIEW

- Notes:
  1. Seal ring to be electrically isolated.
  2. All exposed metalized areas to be plated per MIL-I-38535.
  3. Ceramic to be opaque.
  4. Dimension letters refer to MIL-STD-1835.

Figure 4. 28-Lead 50-mil Center Flatpack (0.700 x 0.75)



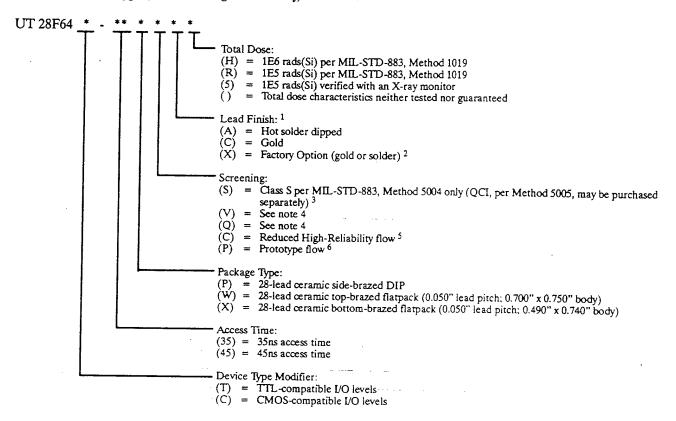
- 1. All exposed metalized areas are gold plated over electroplated nickle per MIL-M-38510.
- 2. The lid is electrically connected to VSS.
- 3. Lead finishes are in accordance with MIL-I-38535.
- 4. Dimension letters refer to MIL-STD-1835.
- Lead position and coplanarity are not measured. ID mark symbol is vendor option. With solder, increase maximum by 0.003.

Figure 5. 28-Lead 50-mil Center Flatpack (0.490 x 0.74)

### ORDERING INFORMATION



### 64K PROM: Prototypes, Reduced High-Reliability, & Class S



### Notes:

1. Lead finish (A,C, or X) must be specified.

2. If an "X" is specified, part marking will match the lead finish and will be either "A" (solder) or "C" (gold).

3. Total dose must be specified. (Not available without radiation hardening.)

This device will be offered as a MIL-I-38535 QML Q, QML V, or SMD device. Anticipated availability is 3Q94. Please contact UTMC for the correct part number and ordering information.

5. Reduced High-Reliability flow per UTMC Manufacturing Flows Technical Description. Devices have 48 hours of burn-in and are tested at -55°C, room temperature, and 125°C. Radiation characteristics are neither tested nor guaranteed and may not be specified.

6. Prototype flow per UTMC Manufacturing Flows Technical Description. Devices have prototype assembly and are tested at 25°C only. Radiation characteristics are neither tested nor guaranteed and may not be specified. Lead finish is at UTMC's option and an "X" must be specified when ordering.

# UT67164 Radiation-Hardened 8K x 8 SRAM -- SEU Hard Data Sheet



February 1992

### **FEATURES**

- ☐ 55ns maximum address access time, single-event upset less than 1.0E-10 errors/bit-day (-55°C to +125°C)
- ☐ Asynchronous operation for compatibility with industry-standard 8K x 8 SRAM
- ☐ TTL-compatible input and output levels
- ☐ Three-state bidirectional data bus
- ☐ Low operating and standby current
- ☐ Full military operating temperature range, -55°C to +125°C, screened to specific test methods listed in Table I MIL-STD-883 Method 5004 for Class S or Class B
- ☐ Radiation-hardened process and design; total dose irradiation testing to MIL-STD-883 Method 1019
  - Total-dose: 1.0E6 rads (Si)
  - Dose rate upset: 1.0E9 rads (Si)/sec
  - Dose rate survival: 1.0E12 rads (Si)/sec
  - Single-event upset: <1.0E-10 errors/bit-day
- ☐ Industry standard (JEDEC) 64K SRAM pinout
- ☐ Packaging options:
  - 28-pin 100-mil center DIP (.600 x 1.2)
  - 28-pin 50-mil center flatpack (.700 x .75)
- ☐ 5-volt operation
- ☐ Post-radiation AC/DC performance characteristics guaranteed by MIL-STD-883 Method 1019 testing at 1.0E6 rads(Si)

### INTRODUCTION

The UT67164 SRAM is a high performance, asynchronous, radiation-hardened, 8K x 8 random access memory conforming to industry-standard fit, form, and function. The UT67164 SRAM features fully static operation requiring no external clocks or timing strobes. UTMC designed and implemented the UT67164 SRAM using an advanced radiation-hardened twin-well CMOS process. Advanced CMOS processing along with a device enable/disable function result in a high performance, power-saving SRAM. The combination of radiation-hardness, fast access time, and low power consumption make UT67164 ideal for high-speed systems designed for operation in radiation environments.

### **PIN NAMES**

A(12:0)	Address	W	Write
DQ(7:0)	Data Input/Output	G	Output Enable
E1	Enable 1	$V_{DD}$	Power
E2	Enable 2	V <sub>SS</sub>	Ground

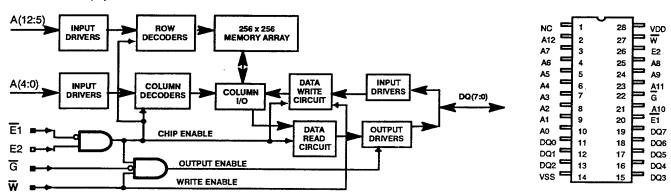


Figure 1. SRAM Block Diagram

Figure 2. SRAM Pinout

#### DEVICE OPERATION

The UT67164 has four control inputs called Enable 1 ( $\overline{E1}$ ), Enable 2 (E2), Write Enable ( $\overline{W}$ ), and Output Enable ( $\overline{G}$ ); thirteen address inputs, A(12:0); and eight bidirectional data lines, DQ(7:0).  $\overline{E1}$  and E2 are device enable inputs that control device selection, active, and standby modes. Asserting both  $\overline{E1}$  and E2 enables the device, causes IDD to rise to its active value, and decodes the thirteen address inputs to select one of 8,192 words in the memory.  $\overline{W}$  controls read and write operations. During a read cycle,  $\overline{G}$  must be asserted to enable the outputs.

**Table 1. Device Operation Truth Table** 

G	$\overline{\mathbf{w}}$	ĒĪ	E2	I/O Mode	Mode
X 1	X	X	0	3-state	Stand-by
X	X	1	X	3-state	Stand-by
X	0	0	1	Data in	Write
1	1	0	1	3-state	Read <sup>2</sup>
0	1	0	1	Data out	Read

#### Notes:

- 1. "X" is defined as a "don't care" condition.
- 2. Device active; outputs disabled.

### READ CYCLE

A combination of  $\overline{W}$  greater than  $V_{IH}(min)$ ,  $\overline{E1}$  less than  $V_{IL}(max)$ , and E2 greater than  $V_{IH}(min)$  defines a read cycle. Read access time is measured from the latter of device enable, Output Enable, or valid address to valid data output.

Read Cycle 1, the Address Access read in figure 3a, is initiated by a change in address inputs while the chip is enabled with  $\overline{G}$  asserted and  $\overline{W}$  deasserted. Valid data appears on data outputs DQ(7:0) after the specified  $t_{AVQV}$  is satisfied. Outputs remain active throughout the entire cycle. As long as device enable and output enable are active, the address inputs may change at a rate equal to the minimum read cycle time  $(t_{AVAV})$ .

Figure 3b shows Read Cycle 2, the Chip Enable-controlled Access. For this cycle,  $\overline{G}$  remains asserted,  $\overline{W}$  remains deasserted, and the addresses remain stable for the entire cycle. After the specified  $t_{\text{ETQV}}$  is satisfied, the eight-bit word addressed by A(12:0) is accessed and appears at the data outputs DQ(7:0).

Figure 3c shows Read Cycle 3, the Output Enable-controlled Access. For this cycle,  $\overline{E1}$  and E2 are asserted,  $\overline{W}$  is deasserted, and the addresses are stable before  $\overline{G}$  is enabled. Read access time is  $t_{GLQV}$  unless  $t_{AVOY}$  or  $t_{ETOY}$  have not been satisfied.

### WRITE CYCLE

A combination of  $\overline{W}$  less than  $V_{IL}(max)$ ,  $\overline{E1}$  less than  $V_{IL}(max)$ , and E2 greater than  $V_{IH}(min)$  defines a write cycle. The state of  $\overline{G}$  is a "don't care" for a write cycle. The outputs are placed in the high-impedance state when either  $\overline{G}$  is greater than  $V_{IH}(min)$ , or when W is less than  $V_{II}(max)$ .

Write Cycle 1, the Write Enable-controlled Access shown in figure 4a, is defined by a write terminated by  $\overline{W}$  going high, with  $\overline{E1}$  and E2 still active. The write pulse width is defined by  $t_{WLWH}$  when the write is initiated by  $\overline{W}$ , and by  $t_{ETWH}$  when the write is initiated by the latter of  $\overline{E1}$  or E2. Unless the outputs have been previously placed in the high-impedance state by  $\overline{G}$ , the user must wait  $t_{WLQZ}$  before applying data to the eight bidirectional pins DQ(7:0) to avoid bus contention.

Write Cycle 2, the Chip Enable-controlled Access shown in figure 4b, is defined by a write terminated by the latter of  $\overline{E1}$  or E2 going inactive. The write pulse width is defined by  $t_{WLEF}$  when the write is initiated by  $\overline{W}$ , and by  $t_{ETEF}$  when the write is initiated by the latter of  $\overline{E1}$  or E2 going active. For the  $\overline{W}$  initiated write, unless the outputs have been previously placed in the high-impedance state by  $\overline{G}$ , the user must wait  $t_{WLQZ}$  before applying data to the eight bidirectional pins DQ(7:0) to avoid bus contention.

### **RADIATION HARDNESS**

The UT67164 SRAM incorporates special design and layout features which allow operation in high-level radiation environments. UTMC has developed special low-temperature processing techniques designed to enhance the total-dose radiation hardness of both the gate oxide and the field oxide while maintaining the circuit density and reliability. For transient radiation hardness and latchup immunity, UTMC builds all radiation-hardened products on epitaxial wafers using an advanced twin-tub CMOS process. In addition, UTMC pays special attention to power and ground distribution during the design phase, minimizing dose-rate upset caused by rail collapse.

### Table 2. Radiation Hardness Design Specifications <sup>1</sup>

Total Dose	1.0E6	rads(Si)
Dose Rate Upset	1.0E9	rads(Si)/s 20ns pulse
Dose Rate Survival	1.0E12	rads(Si)/s 20ns pulse
Single-Event Upset	1.0E-10	errors/bit-day <sup>2</sup>
Neutron Fluence	3.0E14	n/cm²

#### Notes:

- The SRAM will not latch up during radiation exposure under recommended operating conditions.
- 2. 90% Adam's worst case spectrum (-55°C to +125°C).

### 10-4 10-6 10-18 10-10 10-13 10-13 10-13 10-10 10-10

5 25 45

-55 -35 -15

Table 3. SEU versus Temperature

Temperature (°C)

65 85 105 125

# ABSOLUTE MAXIMUM RATINGS <sup>1</sup> (Referenced to Vss)

SYMBOL	PARAMETER	LIMITS
$V_{\mathrm{DD}}$	DC supply voltage	-0.5 to 7.0
$V_{\rm I/O}$	Voltage on any pin	-0.5 to V <sub>DD</sub> + 0.5
$T_{STG}$	Storage temperature	-65 to +150°C
$P_{\mathrm{D}}$	Maximum power dissipation	1.0 W
$T_{J}$	Maximum junction temperature	+150°C
$\Theta_{ m JC}$	Thermal resistance, junction-to-case <sup>2</sup>	10°C/W
$I_{ m LU}$	Latchup immunity (see figure 6b)	+/- 150 mA
II	DC input current	+/- 10 mA

### Notes:

2. Test per MIL-STD-883, Method 1012.

### RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS	UNITS
$V_{\mathrm{DD}}$	Positive supply voltage	4.5 to 5.5	V
T <sub>C</sub>	Case temperature range	-55 to +125	°C
V <sub>IN</sub>	DC input voltage	0 to V <sub>DD</sub>	V

<sup>1.</sup> Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions beyond limits indicated in the operational sections of this specification is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS (Post-Radiation)\*

 $(V_{DD} = 5.0V + /-10\%; -55^{\circ}C < Tc < +125^{\circ}C)$ 

SYMBOL	PARAMETER	CONDITION	MINIMUM	MAXIMUM	UNIT
$V_{IH}$	High-level input voltage		2.2		V
$V_{\mathrm{IL}}$	Low-level input voltage			0.8	V
$V_{OL}$	Low-level output voltage	$I_{OL} = +/-4.0 \text{ mA}, V_{DD} = 4.5 \text{V}$		0.4	V
V <sub>OH</sub>	High-level output voltage	$I_{OH} = +/-4.0$ mA, $V_{DD} = 4.5$ V	2.4		V
C <sub>IN</sub>	Input capacitance 1	$F = 1MHz @ 0V, V_{DD} = 4.5V$		15	pF
Co	Bidirectional I/O capacitance <sup>1</sup>	$F = 1MHz @ 0V, V_{DD} = 4.5V$		20	pF
$I_{IN}$	Input leakage current	$V_{IN} = V_{DD}$ and $V_{SS}$	-10	10	μΑ
I <sub>OZ</sub>	Three-state output leakage current TTL outputs	$V_O = V_{DD}$ and $V_{SS}$ $V_{DD} = 5.5V$ $\overline{G} = 5.5V$	-10	10	μА
I <sub>OS</sub>	Short-circuit output current <sup>2,3</sup>	$V_{DD} = 5.5V, V_{O} = V_{DD}$ $V_{DD} = 5.5V, V_{O} = 0V$	-90	90	mA mA
I <sub>DD</sub> (OP)	Supply current operating @1MHz	CMOS inputs (i.e., $I_{OUT} = 0$ ) $V_{DD} = 5.5V$		40	mA
I <sub>DD</sub> (SB) pre-rad	Supply current standby	CMOS inputs (i.e., $I_{OUT} = 0$ ) $\overline{E1} = V_{DD} - 0.5 V_{DD} = 5.5V$ $E2 = V_{SS} + 0.5$		200	μА
I <sub>DD</sub> (SB) post-rad	Supply current standby  @ f = 0Hz	CMOS inputs (i.e., $I_{OUT} = 0$ ) CS1 = negated $V_{DD} = 5.5 V$ CS2 = negated		3	mA

## Notes:

- 1. Measured only for initial qualification, and after process or design changes that could affect input/output capacitance.
- 2. Supplied as a design limit but not guaranteed or tested.
- 3. Not more than one output may be shorted at a time for maximum duration of one second.
- \* Post-radiation performance guaranteed at 25°C per MIL-STD-883 Method 1019 at 1.0E6 rads(Si).

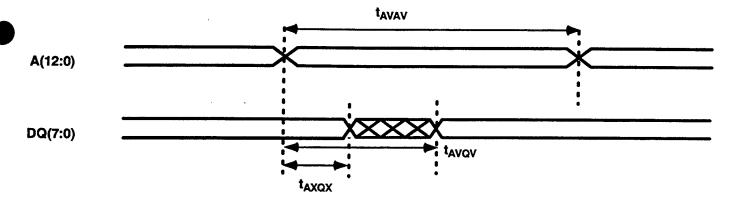
## AC CHARACTERISTICS READ CYCLE (Post-Radiation)\*

 $(VDD = 5.0V + /-10\%; -55^{\circ}C < TC < +125^{\circ}C)$ 

GYD 4DOX			64-85	6716	4-70	6716	4-55	
SYMBOL	PARAMETER	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
t <sub>AVAV</sub>	Read cycle time	85		70		55		ns
t <sub>AVQV</sub>	Read access time		85		70		55	ns
t <sub>AXQX</sub>	Output hold time	5		5		5		ns
tGLOX	G-controlled output enable time	0		0		0		ns
tGLOV	G-controlled output enable time (Read Cycle 3)		30		15		15	ns
t <sub>GHQZ</sub>	G-controlled output three-state time		15		15		15	ns
t <sub>ETQX</sub> 1	E-controlled output enable time	0		0		0		ns
tetqv <sup>1</sup>	E-controlled access time		85		70		55	ns
t <sub>EFQZ</sub> <sup>2</sup>	E-controlled output three-state time <sup>3</sup>		25		20		20	ns

## Notes:

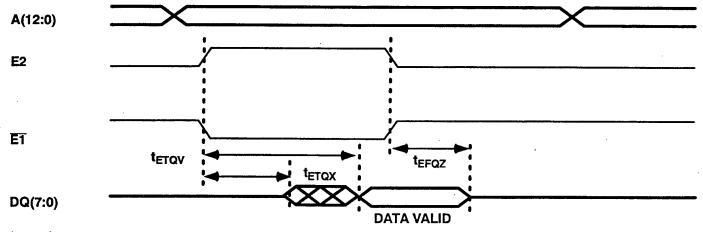
- 1. The ET (enable true) notation refers to the rising edge of E2 or the falling edge of E1, whichever comes last. SEU immunity does not affect the read parameters.
- 2. The EF (enable false) notation refers to the falling edge of E2 or the rising edge of E1, whichever comes first. SEU immunity does not affect the read parameters.
- 3. Three-state is defined as a 500mV change from steady-state output voltage.
- \* Post-radiation performance guaranteed at 25°C per MIL-STD-883 Method 1019 at 1.0E6 rads(Si).



Assumptions:

- 1.  $\overline{E1}$  and  $\overline{G} \le V_{IL}$  (max) 2. E2 and  $\overline{W} \ge V_{IH}$  (min)

Figure 3a. SRAM Read Cycle 1: Address Access



Assumptions: 1.  $G \le V_{IL}$  (max) and  $W \ge V_{IH}$  (min)

Figure 3b. SRAM Read Cycle 2: Chip Enable Access

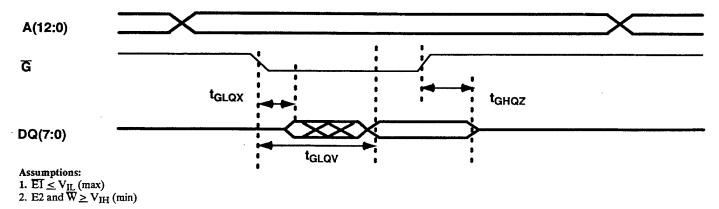


Figure 3c. SRAM Read Cycle 3: Output Enable Access

## AC CHARACTERISTICS WRITE CYCLE (Post-Radiation)\*

 $(V_{DD} = 5.0V + /-10\%; -55^{\circ}C < Tc < +125^{\circ}C)$ 

SYMBOL	PARAMETER  Write cycle time		64-85	671	54-70	671	64-55	l
			MAX	MIN	MAX	MIN	MAX	UNIT
t <sub>AVAV</sub>	Write cycle time	85		70		55		ns
t <sub>ETWH</sub>	Device enable to end of write	65		60		50		ns
tAVET	Address setup time for write (E1 or E2 - controlled)	0		0		0		ns
t <sub>AVWL</sub>	Address setup time for write (W - controlled)	0		0		0		ns
t <sub>WLWH</sub>	Write pulse width	50		35		35		ns
twhax	Address hold time for write (W - controlled)			0		0		ns
t <sub>EFAX</sub>	Address hold time for device enable (E1 or E2 - controlled)			0		0		ns
t <sub>WLQZ</sub>	W-controlled three-state time		15		15	Ů	15	ns
t <sub>WHQX</sub>	W-controlled output enable time			0	1.5	Ó	13	ns
teref	Device enable pulse width (EI or E2 - controlled)			60		50		ns
t <sub>DVWH</sub>	Data setup time			35		35		ns
twHDX	Data setup time  Data hold time			0		0		ns
twlef	Device enable controlled write pulse width	65		60		50	-+	ns
t <sub>DVEF</sub>	Data setup time	50		35		35		ns ·
t <sub>EFDX</sub>	Data hold time	0		0	$\dashv$	0		ns

<sup>\*</sup> Post-radiation performance guaranteed at 25°C per MIL-STD-883 Method 1019 at 1.0E6 rads(Si).

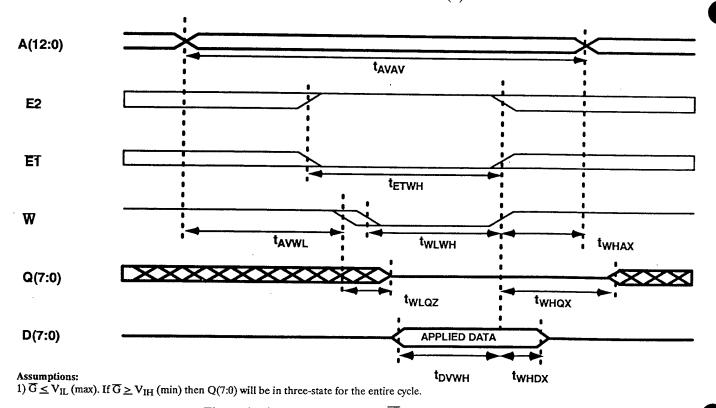
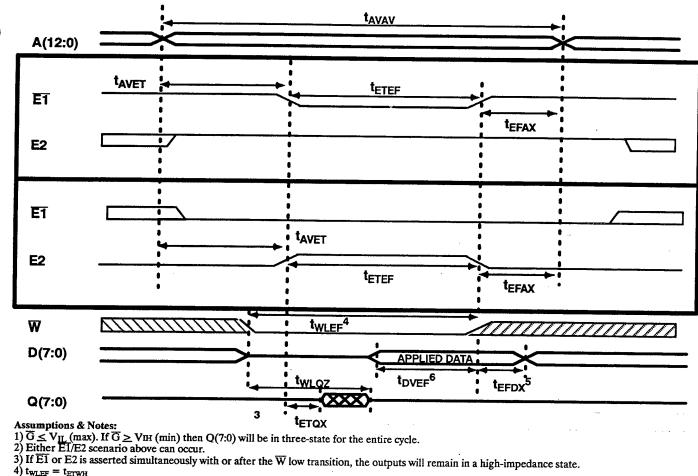


Figure 4a. SRAM Write Cycle 1: W-Controlled Access



4) t<sub>WLEF</sub> = t<sub>ETWH</sub>
5) t<sub>EFDX</sub> = t<sub>WHDX</sub>
6) t<sub>DVEF</sub> = t<sub>DVWH</sub>

Figure 4b. SRAM Write Cycle 2: Enable-Controlled Access

## DATA RETENTION CHARACTERISTICS (Post-Radiation)\* $(T_C = 25^{\circ}C)$

SYMBOL	PARAMETER	MINIMUM	MAXI Vdi	0@	UNIT
			2.0V	3.0V	
$V_{DR}$	V <sub>DD</sub> for data retention	2.0			V
$I_{ m DDDR}$	Data retention current <sup>1</sup>		75	90	μΑ
t <sub>EFR</sub>	Chip deselect to data retention time <sup>1</sup>	0			ns
t <sub>R</sub>	Operation recovery time <sup>1</sup>	t <sub>AVAV</sub>			ns

## Note::

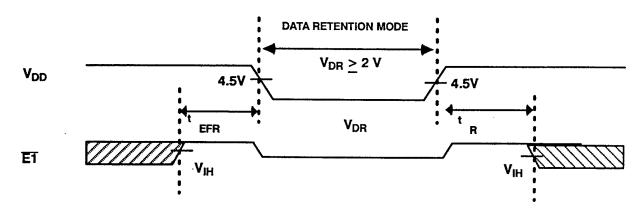
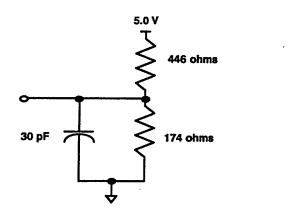
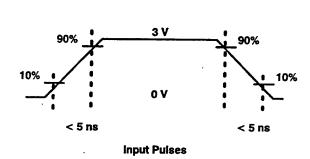


Figure 5. Low  $V_{DD}$  Data Retention Waveform

<sup>1.</sup>  $V_{LC} = 0.2V$   $V_{HC} = V_{DD} - 0.2V$   $EI \ge V_{HC}$ ,  $E2 > V_{HC}$ 

<sup>\*</sup> Post-radiation performance guaranteed at 25°C per MIL-STD-883 Method 1019 at 1.0E6 rads(Si).





**Assumptions:** 

1. 30 pF including scope probe and test socket.

Measurement of data output occurs at the low to high or high to low transition mid-point.

Figure 6a. AC Test Loads and Input Waveforms

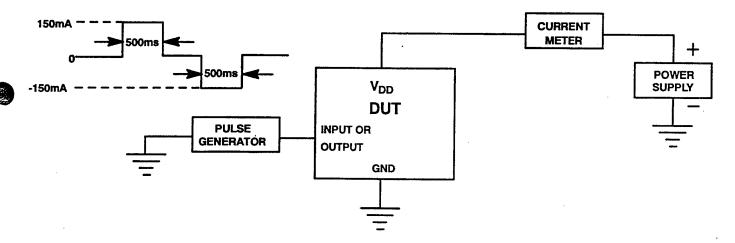


Figure 6b. Latchup Test

## LATCHUP TEST CONFIGURATION

Figure 6b shows the latchup test.  $V_{DD}$  holds at +5.5  $V_{DC}$ , and  $V_{SS}$  holds at ground. The device test is at 125°C. Each type of I/O alternately receives a positive and then negative 150 mA pulse of 500 ms duration. The

current is monitored after the pulse for latchup condition. To prevent burnout, the supply current is limited to 400 mA.

The SRAM has latchup immunity in excess of +150 mA for 500 ms.

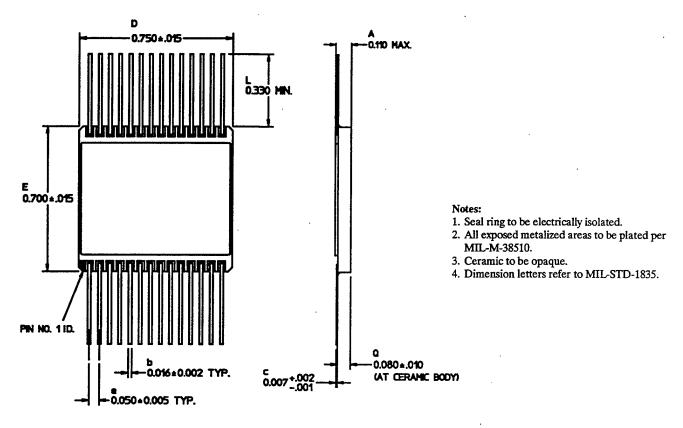


Figure 7a. 28-pin Ceramic Flatpack

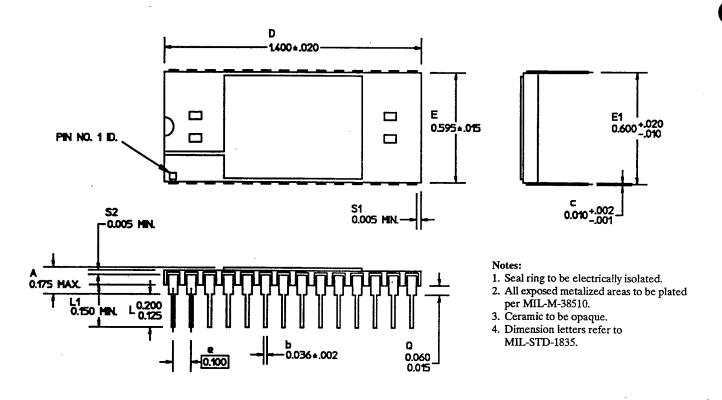
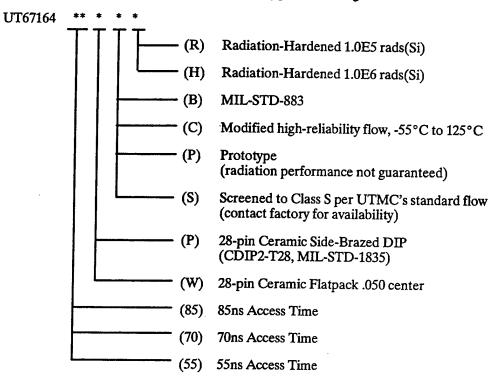


Figure 7b. 28-pin Ceramic DIP Package

## ORDERING INFORMATION

To order the UT67164 SRAM, use the following part number guide:



## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

## General Description

Features

The MAX220-MAX249 family of line drivers/receivers is intended for all EMTA-228E and V.28M·24 communcations interfaces, and in particular, for those applications where ±12V is not available.

Operate from Single +5V Power Supply (+5V and +12V—MAX231 and MAX239)

Superior to Bipolar

These parts are particulary useful in battery-powerco systems since their low-power shutdown mode reduces power dissipation to less than 5µW. The MAX225 MAX233, MAX235, and MAX245AMAX247 use no external components and are recommended for applications where printed circuit board space is critical.

## Applications

Battery-Powered RS-232 Systems Multi-Drop RS-232 Networks Interface Translation Low-Power Moderns Portable Computers

## Low-Power Receive Mode in Shutdown (MAXZ23/MAX242) Meet All EIA/TIA-232E and V.28 Specifications Multiple Drivers and Receivers 3-State Driver and Receiver Outputs Open-Line Detection (MAX243)

Ordering Information

PART	TEMP, RANGE	PIN-PACKAGE
MAX220CPF	3°C to + 70°C	16 Plastic DIP
MAX223CSE	0°C to + 70°C	16 Narrow SO
MAX220CWE	2°C to +70°C	CS abiW 31
MAX221C/D	27C to +78°C.	Dice*
MAX22TEPE	0°38 • 61 0°0:-	16 Plastic DIP
MAX22 ESE	0,98 r of 0,000	6 Narrew SO
MAX27112E	7.58 to 3.00	16 Wide SO
MAX221EJE		16 CERDIP
MAX22CITUE	-55°C to +125°C	16 CERCIP
Ordering Informa	Ordering Information continued at end of data sheet.	t of data sheet.

Selection Table Contact intermental parameters.

		Power	No. of		Nominal	SHON	ž		
_	Part	Supply	RS-232	No. of	Cap. Value	6 Three.	Active in	Active in Data Rate	
_	Number	3	Drivers/Rr	Drivers/Rr Ext. Caps	(F)	State	SHDM	(kpbs)	Features
-=		1	2/2	7	4 7/1C				
	PAX222	1	37.5	-	-				<ul> <li>SM PC sendig 20 Act and reflected and reflections.</li> </ul>
	RAKEPS (NIAKERS)		7	7			`		World to endergone and the control of the control o
	1343275	٠.	'n.	Û			,		5.12 300 to 50
	136×230 (133×20)	•	5/6	4	: 0.0 :				The section of the se
_	BAN CHARACTOR	11.	4	٠.	10.01				The paid of set 200 to 1 and the country of the
_		2011							mayor and Man (2.3).
	34AX232 (852×202)		3.5	7	1001			7	1.1.17y standard
	MAX2324	-:	37:	••	10	.•			The stewards and the same
_	MAX233 (MAX203)	٠.,	21.2	С				;::	': + Hernal caps
	MAYZJJA		313	c				٠.	To present cars four size falls
_	114X234 (MAX204)	1	274		1000				240 100s 148E
	MAX2 15 (MAX205)	٠.	÷	0					's retendence:
Ť	MAX236 (MAX206)	٠.	:/•	4	10(0)	:		· .	1. 1. 10 km three-State
_	MAX237 (13AX207)	~:	5	₹	10(0.1)			··	Complements (BM FC Securities)
_	BAXZ38 (MAXZ08)	•	4/4	4	1000			:	State of the second of the sec
	MAX (NIAXZ(PI)	1,111	>	٠.	1001			ŗ.	Crycland (See 12V or parter, supplier 1971)
		.258.132							1.31+age solution for the Pt. Sentitum.
_	MAX240	**	55	₹	0,			,à	E in Halpack package
	MAX241 (MAX211)	•	y.'	7	: 616:			<u>.</u> ;	Complete IBM PC secal port
_	EANY 242		272	147			,	i.	Separate shuidown and enathr
_	144X243		33	-	1.0			5	Separating detection simplified inhibited
	MAX244	٠.	67.1	4	10			·	J. shin rate
	MAX245	٠.		0			,		the Steam raffer and enables over a supplemental and a second of
	MAX246		0.74	¢			`	÷	in gripping and experience and dewritering
_	1.1AX2.17		0.	٥			`	÷	in the glown cape, let a little in every designability in the first
_	MAXZAE		P.F.	7	¢.		,	: '	sauged durches percents also dustres
	67XV14		1,1	7	9:	7	>	:	this able width at flatters in path age.
							٠		· · · · · · · · · · · · · · · · · · ·

Call toll free 1-800-998-8800 for free samples or literature. ダIXアダ

Maxim Integrated Products 1

## +5V-Powered, Multi-Channel RS-232 **Drivers/Receivers**

# ABSOLUTE MAXIMUM RATINGS—MAX220/222/232A/233A/2433

<b>b</b>	Supply Voltage (V <sub>CC</sub> )	16-Pin Narrow SO (derate 8 70mWPC above + 70°C	"
7	Input Voltages	16-Pin Wide SO (derale 9 52mW/C above + 20°C)	, ,
	IN -0.3V 10 (Vcc - 0.3V)	18-Pin Wide SO (derate 9.52mW/°C above +70°C)	
(	AIN ±30V	20-Pin Wide SO (derate 10.00mW/C above +70°C)	. (1
V		20-Pin SSOP (derate 8.00mW/PC above +70°C)	, ((
V	Curput Voltages	16-Pin CERDIP (derate 10,00mW/C above + 701C)	, , ,
Ŋ		16-Pin CERDIP (derate 10.53n/W/°C above +70°C)	) 41
_	"OUT (Vcc + 0.3V to (Vcc + 0.3V)	Operating Temperature Ranges	,
C	Diverneceiver Output Short Circuited to GND Continuous	MAX2 AC MAX2 C	
);	Continuous Power Dissipation ( $T_A = +70^{\circ}C$ )		
7	16-Pir Plastic DIP (derate 10.53mW/*C above + 70°C) 842mw		
7	18-Pin Plastic DIP (derate 11.11mW/*C above +70°C) 889mw		٠
(	20-Pin Plastic DIP (derate 8.00mW/°C above +70°C) 440mW	Lead Temperature (soldering, 10sec)	
(1	Note 1: Input voltage measured with Toyn in high-impedance state. SHON or V 5 DV	Si Oil or V Ov	
1	Stossos tayonet those bated undar Absolute Davanum Bangs, and care a smarter framewer to the stones. De-	"Albert dans are for the charter Been and the	
N	Sporting of the document alian conditions to provide these men it is operational sections of the structural single in a sporting the section of the structural sections of a section of the structural sections of the structural section of the structural section of the structural section of the section of th	"t the operational sections of the speedicalous is not appear; ".	٠.
1	Car of Shadd 190mb Agen second constraint an straight of final constraints and a	200	

Shossos bayout hose listed unite. Mischier Davamen Kinegs, ingy care, 5-majora damap, in the device. These are arest careing an appealant of the gloves at these or any other conditions beyond those man are 1.1 for epicational sections of the specifications to not implied. [47] and absolute maximum rating conditions to extended foreign englished. [47] are the ELECTRICAL CHARACTERISTICS—MAX220/222/232A/233A/242/243 ( $V_{CC}$  = +5V ± 10%, C1-C4 = 0.1µF,  $T_A$  =  $T_{LIM}$  to  $T_{LiAc}$ , unless otherwise noted)

MAXZA3 RZM 08 13 100 MAXZA3 RZM 08 13 2 00 116	PARAMETER	CONDITIONS					
Mormal operation   14 08   1	RS-232 TRANSMITTERS		MEN	2	MAX	UNITS	
Normal operation   SHON = V.W. MAZ222242	Output Voltage Swing	All transmitter outputs : 3.3ed with 3kD to GND	4	a			
Normal operation   S	Input Logic Threshold Low		2			> :	Ġ
Normal operation   2   14     SHIĞN = OV, MAX2222-2-2 Shuldown   10   1-1     VCC = 5 SV, SHDN = 0 \cdot \	Input Logic Threshold High			-	0.0	>	-
Normal operation   5   40			~	-		>	•
SHON = 0V, MAX222-2-2. Shuldown	Logic Pull-Up/Input Current	Normal operation		5	\$		
VCC = 5V, SHÖN = 0. ∴ ∴ 2v1 = ±15V, MAX222242		SHDN = 0V, MAX222-2-2. shuldown		1001	-1	<u> </u>	
VCC = SHON = 0V V <sub>O</sub> = 15V	Output Leakage Current	VCC = 55V, SHDN = 0.7 .001 = ±15V, MAX222/242		1007	± 10		
Except MAX220		Vcc = SHDN = 0V. Vo = ±15V		+001	101	<u>-</u>	
WCC = V+ V = 0V, VQ; = -2V   300   101A	Data Rate	Except MAX220, norma' operation		200	116	. r. le.	
996  VCC = 5V  VCC = 5V  Except MAX243 R2N  I.MAX243		MAX220		22	20	290	
190   190	ransmitter Oulput Resistance	VCC = V+ V- = 0V, V(P, " = -2V	300	1014		13	
99  VCC = 5V	Output Short-Circuit Current	V(1)1 . 0V	3 :	5 6		۔۔۔ د	
YCC = SV         Evcept MAX243 R2in         0.8         1.3         1.30           VCC = SV         Evcept MAX243 R2in (Note 2)         -3         1.8         2.4           Evcept MAX243 R2in (Note 2)         -0.5         -0.1           Evcept MAX243 R2in (Note 2)         -0.5         -0.1           MAX23.3         -1         -0.5         -0.1           MAX24.3         -1         -0.5         -0.1           MAX24.4         -1.0         -0.5         -0.1           Sourcing Voul = -1.0 mA         -2         -1.0           SHIVIN = VCC or EN = VCC	AS-232 RECEIVERS	Γ		¥.	,	٠	(
VCC = 5V         Except MAX243 R2N         0.8         1.3         ±.00           VCC = 5V         Except MAX243 R2N (Note 2)         -3         1.6         2.4           Except MAX243 R2N (Note 2)         -0.5         -0.1         -0.5         -0.1           Except MAX243 R2N (Note 2)         0.2         0.5         -0.1           MAX243         MAX243         3         5         7           Iour = 3 2mA         0.0 myst. in shdn.         0.2         0.4         0.2         0.4           Sourcing Vour = -1 0mA         3.5         -1         -1         0.2         -1         0.2         0.4           Shrinking Vour = -1 0mA         Shrinking Vour = -1 0mA         -2         -10         -2         -10         -30	RS-232 Input Voltage Operating Range						
VCC = 5V         ∴AX243 R2In (Note 2)         ·3           V <sub>CC</sub> = 5V         ≡xcopi MAX243 R2in         1 8 24           Except MAX243 R2in (Note 2)         ·0 5 ·0 1           Except MAX243 VCc = 5V no hyst. in strdn.         0.2 0.5 1           MAX243         1 5 7           Iour = 3 2mA         0.2 0.4           Iour = 1 0mA         3.5 7           Sourcing Voul = 6NO         2 ·10           Shrinking Voul = VCc or EN = VCc, OV 5 Voul 5 Vcc         10 30           SHINI = VCc or EN = VCc, OV 5 Voul 5 Vcc         1005	3S-232 Inout Threshold Low		0.8	-	25	>	ý
V <sub>CC</sub> = 5V         Except MAX243 R2kn (Note 2)         18         2 4           Except MAX243 R2kn (Note 2)         0.5         0.1           MAX243         1 (AX243 R2kn (Note 2))         0.5         0.1           MAX243         1 (AX243 R2kn (Note 2))         0.2         0.5         1           MAX243         1 (AX243 R2kn (Note 2))         3         5         7           I (Out = 3 2mA         0.2         0.4         0.2         0.4           Sourcing Voul = 10 mA         3.5 VCC · 0.2         0.4         0.2           Shinking Voul = VCC or EN		1	5	,		>	
V.C. = JV   V.C. = SV   AVZ43 R2N (None 2)   0.5   0.1     Except MAX243, V.C. = 5V   no hyst. in shdn.   0.2   0.5   1     MAX243   1   1   7     Nour = 3 2mA   3   5   7     Vour = -1 0mA   3.5   V.C 0.2     Sourcing Vour = KVC   2   0.5   1     Shrinking Vour = V.C. OV § Vour 5 V.C.   10   30     SHDM = V.C.C OV EN = V.C. DV § Vour 5 V.C.   1005   2.10	3S-232 (nout Threshold High			8-	2.4		
Except MAX243, VCC = 5V no hyst. in strdn.   0.2   0.5   1		•		0.5	Ç	>	
MAX243   1   7   7   7   7   7   7   7   7   7	4S-232 Input Hysteresis	Except MAX243, VCC = 5V. no hyst. in shdn.	0.2	0.5	;		
OUT = 3 2mA		MAX243		-		>	
Out = 3 2mA	RS-232 Input Resistance		6		,		
Pour = -1 0mA   3.5 Vcc · 0.2   2   2   2   2   2   2   2   2   2	TL/CMOS Output Voltage Low	10U1 = 3 2mA	,	5		;	
Sourcing Vour = GND -2 .0 Shrinking Vour = Vcc. 10 30 SHDN = Vcc. or EN = Vcc. 0V < Vour ≤ Vcc. 10 30	TL/CMOS Output Voltage High	10Ut ≈ ·10mA		20.00	5	, ,	
SHrinking Vour = Vcc. or EN = Vcc. 0V < Vour ≤ Vcc. 10 30 10 Vcc. or EN = Vcc. 0V < Vour ≤ Vcc. 10 Vcc. or EN = Vcc. 0V < Vour ≤ Vcc.	TL/CMOS Output Short-Circuit Current	Sourcing Vour = GND		2		1	
SHDN = Vcc or EN = V:0.0V < Vour s Vcc 1005 110		Shrinking Vour = Vcc	2	30		Αr	
	IL/CMOS Output Leakage Current	SHDN = VCC or EN = VCC, 0V 5 Vout \$ VCC		10.05	1 10	Ą	

# +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

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767777707766666666666666666666666666666	±10%, C1-C4 = 0 1µF, T <sub>c</sub> = T <sub>1</sub> µ <sub>c</sub> , to T <sub>1,1,2</sub> profess other
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_	PAHAMETER		CONDITIONS	N.W.	ТҮР	MAX	UNITS
	EN input inreshold Low	MAX242			1.4	9.0	>
	EN Input Threshold High	MAX242		20	- 4	:	 .>
	POWER SUPPLY					-	
	Operating Supply Vollage			4.5		5.5	:>
			MAX220		5.0	2	
1	Vcc Supply Current (SHDN = Vcc)	Lito losi d	MAX222/23; ± 233A/242/243		ंच	. 0	878 -11M
	Figures 5, 6, 9, 19	3kQ load	MAX220		12		+1 t:
		toth outputs	MAX22275 . 333A/242/243		<u>. '2</u>		
			14 1,7% (			3	
	Shutdown Supply Current	MAXDONOS	LA OTHER		e,	9.	
4			1A : 40 to - 55 C		~ j%	9	· <u>·</u>
ð	SHDN Input Leakage Current	MAX222/242			3	3 -	
	SHDN Threshold Low	M4X222/242			: 5		1
	SHDN Threshold High	1.1.3.X2227242		- 60	. =	;	
,	AC CHARACTERISTICS				:		
		C. = 50pF to 2500pF Rt = 3kΩ to 7kΩ.	MAX222/23:433/4242/243	و ::	≙	 8	
	Transition Slew Rate	VGC = 5V, TA = +25°C.			. :	:	7 m
		measured from +3V to -3V or -3V to +3V	MAX220	u:	٣	ű.	
	Transmitter Propagation Delay	1	MAX222/232- 334/242/243		13	3.5	
	TLL to RS-232 (Normal Operation)		MAX220		4	-01	
_	Figure 1	1	MAX222;232±, 233A/242/243		1.5	3.5	ú
			l		5	٩	
<del></del>	Receiver Promacration Colory	:: ::	MAX222/272: 334/242/243		5.0		
	RS-232 to Tt.L (Normal Operation)	•	MAX220		9.6	:	
4	Figure 2		MAX222/2		9.0	-	-
3		-	MAX220		80		
	Receiver Propagation Delay	friegs	MAX242	;	. 0	. <u>.</u>	
	13-532 (0 1LL (Shutdown), Figure 2	Pres	MAX242	:	. 5.2	. 01	Ξ
	Receiver-Output Enable Time, Figure 3	Ifя	MAX242		125	909	
-1.	Receiver-Output Disable Time, Figure 3	10A	MAX242		160	200	. •
	Transmitter-Output Enable Time (SHDN goes High), Figure 4	. 131	MAX222/242 TuF caps		250		, A 13
1	Transmitter-Outout Disable Time		(do programme)		:		
	(SHDN goes Low). Figure 4	101	MAX222/242 . 'uF caps		(00)		
	Transmitter + to - Propagation	bart, law	MAX2221252: 233A12421243		300		:
	Uciay Dillerence (Normal Operation)		MAX220		2000		¥
	Receiver + to - Propagation	Pre-B. Dr. H.	MAX222/2324, 2.334/242/243		100		:
Ġ.	Comman Operation)		MAX220		225		(

Note 2: MAX243 R2out is guaranteed to be low when R2n; is < 0V or is floating:

Z Z Z Z

## **MAX220-MAX249**

## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

## Typical Operating Characteristics

# MAX220/MAX222/MAX232A/MAX233A/MAX242/MAX243

ON-TIME EXITING SHUTDOWN MAXZZZANAXZZZ  ON V V V V V V V V V V V V V V V V V V V	
AVAILABLE OUTPUT CURRENT  VS. DATA RATE  OUTPUT CURRENT  VS. DATA RATE  HOWS FROM V. 13 V.  ALC CAPS  ALC	
OUTPUT VOLTAGE VS. LOAD CURRENT  TO SELECT HANCE AND	

		<b>\$</b>		
SHUTOOWN - 4X242				<u>*</u>
ON-TIME EXITING SHUTDOWN - MAX222/MAX242	1 to CAPS	SHOW	0 th CAL	vib/sugas
0	\$\$	V) 3047_C · · · · · · · · · · · · · · · · · · ·	,	
JURRENT Te	DUIPUT LOAD CUPRENT FLOWS FROM V. 10 V		9	790
AVAILABLE OUTPUT CURRENT vs. data rate	/	VC - 5.78V		DATA BATÉ HABITS SECT
	Aut Caps		2 7	

# +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

# ABSOLUTE MAXIMUM RATINGS---MAX223/MAX230-MAX241

800mw 941mw 1000mw 889mw 727mw 800mw 800mw

V9.4 of V6.0.	20-Pin Wide SO (derate 10.00mW/*C above +70*C)
VCC	24.Pin Wide SO (derate 11.76mW/°C above +70°C)
	28.Pin Wide SO (derate 12.50mW/°C above +70°C) 1
long Voltages	44-Pin Plastic FP (derate 11.11mW/°C above +70°C).
1 (Vec + 0.3V) to (Vec + 0.3V)	14-Pin CERDIP (derate 9.09mW/°C above +70°C)
	16-Pin CERDIP (derate 10.00mW/PC above +70°C)
Output Voltages	20 Pin CERDIP (derate 11.11mW/°C above + 70°C)
To (V- + 0.3V) to (V 0.3V)	24-Pin Narrow CERDIP
	(derate 12.50mW/*C above + 70°C)
Short Director Direction Town	24-Pin Sidebraze (derate 20.0mW/PC above +70°C).
o (1 . = +70°C)	28-Pin SSOP (derate 9.52mW/°C above +70°C)
14-Pin Plastic DIP (derate 10 05-4W/*C above +70°C) 800-41	jes
16 Pur Plastic DIP (denate 10 53 mW/°C above + 70°C) 842mVV	
20 For Plastic DIP (decale 11 11 20 W/C above + 70°C) (889c V)	
24 Pri Nation Plastic DIP	MAX2 M 55°C to
(derate 13.33***///C abox** + 70*C) 1067** %	Storage Temperature Range 65°C to
24-Pin Plastic DIP (derate 9 (8)-W/PC above + (UCC) 500m/PC	Lead Temperature (soldering, 10 sec)
Terem Wide SO (derate 9 SZMP). Caddove + (17 C)	

0°C to +70°C -40°C to +85°C 55°C to +125°C 65°C to +160°C

1600mW 1600mW 762mW

Stesses beyond thoso istind under "Assolute May-rurn Ratings" may 11 se remainent damage to the dowce. Thase are striss values, and unchorud revisions of the dowce at these or are other controlled house of the dowce at these or are other controlled by the down and the dowce at these or are other controlled two securities to any affect the "Fredish". 

-		CONDITIONS	ž	٦. -	MAX	ONIES
Chatgod Voltage Swing	All transmitter o	All transmitter outputs leaded with 30kΩ to ground	15.0	1/3		>
		MAXZ32/255		2	10	
Voc. Power-Supply Current	No load.	MAX223:232:236/234-238/240/241		7	15	Ϋ́E
	2	MAX23: 239		4		
		MAX23		α-		,
V. Passer Supply Carrest		MAX23		J.	7	
		MAX223		15	3	
Shardown Supply Current	14 = -25 C	MAX23, 24: 230,240/241		-	ç	<u>{</u>
Input Logic Threshold Low	TIN. ET. STIDIN	IIN, ETT, SHON (MAX222): 11 SHON (MAX230/235-241)	:	:	ž.,	>
	T <sub>IN</sub>		2.0			
Programmeshold High	EN. SHDIT (MA	EN, SHDM (MAX223). EN, SHDM (MAX230/235 255,246/241)	24			>
Logic Pull-Up Current	Vice sul			15	5,75	됩.
Hegeiver Input Voltage Oberating Range			30		.ā	>

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## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

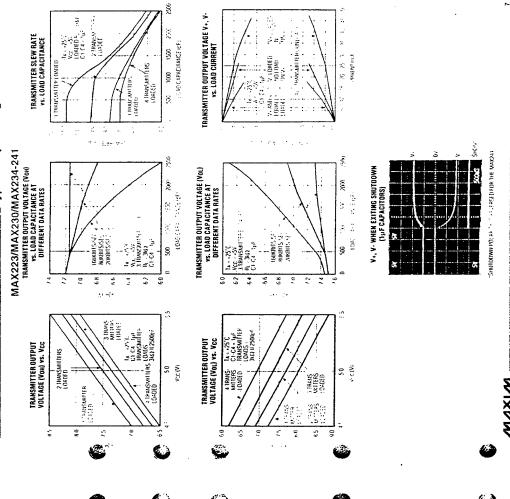
ELECTRICAL CHARACTERISTICS — MAX223/MAX230-MAX241 (continued)
(MAX223/230/232/234/236/237/238/240/241 V<sub>CC</sub> = +5V ±10%, MAX233/MAX235 V<sub>CC</sub> = 5V ±5%, C1-C4 = 1 0<sub>1</sub> F. MAX231/MAX239
V<sub>CC</sub> = 5V ±10%, V+ = 7.5V to 13.2V, T<sub>A</sub> = T<sub>MM</sub> to T<sub>MAX</sub>, unless otherwise noted )

MAX220-MAX249

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
BS-232 loon! Threshold low	IA = +25°C	Normal operation SHDN = 5V (MAX223) SHDN = 0V (MAX235/2	irmal operation SHDN = 5V (MAX223) SHDN = 0V (MAX235/236/240/241)		90	-2	>
	Vcc = 5V	Shutdown (MAX223) SHDN = 0V, EN = 5V (R4IN, R5IN)	3) RSIIv.)		90	1.5	>
48.979 board Broschridt Link	IA - 125°C	Normal operation SHDN = 5V (MAX223) SHDN = 0V (MAX2335P	irmal operation SHON = 5v (MAX223) SHDN = 0v (MAX233p36;pa0;pa1)	 	1.7	2.4	;
nga nga nga nga nga nga	Vcc = 5V	Shuldown (MAX223) SHDN = 0V, EN = 5V (R4 <sub>IN</sub> , R5 <sub>IN</sub> )	3) RSiN)		1.5	2.4	>
RS-232 Input Hysteresis	Vcc = 5V, no hy	VCC = 5V, no hysteresis in shuldown		2.0	0.5	10	>
RS-232 Input Resistance	TA = +25°C. VCC = 5V	c = 5V		3	5	7	κΩ
TTL/CMOS Output Voltage Low	lour = 1.6mA (*	lout = 1.6mA (MAX231-233 lour = 3.2mA)	3.2mA)			0.4	>
TTL/CMOS Output Voltage High	lour = 1.0mA			35	VCC - 0.4		>
TL/CMOS Outpul Leakage Current	0V ≤ Rout ≤ Vcc; EN = 0V (MAX223	0V < Rout < VCC; EN = 0V (MAX223); EN = VCC (MAX235·241)	(235-241)		0.05	± 10	Ą
Receiver Output Fnable Time	Normal	MAX223			009		
	operation	MAX235/236/239/240/241	240/241		\$		£
Beceiver Output Disable Tune	Normal	MAX223			906		1
	operation	MAX235/236/239/240/241	240/241		250		£
	RS-232 IN	Normal operation			0.5	01	
Propagation Delay	OUT,	SHON = 0v	IPHLS		4	40	sa Si
	C <sub>L</sub> = 150pF	(MAX223)	IPLHS		9	40	
Pansilion Recion Slew Rate	MAX223/MAX230/MAX234-241 IA = +25°C, VCC = 5V Rt = 3kΩ to 7kΩ, Ct = 50pF to measured from +3V to -3V or -3	MAX223/MAX230/MAX234-241 IA = +25°C, VCC = 5V Rt = 3kΩ to ?kΩ. Ct = 50pF to 2500pF measured from +3V to -3V or -3V to +3V	др. 1.3V	е	5 1	30	
	MAX231/MAX232/MAX233 T <sub>A</sub> = +25°C, V <sub>CC</sub> = 5V R <sub>L</sub> = 3kΩ to 7kΩ, C <sub>L</sub> = 50p measured from +3V to ·3V	MAX231/MAX232/MAX233 T <sub>A</sub> = +25°C, V <sub>CC</sub> = 5V R <sub>L</sub> = 3KΩ to 7kΩ, C <sub>L</sub> = 50pF to 2500pF. mensured from +3V to ·3V or ·3V to <sub>?</sub> 3V	0pF. +3V		4	30	<u> </u>
Transmitter Output Resistance	$V_{CC} = V_{+} = V_{-}$	$V_{CC} = V_{+} = V_{-} = 0V, V_{OUT} = \pm 2V$		300			a
Transmitter Out Short-Circuit Current					±10		Am A

## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers





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## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

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# ABSOLUTE MAXIMUM RATINGS—MAX225/MAX244-MAX249

Supply Voltage ( $V_{CC}$ )	Continuous Power Dissipation $\{I_A = *IV^{(C)}\}$ 28-pn Wide SO (Jedrale 12 SOmW/*C above $*IV^{(C)}$ ). I 000mW 40-pn Plastic DIP (Jedrale 11.1 1mW/*C above $*IV^{(C)}$ ) 611mW
ENTB. ENTA, ENTB0.3V to (V <sub>CC</sub> + 0.3V)	44-Pin PLCC (derate 13.33mW/°C above +70°C) 1067mW Operating Temperature Ranges
Tour (Note 3) ± 15V Rour (VCC + 0.3V)	
Short Circuit (1 output at a time) Tour to GND	Storage Temperature Range 65°C to + 160°C Lead Temperature (solidering, 10 sec.)
Mour to GNU	npedance state, shutdown, or $V_{\mathrm{GC}}$ . (W
Sinsses bayond those isted under "Nosoldo Advantum Haintys" intry causo preminar operation of the device on these or any otno conditions beyond hose individued in the absolute maximum rating coordinate for extended periods may effect device reliability.	Strasses beyond those issten untal "Australian Halings" may cause permittent straight is the slower. These are the straight and has been a population of the obiged and population of propored those independent in the expensional sections of the street distributes as not implied. I survium in absolute maximum rating conditions for extended periods may affect the obligation.
ELECTRICAL CHARACTERISTICS—MAX225/MAX244-MAX249	//MAX244-MAX249

# ELECTRICAL CHARACTERISTICS-MAX225/MAX244-MAX249

(MAX225 V<sub>CC</sub> = 5.0V  $\pm$ 5%; MAX244.MAX249 V<sub>CC</sub> = +5 0V  $\pm$  10%, external capacitors C1·C4 = 1 $\mu$ f. I<sub>A</sub> = 1 $\mu$ tr<sub>1</sub> to 1 $\mu$ ax, unless otherwise noted.)

PARAMETER		CONDITIONS	MIN	тур	MAX	UNITS
RS-232 TRANSMITTERS						
Input Logic Threshold Low				7.	0.8	>
Input Logic Threshold High			: '~ !	?	:	>
		Normal operation		5	55	•
Logic Puil-Up/Input Current	l aoies (A. 10	Shutdown		1007		<u>{</u>
Data Rate	Tables 1A-1D.	Tables 1A-1D. Normal operation		150	3	kbits/sec
Output Voltage Swing	All transmitter o	All transmitter outputs loaded with 3Ωk to GND	+5	±7.5		>
Outrate Laboratory Changelory	Tables	ENA. ENB. ENT. ENTA. ENTB = VCC. VOUT = 115V		1007	125	ď
Output Leakage Currein (Shuldown)	O C Sange	VCC = 0V. VOUT = ± 15V		10.01	125	<u> </u>
Transmitter Output Resistance	Vcc = V = V.	Vcc = V = V = (V, Vout = 12V (Note 2)	300	70		<b>α</b>
Output Short-Circuit Current	VOLJT = OV		\ + -	G.		νω
RS-232 RECEIVERS						
RS-232 Input Voltage Operating Range					125	>
RS-232 Input Threshold Low	Vcc = 5V		90	- 3		>
RS-232 Input Threshold High	VCC = 5V			a -	5.4	>
RS-2. Input Hysteresis	VCC = 5V		0.2	.: စ	c -	>
RS-232 Input Resistance			က	d)	1	С¥
TTL/CMOS Output Voltage Low	10UT = 3 2mA			6.2	0.4	۸
TTL/CMOS Output Voltage High	10UT = -1.0mA		3.5	Vcc - 52		>
	Sourcing Vour = GND	= GND	?	CF.		400
Tromos Cothal Start-Circuit Correra	Sinking Vout = Vcc	= Vcc	ō	8		
TTL/CMOS Output Leakage Current	Normal operat Tables 1A-1D,	Normal operation, outputs disabled, Tables 1A-1D, 0V s Vour s Vcc, ENR_ = Vcc.		10.36	10 10	<u>₹</u>

## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

ELECTRICAL CHARACTERISTICS—MAX225/MAX244-MAX249 (continued)
[MAX225 V<sub>CC</sub> = 5 0V ±5%, MAX244-MAX249 V<sub>CC</sub> = +5 0V ± 10%, external capacitors C1-C4 ≈ 1µF, T<sub>A</sub> = T<sub>MM</sub> to T<sub>MAX</sub>, unless otherwise noted.)

PARAMETER	NOO	CONDITIONS	Z W	ďΣ	MAX	UNITS
POWER SUPPLY AND CONTROL LOGIC						
		MAX225	4 75		5.25	>
Operating Supply Voltage		MAX244-MAX249	4.5		5.5	>
	Jan 1 and	MAX225		01	50	
	ואס רספס			=	30	9
ACC Subbly Current (Normal Operation)	3kO loads on all	MAX225	1	:		<u> </u>
	outputs	MAX2344 MAX249		17	:	
	1A = +25 C		:	. 8	: :82 :	
shuldown supply Current	TA = THIN TO TMAX		   		20	<u>{</u>
man er en	Leakage Current				1-1	Ϋ́
Control Input	Threshold Low			1.4	0.8	>
	Threshold High		24	-4		>
AC CHARACTERISTICS	And an annumental and the parties of					
<u> </u>	C <sub>L</sub> = 50pF to 2500pF R <sub>L</sub> = 3κΩ to 7κΩ VC <sub>C</sub> = 5V T <sub>A</sub> = +25 °C measured from +3V to 3V or 70 to +30	F R <sub>1</sub> = 3×0.55 7×0. C To 3V or 27 to +3;	ر ر		30	V/µs
Transmitter Propagation Delay	(PHR)			. 5	3.5	-
Figure 1	Phr.		:	1.5	3.5	£
Receiver Propagation Delay	IPH(R			90	1.5	=
Figure 2	PLFR			0.6	1.5	2
Receiver Propagation Delay	Press			90	10	:
Figure 2	કત્નાલ			30	0	1
Transmitter + to - Propagation Delay Difference (1) per allon )	Dec 1 byes			350		ğ
Receiver + to - Propagation Delay Difference (1:20rmal Operation)	DAG T DEPT			350		Ê
Receiver-Output Enable Time, Figure 3	len .			8	900	SU
Receiver-Output Disable Time, Figure 3	HO1			8	200	Sc
Transmitter Earth Lave		MAX246-249 (excludes charge plant)		ď		<u> </u>
acin alganz Janustra	MAXZ	MAX225/MAX245-MAX249 (includes charge-tounp startup)	: 	õ		3111
Transmitter Disable Time Froure 4	101			8		Su

Note 4: The 300H mamman specification complies with EIA/TIA-232E, but the actual resistance when in shuldown mode or VCC = 0 is 101H as is implied by the leakage specification.

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# +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

Table 1a. MAX225 Control Pin Configurations

ENT	ENB	OPERATION STATUS	TRANSMITTERS	RECEIVERS
0	0	Normal Operation	All Active	All Active
0	-	Normal Operation	All Active	All 3-State
1	0	Shutdown		All Low-Power Receive Mode
-	-	Shutdown	All 3-State	All 3-State

**642XAM-0S2XAM** 

## Table 1b. MAX245 Control Pin Configurations

		€	· ·		<b>O</b>
RECEIVERS	RB1-RB5	All Active	RB1-RB4 3-State RB5 Active	All Low Power Receiver Mode	RB1-RB4 3-State RA5 Low-Pewer Receiver Node
RECE	RA1-RA5	All Active	!	21 _0w Power Paperver Mode	PATTRA4 3-State RAFLOW-Power Receiver Mode
TRANSMITTERS	TB1-TB4	All Active	:	iate	Ali 3-State
TRANSA	TA1-TA4		Ali Active	All 3-State	All 3-State
OPERATION	STATUS	Normal Operation All Active	Normal Operation	Shuldown	Shuldown
ENE		0	-	0	-
FN		0	0	-	-

## Table 1c. MAX246 Control Pin Configurations

1	FNR	OPERATION	TRANSA	TRANSMITTERS	RECE	RECEIVERS
	) i	STATUS	TA1-TA4	B1-TB4	RA1-RA5	RB1-R85
0	С	0 0 Normal Operation All Active All Active	All Active All Act		ia a proc	All Active
٥	-	0 1 Normal Operation All Active All 1335	All Active	. £	4. 4. 23cm RB1 RB4 3-55a RB5 Acts. 6	RB1 RB4 3-5:ate RB5 Acts.e
-	0 Shutd	Shuidown	All 3-State	Al App.	52. 544 3.State	All A, twe
-	-	Shutdown	All 3-State	All Patrice	HAT PAA 3 State PAE Low-Power PEER LO MODE	HRT RB4 3 7 pg HAS Low-Proper Receiver 12, 35

## Table 1d. MAX247/248/249 Control Pin Configurations

+5V-Powered, Multi-Channel RS-232 Drivers/Receivers

<u>'</u>							TRANSA	TRANSMITTERS	BECEI	RECEIVERS
	ENTA	ENTB	ENRA	ENRB	ō	MAX247	TA1-TA4	TB1-TB4	HA1-HA4	RB1-RB5
					STATUS	MAX248	TA1-TA4 TB1-TB4	TB1-TB4	RA1-RA4	RB1-RB4
-						MAX249	TA1-TA3	TB1-TB3	RA1-RA5	R81-R85
<u> </u>	0	0	0	0	Normal Operation		All Active	All Active	All Active	All Active
	0	0	О	-	Normal Operation		All Activi-	All Active	All Actives	All 3-State, except RB5 stays active on BAX247
	0	0	-	0	Normal Operation		All Active	All Active	All 3-State	All Active
	С	С	-	-	Normal Operation		All Active	All Active	All 3-State	All 3-State, except RB5 stays active on IAKX247
	0	-	0	0	Normal Operation		All Active	All Active ; 21 3-State	All Activit	All Active
	o	-	0	-	Normal Operation		All Active	3-State	All Activo	All 3-State except RBE stays active on MAX247
	С	-	-	0	Normal Operation		All Active	ar 3-State	All 3-State	All Active
	ي	-	-	-	Normal Operation		All Actor	All Action   Au 303tate	All 3-State	All Astate except R65 stays active on PANCAL
	-, !	0	0	0	Normal Operation		All Jobate, 24 Active	AL ACTIVE	All Active	all Active
	-	0	0	-	Normal Operation		All 3-516%	A- Active	All Active	exoc
	- :	С	-	С	Normal Operation		All 3-State 148 Active	AH ACINE	All 3-State	#" #511VP
		2	-	-	Normal Operation		All 3-Clar	i - Active	Aff 3-State	All 3-State except PES stays active on PLAX247
	-	-	c	С	Shuldown		All 3 State t	All 3 State Lan 3-State	Low-Power Receive Mode	Law-Power Peggelde Mode
	-	-	0	-	Shutdown		All 3 states	Alf 3.34.45 ( 44 3.5) ale	Low Power Receive Made	All 3 state except RdS stays active on Rdx247
	-	-	-	0	Shuldown		All 3-Stare	All 3-Stare! .:: 3-State	All 3-State	Low-Fower Receive Mode
	-	-	-	-	Shuldown		All 3-State	All 3-State   All 3-State	All 3-State	All 3-State, except PBS stays active on MAX247

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## Detailed Description

The MAX220-MAX249 contain four sections: dual charge-pump DC-DC voltage converters, RS-232 drivers, RS-232 receivers, and receiver and transmitter enable control inputs.

## Dual Charge-Pump Voltage Converter

operation. The first converter uses capacitor Ct to double the +5V input to +10V on C3 at the V+ output. The second converter uses capacitor C2 to invert +10V to -0V on C4 The MAX220-MAX249 have two internal charge-pumps that convert +5V to ±10V (unloaded) for RS-232 driver at the V- output.

(V+) and -10V (V-) outputs to power external circuity (see Typical Operating Characteristics), except on the age drops with increasing load current. Do not load V+ and V- to a point that violates the minimum  $\pm 5V\,E(LL/T1A.232E$ A small amount of power may be drawn from the +10V MAX225 and MAX245 MAX247, where these pins are not available. V+ and V- are not regulated, so the output voltdriver output voltage when sourcing current from 1/+ and Vto external circuitry

external circuitry. When these parts are shut down, V. falls to 0V, and V+ falls to +5V. For applications where a +10V external supply is applied to the V+ pin (instead of using the internal charge pump to generate +10V), the C1 capacitor must not be installed and the  $\overline{\rm SHDN}$  pin must be tied to  $V_{CC}$ . This is because V+ is internally con-When using the shutdown feature in the 'AAX222, MAX225, MAX230, MAX235, MAX241 and MAX245-MAX249 avoid using V+ and V· to power nected to V<sub>CC</sub> in shutdown mode.

## RS-232 Drivers

The typical driver output voltage swing is  $\pm 8V$  when loaded with a nominal  $5k\Omega$  RS-232 receiver and  $V_{CC}$  = +5V. Output swing is guaranteed to meet the EIA-TIA-232E put levels under worst-case conditions. These include a minimum 3KR load,  $V_{CC} = +4.5V$ , and maximum operating temperature. Unloaded driver output voltage ranges from (V+ -1.3V) to (V-+0.5V). and V.28 specification, that calls for ±5V minimum priver out

inputs of unused drivers can be left unconnected since  $400k\Omega$  input pull-up resistors to  $V_{CC}$  are built-in. The pull-up resistors force the outputs of unused dr. ers low lypically microamperes (maximum 25µA)—when in shuldown mode, in three-state mode, or when device power is removed. Outputs can be driven to ±15V. The power-supwhere the pull-ups are disabled. Driver outputs torn off and enter a high-impedance state-where leakage current is Input thresholds are both TTL and CMOS compatible. The because all drivers invert. The internal input puir-up resistors typically source 12µA, except in shutdc.xn mode ply current typically drops to 8µA in shutdown mode

The MAX239 has a receiver 3-state control line, and the MAX229 MAX224 MAX245 MAX245 and MAX24 have both a receiver 3-state control line and a low-power shutdown control. The receiver TLL/CMOS oulputs are in a high-impedance 3-state mode whenever the 3-state ENable line is high, and are also high-impedance whenever the shutdown control line is high

the driver output pulled to ground. The driver output leakage remains less then 1µA, even if the transmitter output is backdriven between 0V and (V<sub>CC</sub> + 6V). Below -0.5V the unpedance. The transmitter is also zener clamped to When in low-power shutdown mode, the driver outputs are turned off and their leakage current is less than 11th with transmitter is diode clamped to ground with 1kΩ series approximately V<sub>CC</sub> + 6V, with a series impedance of 1kt).

as required by the EIATIA-232E and V.28 specifications. Typical slew rates are 24V/Hs unloaded and 10V/Hs loaded with 3Ω and 2500pF. The driver output slew rate is limited to less than 30V/µs

## **RS-232 Receivers**

EIA/TIA-232E and V.28 specifications define a voltage level thresholds are set at 0.8V and 2.4V, so receivers respond to TL level inputs as well as EIA/TIA-232E and V 28 levels greater than 3V as a logic 0, so all receivers invert. Input

The receiver inputs withstand an input overvoltage up to £25V and provide input terminating resistors with nominal 5kΩ values. The receivers implement Type 1 interpretation of the fault conditions of V.28 and EIA/TIA-232E

The receiver input hysteresis is typically 0.59 with a guaranteed minimum of 0.29. This produces clear output transitions with slow-moving input signals, even with moderate amounts of noise and ringing. The receiver propagation delay is typically 600ns and is independent of input swing direction.

## Low-Power Receive Mode

The low-power receive-mode feature of the MAX223. MAX242, and MAX245-MAX249 puts the IC into shutdown awakened to look for activity. Using low-power receive mode, the system can still receive a signal that will actimode, but still allows it to receive information. This is important for applications where systems are periodically vate it on command and prepare it for communication at laster data rates. This operation conserves system power

## MAX243—Negative Threshold

The MAX2343 is pin compatible with the MAX232A, differing only in that RS-232 cable fault protection is removed on one of the two receiver inputs. This means that control lines such as CTS and RTS can either be driven or left floating without interrupting communication. Different cables are not needed to interface with different pieces of equipment

only if it a input is connected to a control line that is actively divien negative. If not driven it defaults to the 0 or while the regative threshold receiver is connected to the The reput meshold of the recuver without cable fault protection is -3.8V rather than +1.4V. Its output goes positive 'OK to send" state. Normally, the MAX243's other receiver (+1 4V trashold) is used for the data line (TD or RD), contelling (D48, D1S, CTS, RTS, etc.)

munications (C to stop sending data. To avoid this, the control  $\mathbb{R}^n$  is a nust either be driven or connected with Other members of the RS-232 family implement the 2326 specifications. This means a receiver output goes high wherever its input is driven negative, felt lloating, or optional cable fault protection as specified by EIA/TIAshorted to ground. The high output tells the serial comjunyair: : an appropriate positive voltage level

## Shutdown-MAX222-MAX242

with research and MAX223 and MAX224 also have a nectorer contender that enable input (EN) that allows receiver output (EN) that allows receiver output (EN) that all other desices. the MAX223 and MAX242, two receivers continue to operate in a reduced power mode when the chip is in On 114 TAX222, MAX235, MAX236, MAX240, and MAX241 34 receivers are disabled during shutdown. On Shutdown Under these conditions, the propagation delay increases to about 2.5µs for a high-to-low input transition When it is uidown, the receiver acts as a CMOS inverter put contributed and shill wan an SHDN van an SHDN vin the receiver outputs €

power letter mode. Driver outputs enter a high-impedance state three-state mode). On the MAX225, as five receivers are controlled by the  $\overline{\rm ENR}$  input. On the the ENA mout, while the remaining two receivers (RA5) and RB5, are always active. RA1-RA4 and RB1-RB3, are The t/AXZ25 provides five transmitters and five receivers. unifier or it, a controls. The charge pumps form of and shutdown when a logic high is applied to the ENT meet in this state, the supply current drops to less Jht of the receiver outputs are controlled by while the 1.4X245 provides ten receivers and eight transthan 25µ2 and the receivers continue to operate in a low-"1 devices have separate receiver and trans-\*\*\* state mode when ENR is a logic high the deser miller: put mag MAX2.:

## Receiver and Transmitter Enable

Control Inputs

the 254,255 and MAX245-MAX249 feature transmitter and race, an enable controls

The recellers have three modes of operation full-speed power receive (enabled receivers continue to function at lower data rates). The receiver enable inputs control the receive (1 ) and active), three-state (disabled), and low

(warra active) and three-state (disabled). The transmitter enable inputs also control the shutdown mode. The lers that two modes of operation full speed transmit device enters shutdown mode when all transmitters are disabled Enabled receivers function in the low-power full-screet receive and three-state modes. The transmitrecerre made when in shutdown,

+5V-Powered, Multi-Channel RS-232

Drivers/Receivers

Tables 14-10 define the control states. The MAX244 has no centrol pins and is not included in these tables

logic righ at the Arside control input (ENA) causes the four A-side receivers and drivers to go into a three-state mode. Similar, the B-side control input (ENB) causes the four B-The 125X246 has fon receivers and eight drivers with two contra pins, each controlling one side of the device. A and RSS) remain active at all times. The entire device is put into r ...stown mode when both the A and B sides are distabled  $\overline{\rm ENB}$  =  $\overline{\rm ENB}$  =  $+5\rm{VJ}$ side must and receivers to go into a three-state mode. As in the 1.147.245, one A-side and one B-side receiver (RAS

The CHAXAA provides nine recoivers and eight drivers with that control pins. The ENRA and ENRB receiver with 12.1 control pins. The ENRA and ENRB receiver enable abouts. The ENRA and ENRB receiver that ENR and ENRB transmitter enable inputs each control. The denote enters shutdown mode with a logic high on both  $\mathbb{P}[1,\lambda]$  and  $\overline{\mathbb{P}MR}$ hur or see The muth receiver (RBS) is always active

The NEX248 provides eight receiver and eight drivers with the CNRA and ENRB receiver enable inputs each control four receiver outputs. The ENTA and ENTB transmitter enable inputs control four dri vers each. This part does not have an always-active mitter), it into a three-state mode with a logic high on both  $\mathbb{C}^{1,2}$  and  $\overline{\mathbb{C}^{1,1}}$  and  $\overline{\mathbb{C}^{1,1}}$  and The device enters shutdown mode and trans-(3,431,5)

enters shuidown mode and transmitters go into a three-state military with a logic high on both ENTA and ENTB. In The UP 6249 provides ten receivers and six drivers with four correct pins. The ENRA and ENRB receiver enable inputs each control live rocever outputs. The ENTA and ENTE Presented in the control lives and account of the control lives and the The is no always-active receiver. The device "ansmitter enable up its control three drivers mode, active receivers operate in a low-power recenseration at data rates up to 20kbits/s. shuto: An

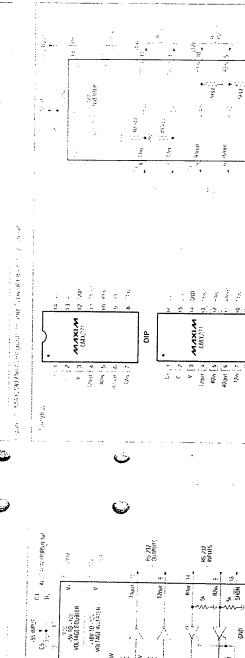
## Applications Information

operating circuits. In applications that are sensitive to power-supply noise,  $V_{CC}$  should be decoupled to ground Figures 5 through 25 show pin configurations and typical with a capacitor of the same value as C1 and C2 con nected as close as possible to the device.

Z/X/Z

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## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers र्मे अभाषात्रक 18; NC ũ DIP SO 11mm | 2 7. ... OHE UT .107 § 5 R2. -5v TO -10v 16.5% I.S. \* • • \* • • \* • • • +5V-Powered, Multi-Channel RS-232 Ş £ 5.8 Ċ نید د E Property S - 0 - 0 Drivers/Receivers CAPACITANCE (µF) 0 01 01 ឌ 0.1 S 4.7 0 2.7 0 14X232A 01 5 MAX232 DEVICE MAX220 TOP VIEW **64SXAM-0SSXAM**



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15 Rhs.
17 Rhs.
18 Rhs.
18 Rhs.
19 C. 17 Rhs.
19 C. 17 Rhs.
19 C. 17 Rhs.
19 Rhs.
10 Rhs.
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Figure 5 MAX220/232/232A Pin Configuration and Typical Operating Circl.

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DIP/SO

Figure 6 MAX222NMAX242 Pin Configuration and Typical Operating Circuit

PIN NUMBERS ARE FOR DIP/SO #AT 4:4GES ONLY

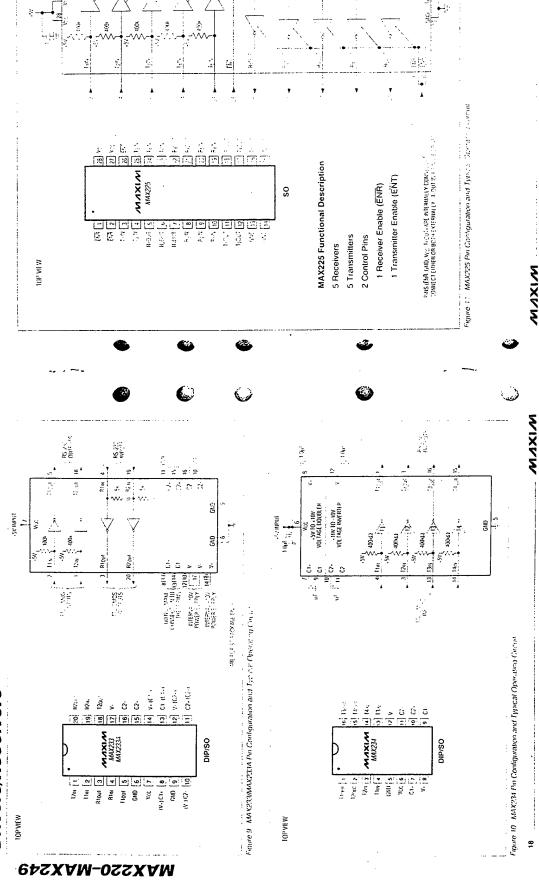
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M/X/M

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# +5V-Powered, Multi-Channel RS-232 Drivers/Receivers



# Drivers/Receivers

**642XAM-0SSXAM** 

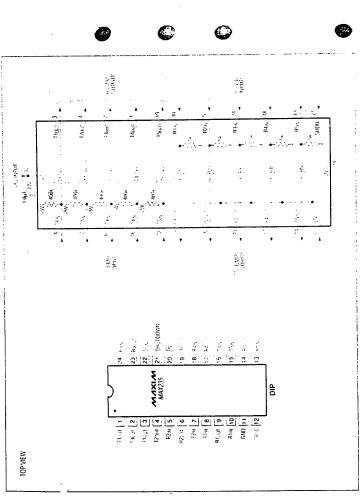


Figure 12 MAX235 Pin Configuration and Typical Operating Circuit

VCC .5V TO .10V VOLTAGE DOUBLER .01 10V 10 -10V Fightive. ₹. GHS ċ Figure 13. MAX236 Pin Consiguration and Typical Detrating Origin" 21 Sec. 15. 15. 17 R3 . . 22 R2C. 18: 13: DIP/SO River | 3 River | 5 Fig. | 5 Fig. | 6 Fig. | 7 Fig. | 7 5 5 5 6 33. #30.60.

35.232 01170174

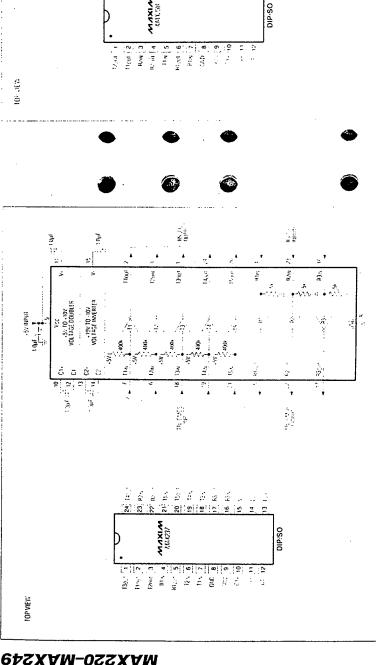
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22] 1131.11 21 144 20 14... 19, 13.

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Faure 15 AAX238 Pm Configuration and Type 1 Trees

Figure 14. MAX237 Pin Configuration and Typical Operating Grewit

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**642XAM-022XAM** 

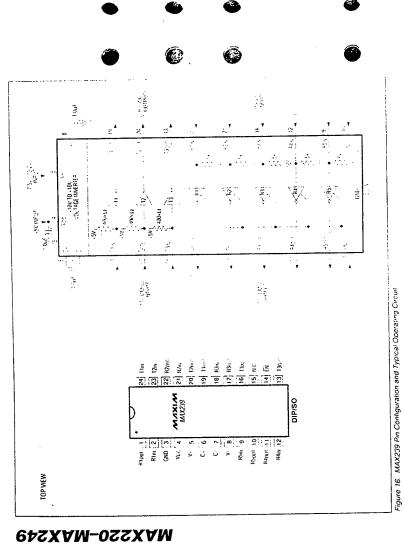
-59 TQ - 51 VOL 18 VOL TAGE \* 52 TG - 51 VQ - 52 VG -

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10P VIEW

## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers



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Figure 17 MAX240 Pin Configuration and Typical Operating Circut

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182 V P.

DIP/SO

R2 OUTPUT

R1 OUTPUT

RECEIVER INPUT

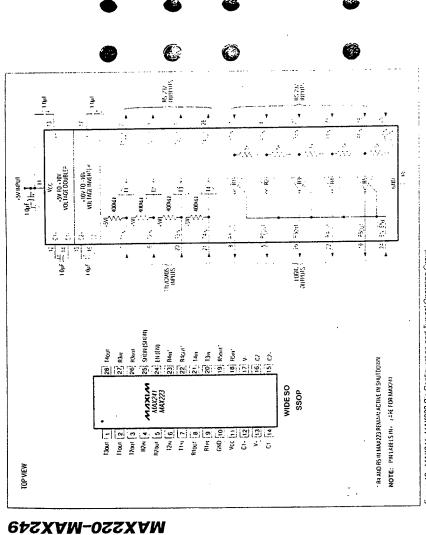
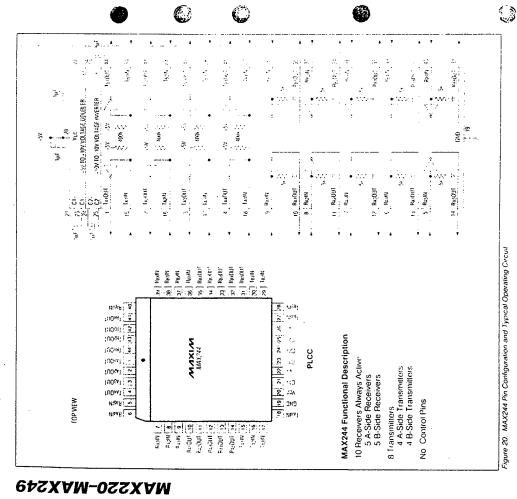


Figure 18 MAX241, MAX223 Pin Conliguration and Typical Operaling Circuit

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10P V1(V)

# +5V-Powered, Multi-Channel RS-232 Drivers/Receivers



100 10 Receivers 5 A-Side Receivers (RAs always active) 5 B-Side Receivers (RRs always active) 33 Res. . . . . . O 34) Record 11. R. . . . 35 Is. - 16 78, R. 7. Pr. 1 26 Beach ٠ ي ي 1 l 75 R **MAX245 Functional Description** 2 Control Pins 1 Receiver Enable (ENR) 1 Transmitter Enable (ENT) 8 Fransmitters 4 A-Side Transmitters 4 B-Side Transmitters #2001 [5 #2001 [7] #2011 [8] 3 mm 1 5 01 1121-70 24. 12.7g F1-11 (13 14.04 3 t His F: # 7. 1, 1,37

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MAXIM

Figure 21 MAX245 Pin Configuration and Typical Operating Circuit

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# +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

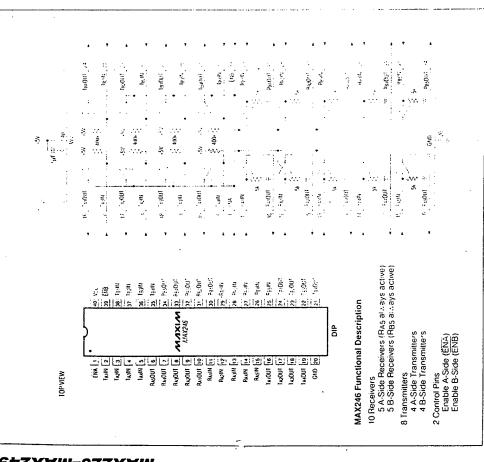


Figure 22. MAX246 Pin Configuration and Typical Operating Circui

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taling je ed 1448 8, 1546 7, 1540 FIGURE : 33 Percent 1.0° Posture 3. 14.00 tel bull 4 HIPS N:-ig 5 推 AAXIA UAKSE 2) Indian 10 Ind [9] INU---21, 1,.... [1] min 1.100 14 1412

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## MAX247 Functional Description

Regist is

REACES D

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Res(01) 34 FNR9: 30

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- 4 A Sign Receivers 5 B-Sign Receivers (RBs a mays active)
  - Fransim tiers
    4 A-S de Transimitiers
    4 B-S de Transimitiers
- Suic Susci
- frate a Receiver A.Side (ENIÀA)
  Eriate a Receiver B.Side (EVIRB)
  Eriate a Transmitter A.Side (EVITA)
  Eriate a Transmitter B.Side (EVITA)

Floure 13 MA-112 Pin Configuration and Typical Operang 1

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10P VIEW

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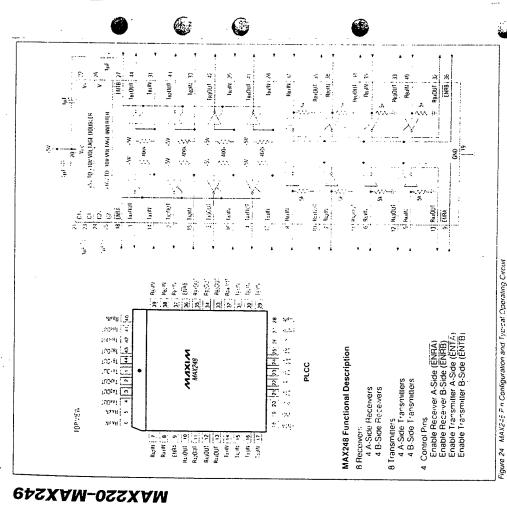
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## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers



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Figure 25 MAX249 Pin Configuration and Typical Operating Circuit

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## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

## Ordering Information (continued)

**642XAM-022XAM** 

MAX222CPN MAX222CWN MAX222C/D MAX222EPN				0000	0.0
MAX222CWN MAX222C/D MAX222EPN	0°C to +70°C	18 Plastic DIP	MAX232AEPE	-40°C to +85°C	to mastic Diff
MAX222C/D MAX222EPN	0°C to +70°C	18 Wide SO	MAX232AESE	-40°C to +85°C	16 Narrow SO
MAX222EPN	0°C to +70°C	Dice*	MAX232AEWE	-40°C to +85°C	16 Wide SO
	40°C to +85°C	18 Plastic DIP	MAX232AEJE	-40°C to +85°C	16 CERDIP
MAX222EWN	40°C to +85°C	18 Wide SO	MAX232AMJE	-55"C to + 125"C	16 CERDIP
	40°C to +85°C	18 CERDIP	MAX232AMLP	-55°C to + 125°C	201.0C
MAX222MJN	55°C to +125°C	18 CEROIP	MAX233CI1	0'C to 1 70'C	20 Plastic Diff
MAX223CAI	0°C to +70°C	28 SSOP	MAX233EPP	-40°C to +85°C	20 Plastic DIP
MAX223CWI	0°C to +70°C	28 Wide SO	MAX233ACPP	0°C to +70°C	20 Plastic DIP
1.44X23C/D	0.C to + 70.C	Dice.	MAZERBACWE	0"C to + 70"C	20 Wide SO
MAX223EA!	40.C to 185.C	28 SSOP	MAX2,33ALPF	AUTC to ABSTC	To Plantic DIP
MAX223EWI	40°C to +85°C	28 Wide SO	MAZZ33AEWP	40°C to +85°C	20 Wide SO
MAX225CWI	0'C to +70"C	28 Wide SO	MAX234CPE	0'C IS + 70'C	16 Plastic Diff
MAX225EWI	.40°C to +85°C	28 Wide SO	MAX234CWE	0°C to +70°C	16 Wide SO
MAX230CPP	0°C to +70°C	20 Plastic DIP	MAY234C/D	0°C to +70°C	Oce.
MAX230CWP	0°C to 170°C	20 Wide SO	MAX234EPE	7.40°C to +85°C	:6 Plastic DIF
MAX230C/D	0°C to +70°C	Dice*	MAX224[WE	40°C to +85°C	16 Wirds, SO
MAX230EPP	-40°C to +85°C	20 Plastic DIP	MAY234E.IF	40°C to +85°C	16 CERDIP
MAX230EWP	-40°C to +85°C	20 Wide SO	MAX234MJE	55°C to +125°C	16 CERDIP
MAX230EJP	.40°C to +85°C	20 CERDIP	MAX235CPG	0°C to + 70°C	24 Wide Plastic Diff
MAX230MJP	55°C to 1125°C	20 CERDIP	MAY235EPG	40 C to . 85 C	24 Web: Plaster DIF
MAX231CPD	0°C to +70°C	14 Plastic DIP	DO PPECKAM	40°C to 185°C.	24 Componer SB
MAX231CWE	0'C to + 70'C	16 Wide SO	MAX235MDG	-55°C to +125°C	24 Ceramic 518
MAX231CJD	0°C to +70°C	14 СЕЯОІР	MAX236CNG	0'C to + 70'C	24 Narrow Plastic Off
MAX231C/D	0°C to +70°C	Dice*	MAX236CWG	0°C to •70°C	24 Wide SO
MAX231EPD	40°C to +85°C	14 Plastic DIP	MAX236C/D	0°C to • 70°C	Dice*
MAX231EWE	.40°C to +85°C	16 Wirse SO	MAX236EMG	-40°C to +85°C	24 Narrow Plastic DIP
MAX231EJD	40°C to +85°C	14 CERDIP	MAX236FWG	-40 C to +85°C	24 Wide SO
MAX231MJD	.55°C to +125°C	14 CERDIF	MAX230FRG	40 C to +85 C	24 Narrow CF RDIF
MAX232CPE	0°C to +70°C	16 Plastic DIP	MAX236MRG	-55°C to + 125°C	24 Narrow CERDIF
MAX232CSE	0°C to +70°C	16 Narrow SO	MAX237CNG	0°C ic •70°C	24 Narrow Plastic Uif*
MAX232CWE	0°C to +70°C	16 Wide SO	MAX237CWG	0°C to +70°C	24 Wide SO
MAX232C/D	0°C to +70°C	Dice*	MAX237C/D	0°C to +70°C	Dice*
MAX232EPE	-40°C to +85°C	16 Plastic DIP	MAX237ENG	-40°C to +85°C	24 Narrow Plastic DIP
MAX232ESE	-40°C to +85°C	16 Narrow SO	MAX237EWG	.40°C to +85°C	24 Wide SO
MAX232EWE	-40°C to +85°C	16 Wide SO	MAX237ERG	-40°C to +85°C	24 Narrow CERDIP
MAX232EJE	-40°C to +85°C	16 CERDIP	MAX237MRG	-55°C to +125°C	24 Narrow CERDIF:
MAX232MJE	-55°C to +125°C	16 CERDIP	MAX238CNG	0°C to +70°C	24 Narrow Plastic DIP
MAX232MLP	-55°C to +125°C	20 LCC	MAX238CWG	0°C to +70°C	24 Wide SO
MAX232ACPE	0°C to +70°C	16 Plastic DIP	MAX238C/D	0°C to +70°C	Dice.
MAX232ACSE	0°C to + 70°C	16 Narrow SO	MAX238ENG	-40°C to +85°C	24 Narrow Plastic DIF:
MAX232ACWE	0°C to +70°C	16 Wide SO	Corract factory fe	Corract factory for dice specifications	

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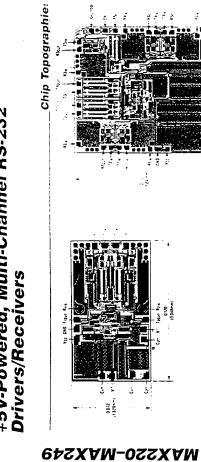
## +5V-Powered, Multi-Channel RS-232 Drivers/Receivers

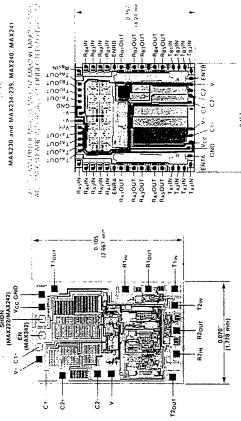
## Ordering Information (continued)

A0°C   10 + 86°C   24 Wide SO   VIXZAJCKE   U°C   10 + 10°C	PART	TEMP. RANGE	PIN-PACKAGE	MAX243CPE	C.C. to 170°C	16 Plastic DIP
MAXZ38ERG         40°C to + 65°C         2a Nariow CERDIP         MAXZ38CWE         0°C to + 10°C           MAXZ38AHG         -56°C to + 125°C         2a Nariow Peste Dif         MAXZ38CWG         0°C to + 70°C           MAXZ38CWG         0°C to - 70°C         2a Nariow Paste Dif         MAXZ38EVE         40°C to + 8°C           MAXZ38CWG         0°C to - 70°C         2a Nariow Paste Dif         MAXZ38CWE         40°C to - 18°C           MAXZ38CWG         0°C to - 70°C         2a Nariow Paste Dif         MAXZ38CWE         40°C to - 18°C           MAXZ38CWG         0°C to - 70°C         2a Nariow CERDIF         MAXZ34CWE         40°C to - 18°C           MAXZ38EWG         40°C to - 18°C         2a Nariow CERDIF         MAXZ44COH         9°C to - 10°C           MAXZ38EWG         40°C to - 10°C         2a Nariow CERDIF         MAXZ44COH         9°C to - 10°C           MAXZ4CCH         0°C to - 10°C         2a Nariow CERDIF         MAXZ46COH         9°C to - 10°C           MAXZ4CCH         0°C to - 10°C         2a Nariow CERDIF         MAXZ46COH         9°C to - 10°C           MAXZ4CCH         0°C to - 10°C         2a Nariow CERDIF         MAXZ46COH         9°C to - 10°C           MAXZ4CCH         0°C to - 10°C         2a Nariow CERDIF         MAXZ46COH         9°C to - 10°C	MAX238EWG	.40°C to 485°C	24 Wide SO	. NAX243CSE	6.7C to + 70°C	16 Narrow SO
MAX23BMRG         -55°C to - 125°C         24 Natrow CERDIP         MAX23BCHO         0°C to - 70°C           MAX23BCWG         0°C to - 70°C         24 Natrow Plastic CF         MAX243EFF         40°C to - 18°C           MAX23BCWG         0°C to - 70°C         22 Wide SO         MAX243EWF         40°C to - 18°C           MAX23BCWG         0°C to - 70°C         24 Wide SO         MAX243EWF         40°C to - 18°C           MAX23BCWG         40°C to - 8°C         24 Marow Plastic DF         MAX243EWF         40°C to - 18°C           MAX23BCWG         40°C to - 8°C         24 Marow CERDIF         MAX24GOH         9°C to - 10°C           MAX23BCWG         40°C to - 10°C         24 Marow CERDIF         MAX24GOH         9°C to - 10°C           MAX24GCM         0°C to - 10°C         28 SSOP         MAX24GOH         9°C to - 10°C           MAX24CM         0°C to - 10°C         28 SSOP         MAX24GCH         9°C to - 10°C           MAX24CM         0°C to - 10°C         28 SSOP         MAX24GCH         9°C to - 10°C           MAX24CM         0°C to - 10°C         28 SSOP         MAX24GCH         9°C to - 10°C           MAX24CM         0°C to - 10°C         28 SSOP         MAX24GCH         9°C to - 10°C           MAX24CM         0°C to - 10°C <th< td=""><td>MAX238ERG</td><td>.40°C to +85°C</td><td>24 Narrow CERDIP</td><td>:JAX243CWE</td><td>0°C to +70°C</td><td>16 Wide SO</td></th<>	MAX238ERG	.40°C to +85°C	24 Narrow CERDIP	:JAX243CWE	0°C to +70°C	16 Wide SO
MAXZ3BCMG         QPC to - 70°C         24 Netroup Paste CpF         MAXZ3BCNG         40°C to - 18°C           MAXZ3BCWG         Q°C to - 70°C         24 Wirde SO         MAXZ3BWE         40°C to - 18°C           MAXZ3BEWG         40°C to - 10°C         Diod*         MAXZ3BWE         40°C to - 10°C           MAXZ3BEWG         40°C to - 10°C         AN Bertow CFRDF         MAXZ4GCH         9°C to - 10°C           MAXZ3BEWG         40°C to - 10°C         24 Nete SO         MAXZ4GCH         9°C to - 10°C           MAXZ3GERG         40°C to - 10°C         24 Nete SO         MAXZ4GCH         9°C to - 10°C           MAXZ4GCA         40°C to - 10°C         24 Nete SO         MAXZ4GCH         9°C to - 10°C           MAXZ4GCA         60°C to - 10°C         28 Nete SO         MAXZ4GCH         9°C to - 10°C           MAXZ4GCA         6°C to - 10°C         28 SSOP         MAXZ4GCH         9°C to - 10°C           MAXZ4GCA         6°C to - 10°C         28 SSOP         MAXZ4GCH         9°C to - 10°C           MAXZ4GCA         6°C to - 10°C         28 SSOP         MAXZ4GCH         9°C to - 10°C           MAXZ4GCA         6°C to - 10°C         28 SSOP         MAXZ4GCH         9°C to - 10°C           MAXZ4GCA         6°C to - 10°C         28 SSOP	MAX238MRG	-55°C to +125°C	24 Narrow CERDIP	" MAX243C/D	0°C to + 70°C	Dice.
MAXZ38CWG         OFC to - 70°C         24 Wide SO         MAXZ38ENE         -40°C to - 88°C           MAXZ38CWG         O°C to - 70°C         Dee*         MAXZ38ENE         -40°C to - 88°C           MAXZ38EWG         -40°C to - 88°C         24 Matrow CERDF         -40°C to - 10°C           MAXZ38EWG         -40°C to - 88°C         24 Matrow CERDF         -40°C to - 10°C           MAXZ38EWG         -40°C to - 48°C         24 Matrow CERDF         -40°C to - 10°C           MAXZ38EWG         -40°C to - 48°C         24 Matrow CERDF         -40°C to - 10°C           MAXZ38EWG         -40°C to - 48°C         24 Matrow CERDF         -40°C to - 10°C           MAXZ44CMI         0°C to - 10°C         -40°C to - 10°C         -40°C to - 10°C           MAXZ44CMI         0°C to - 10°C         -40°C to - 10°C         -40°C to - 10°C           MAXZ44CMI         0°C to - 10°C         -40°C to - 10°C         -40°C to - 10°C           MAXZ45CMI         0°C to - 10°C         -40°C to - 10°C         -40°C to - 10°C           MAXZ45CMI         0°C to - 10°C         -40°C to - 10°C         -40°C to - 10°C           MAXZ45CMI         0°C to - 10°C         -40°C to - 10°C         -40°C to - 10°C           MAXZ45CMI         0°C to - 10°C         -40°C to - 10°C         -40°C to - 10°C	MAX239CING	0°C to +70°C	24 Narrow Plastic Ciff	MAX243EPE	-40°C to +85°C	16 Plastic DIP
MAXZ3GCD         OPC 10 - 70°C         Dice*         MAXZ3GCW         AGC 10 - 48°C         ABARCAGEM         AGC 10 - 48°C         ABARCAGEM         AGC 10 - 48°C         ABARCAGEM         AGC 10 - 48°C         AGC 10	MAX239CWG	0°C to +70°C	24 Wide SO	MAX243ESE	.40°C to +85°C	16 Narrow SO
MAXZHENG         ANTERING	MAX239C/D	0"C to - 70"C	Dice.	MAX243EWE	-40°C to +85°C	16 Wide SO
MAXZ38EWG         40°C to -85°C         24 Wde SO         MAZZ38EWG         56°C to -12°C           MAXZ38ERG         40°C to -85°C         24 Natrow CERDF         MAZZ4GOH         9°C to -17°C           MAXZ30ARRG         56°C to -12°C         24 Natrow CERDF         MAZZ4GOH         9°C to -17°C           MAXZ4GATAI         0°C to -10°C         24 Natrow CTRBH         347-244CAI         10°C to -17°C           MAXZ4GATAI         0°C to -10°C         28 SSOP         347-244CAI         10°C to -17°C           MAXZ4GATAI         0°C to -10°C         28 SSOP         347-244CAI         10°C to -17°C           MAXZ4CAI         0°C to -10°C         28 SSOP         347-244CAI         10°C to -17°C           MAXZ4CAI         0°C to -10°C         28 SSOP         347-246CPI         3°C to -17°C           MAXZ4CAI         0°C to -10°C         28 SSOP         347-246CPI         3°C to -17°C           MAXZ4CAI         0°C to -10°C         28 SSOP         347-246CPI         3°C to -17°C           MAXZ4CAI         0°C to -10°C         28 SSOP         347-246CPI         3°C to -17°C           MAXZ4CAI         0°C to -10°C         28 SSOP         347-246CPI         3°C to -17°C           MAXZ4CAI         0°C to -10°C         28 SSOP         347-246	E. MAXCON NG	40°C to +85°C	24 Narrow Plastic (34)	. MAX243EJF	40°C to +85°C	16 CERDIP
MAXZ23GERG         40°C to +8°°C         24 Natrow CERDF         MAXZ44GOH         9°C to +10°C           MAXZ23GERG         40°C to +2°°C         24 Natrow CERDF         34 Natrow CERDF         10°C to +10°C           MAXZ4CAH         0°C to +10°C         28 SSOP         14AZ24GDH         0°C to +10°C           MAXZ4CAH         0°C to +70°C         28 SSOP         14AZ24GDH         0°C to +10°C           MAXZ4CAH         0°C to -70°C         28 SSOP         MAXZ46CPH         0°C to +10°C           MAXZ4CAH         0°C to -70°C         28 SSOP         MAXZ46CPH         0°C to +10°C           MAXZ4CAH         0°C to -70°C         28 SSOP         MAXZ46CPH         0°C to +10°C           MAXZ4CAH         0°C to -70°C         28 SSOP         MAXZ46CPH         0°C to +10°C           MAXZ4CAH         0°C to -70°C         28 SSOP         MAXZ46CPH         0°C to +10°C           MAXZ4CAH         0°C to -70°C         28 SSOP         MAXZ46CPH         0°C to +10°C           MAXZ4CAH         0°C to -70°C         10°C to +10°C         10°C to +10°C           MAXZ4CAH         0°C to -70°C         10°C to +10°C         10°C to +10°C           MAXZ4CAH         0°C to -70°C         10°C to +10°C         10°C to +10°C           MAXZ4CAH	MAXZ39EWG	40"C to +85°C	24 Wide SO	"SAX243MJE	58°C to + 125°C	16 CEROIP
MAX24CMI         GC to - 1PSTC         24 Nation of Third         MAX24CMI         GC to - 1PSTC           MAX24CMI         GT to - 1PSTC         AT Habite IF         MAX24CMI         TO To - 1PCT           MAX24CMI         GT to - 1PCT         B SSOP         LAAZ45CH         TO To - 1PCT           MAX24CMI         GT to - 1PCT         B SSOP         LAAZ45CH         TO To - 1PCT           MAX24CMI         GT to - 1PCT         B SSOP         LAAZ46CPL         3°C to - 1PCT           MAX24CMI         GT to - 1PCT         B SSOP         MAX246CPL         3°C to - 1PCT           MAX24CMI         GT to - 1PCT         B SSOP         MAX246CPL         3°C to - 1PCT           MAX24.EMI         GT to - 1PCT         B Wide SO         MAX246CPL         3°C to - 1PCT           MAX24.EMI         GT to - 1PCT         B SSOP         MAX246CPL         3°C to - 1PCT           MAX24.EMI         GT to - 1PCT         B Wide SO         MAX246CPL         3°C to - 1PCT           MAX24.EMI         GT to - 1PCT         B Wide SO         MAX246CDI         3°C to - 1PCT           MAX24.EMI         GT to - 1PCT         B Wide SO         MAX246CDI         3°C to - 1PCT           MAX24.EMI         GT to - 1PCT         B Wide SO         MAX246CDI <t< td=""><td>MAX239ERG</td><td>.40°C to +85°C</td><td>24 Narrow CERDIF</td><td>MAX244COH</td><td>0°C to +70°C</td><td>44 PLCC</td></t<>	MAX239ERG	.40°C to +85°C	24 Narrow CERDIF	MAX244COH	0°C to +70°C	44 PLCC
MAXZ4G7MI         QTC In - 7DC         Ad Phase 11         MAZZ4G71         Ab C In - 17CT           MAXZ4G7MI         QTC In - 17DC         Dace*         MAZZ4G71         TO In - 17CT           MAXZ4GAN         QTC In - 7DC         28 SSOP         MAZZ4GCPL         AC In - 17C           MAXZ4GAN         QTC In - 7DC         28 Wade SO         MAZZ4GCPL         AC In - 17C           MAXZ4GAN         QTC In - 7DC         28 SSOP         MAZZ4GCPL         AC In - 17C           MAXZ4GAN         ATT In - 17C         MAZZ4GCPL         AC In - 17C         AC In - 17C           MAXZ4GAN         ATT In - 12C         AMAZA4CPL         AC In - 17C         AC In - 17C           MAXZ4GAN         ATT In - 12C         AMAZA4CPL         AC In - 17C         AMAZA4CPL           MAXZ4GAN         ATT In - 12C         AMAZA4CPL         AC In - 17C         AMAZA4CPL           MAXZ4GAN         ATT IN - 12C         AMAZA4CPL         AC In - 17C         AMAZA4CPL           MAXZ4GAN         ATT IN - 12C         AMAZA4CPL         AC In - 17C         AMAZA4CPL           MAXZ4GAN         ATT IN - 12C         AMAZA4CPL         AC In - 17C         AMAZA4CPL           MAXZ4GAN         ATT IN - 12C         AMAZA4CPL         AC In - 17C         AMAZA4CPL </td <td>MAXZZOMBE</td> <td>55°C to + 125°C</td> <td>24 Narrow CFRDE</td> <td>**************************************</td> <td>0/C to 1/0/C</td> <td>Тисе</td>	MAXZZOMBE	55°C to + 125°C	24 Narrow CFRDE	**************************************	0/C to 1/0/C	Тисе
MAXZAGUN         IVC In . IVC         Dice*         MAXZAGUN         PT. In . IVT           MAXZAGUN         O'C In . IVC         28 SSOP         MAZZAGUN         PT. In . IVT           MAXZAGUN         O'C In . IVC         28 Wide SO         MAZZAGUN         O'C In . IVT           MAXZAGUN         O'C In . IVC         28 SSOP         MAZZAGUN         O'C In . IVT           MAXZAGUN         O'C In . IVC         28 SSOP         MAZZAGUN         O'C In . IVT           MAXZAGUN         O'C In . IVC         28 SSOP         MAZZAGUN         O'C In . IVT           MAXZAGUN         O'C In . IVC         28 SSOP         MAZZAGUN         O'C In . IVT           MAXZAGUN         O'C In . IVC         18 Pinsac Dir         MAZZAGUN         O'C In . IVT           MAXZAGUN         O'C In . IVC         IB Wide SO         MAZZAGUN         O'C In . IVT           MAXZAGUN         O'C In . IVC         IB Pinsac Dir         MAZZAGUN         O'C In . IVT           MAXZAGUN         O'C In . IVC         IB Pinsac Dir         MAZZAGUN         O'C In . IVT           MAXZAGUN         O'C In . IVC         IB Pinsac Dir         MAZZAGUN         O'C In . IVT           MAXZAGUN         O'C In . IVC         IB Pinsac Dir         MAZZAGUN         O'C In . I	MAX240CMH	O'C to 70 C	44 Plasac FP	SACSAN OFF	A+ C In + H2, 0	44 11 636.
MAXZATCAI         UTC In - 10°C         28 SSOP         LIANZAGEPL         40°C In - 10°C         48°C           MAXZATCAI         0°C In - 70°C         28 Wide SO         MAZZAGEPL         40°C In - 10°C         48°C           MAXZATCAI         0°C In - 70°C         28 SSOP         MAZZAGEPL         40°C In - 10°C           LAXXATEVII         40°C In - 70°C         20 SSOP         MAZZAGCII         7°C In - 10°C           MAXZAZUH         0°C In - 70°C         18 Passic DIP         "AXZAGCII         40°C In - 10°C           MAXZAZUH         0°C In - 70°C         18 Passic DIP         "AXZAGCII         40°C In - 10°C           MAXZAZUH         0°C In - 70°C         18 Passic DIP         "AXZAGCII         40°C In - 10°C           MAXZAZUH         0°C In - 70°C         18 Passic DIP         "AXZAGCII         0°C In - 10°C           MAXZAZUH         0°C In - 70°C         18 Passic DIP         "AXZAGCII         0°C In - 10°C           MAXZAZUH         0°C In - 70°C         18 Passic DIP         "AXZAGCII         0°C In - 10°C           MAXZAZUH         0°C In - 70°C         18 Passic DIP         "AXZAGCII         0°C In - 10°C           MAXZAZUH         0°C In - 70°C         18 Passic DIP         "AXZAGCII         0°C In - 10°C           MAXZAZU	MAX240CAD	0°C to + 70°C	Dice*	MAX245031	17"C: 10 + 70"C	40 Pastic DIF
RAXZACENT         O'C to - 70°C         28 Wide SO         MAXZAGEPL         - 40°C to - 80°C           MAXZACTO         O'C to - 70°C         Doe*         MAXZAGEPL         - 70°C to - 70°C           MAXZACTO         O'C to - 70°C         Doe*         MAXZAGEPL         - 70°C to - 70°C           MAXZACTO         O'C to - 70°C         28 SSOP         MAXZAGED         - 70°C to - 70°C           MAXZAGENH         O'C to - 70°C         20 SSOP         MAXZAGENH         - 70°C to - 70°C           MAXZAGENH         O'C to - 70°C         18 Master DIP         - 44XZAGECH         - 70°C to - 70°C           MAXZAGENH         O'C to - 70°C         18 Mater SO         - 44XZAGECH         - 70°C to - 70°C           MAXZAGENH         O'C to - 70°C         18 Mater SO         - 44XZAGECH         - 70°C to - 70°C           MAXZAGENH         O'C to - 70°C         18 Mater SO         - 44XZAGECH         - 70°C to - 70°C           MAXZAGENH         O'C to - 70°C         18 Mater SO         - 44XZAGECH         - 70°C to - 70°C           MAXZAGENH         O'C to - 70°C         18 Mater SO         - 44XZAGECH         - 70°C to - 70°C           MAXZAGENH         O'C to - 70°C         18 Mater SO         - 44XZAGECH         - 70°C to - 70°C           MAXZAGENH         O'C		0"C to + 70°C	28 SSOP	MAX245C/D	U.C. to . 70°C	Dage.
0°C to -70°C   0°C		0°C to - 70°C	28 Wide SO	MAX245EPL	-40 C to +85°C	40 Prastic DIP
40°C to -66°C   28 SSOP   MAX246CO   0°C to -10°C     40°C to -86°C   28 SSOP   MAX247CH   40°C to -66°C     60°C to -70°C   28 SSOP   MAX247CH   0°C to -10°C     60°C to -70°C   18 Mate SO   MAX247CH   0°C to -10°C     60°C to -70°C   18 Mate SO   MAX246CO   0°C to -10°C     60°C to -70°C   18 Mate SO   MAX246CO   0°C to -10°C     60°C to -86°C   18 Mate SO   MAX246CO   0°C to -10°C     60°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     60°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     60°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   MAX246CO   0°C to -10°C     70°C to -66°C   18 Mate SO   18 Mate SO   18 MAX246CO   18	MAX24:C/D	0°C to +70°C	Orce*	MAX246CPL	2.C to + 70°C	40 Plastic DIP
	MAXZ	40"C to -65°C	28 SSOP	MAX245C/D	0°C to +70°C	Dice.
1	MAXZATEWI	40°C to +85°C	28 Wide SO	MXZ46EPL	40'C to 185'C	40 Plastic DIP
0°C in - 7°S C   18 Prioshe Dif   VAX247CH   C C in - 7°C C   0°C in - 7°S C   0°C in - 7°C in - 7°S C   0°C in - 7°C	MAX242CAP	0°C to - 70 C	20 SSOP	MAX247CPI	D.07 + 61 D.0	46 Prashe DIP
0   0   0   0   0   0   0   0   0   0	MAX2:2CFN	0°C to .73°C	18 Plastic DIF	SAX247CAD	C.C to + 70.C	Dice*
OrC to -20°C   Dee*   MAX246(COH   O°C to -70°C	MAX242CWIU	0°C to - 75°C	18 Wide SO	MAX247FPL	. 40°C to +85°C	40 Flasic DIP
APPC to -85°C   18 Mate 50   MAX248CD   (PC to +70°C   APPC to -86°C   18 Mate 50   MAX249CD   (PC to +70°C   APPC to -86°C   18 CERDP   MAX249CD   (PC to +70°C   APPC   APPC	MAXPARCAD	0°C to - 70°C	Dice*	MAX248COH	0°C to + 70°C	44 FLCC
40°C to -65°C 18 Wide 50 1652841.01 40°C to 70°C 40°C to 45°C 18 CEROP 16528495011 6°C to 70°C 55°C 18 CEROP 1652849501 40°C to 48°C	MAX2421 PN	40°C to -85°C	18 Plaste: DP	MXZ48CA)	O'C to + 70°C	Dice.
40°C to -65°C 18 CERDIP MAX249CO11 (°C to -70°C -55°C to -125°C 18 CERDIP 'MX249CO11 -40°C to -85°C	LAAXZ42EWIN	40°C to +#5°C	18 Wide 50	HO BEACKER,	40°C to +85°C	44 PLCC
.55°C to +125°C 18 CERDIP :1AX249EOH -40°C to +85°C	MAX2:2L.ID	40°C to -65°C	18 CERDIP	MAX249CCH	O'C to . 70 C	44 Pt C.C.
	MAX242MJN	-55"C to - 125°C	18 CERDIP	MAX249EOH	-40"C to +85"C	44 PLCC

MAXIM

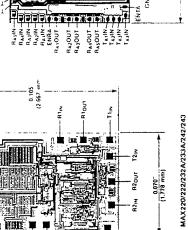
# +5V-Powered, Multi-Channel RS-232





MAX230 and MAX234-239, MAX240, MAX241

MAX231, MAX232 and MAX233





COMMECT SUBSTRATE TO V4

Maxim cannot assume responsibility for use of any circuity. President implied. Maxim reserves: "Profit to change the circuity and specifical

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## HS-82C55ARH

Radiation Hardened CMOS Programmable Peripheral Interface

September 1995

## Features

- · Radiation Hardened
  - Total Dose >105 RAD (Si)
  - Transient Upset <10<sup>8</sup> RAD (Si)/s
  - Latch Up Free EPI-CMOS
- · Low Power Consumption
  - IDDSB = 20μA
- Pin Compatible with NMOS 8255A and the Harris 82C55A
- · High Speed, No "Wait State" Operation with 5MHz HS-80C86RH
- 24 Programmable I/O Pins
- Bus-Hold Circuitry on All I/O Ports Eliminates Pull-Up Resistors
- · Direct Bit Set/Reset Capability
- · Enhanced Control Word Read Capability
- · Hardened Field, Self-Aligned, Junction Isolated CMOS Process
- · Single 5V Supply
- · 2.0mA Drive Capability on All I/O Port Outputs
- Military Temperature Range: -55°C to +125°C

## Description

The Harris HS-82C55ARH is a high performance, radiation hardened CMOS version of the industry standard 8255A and is manufactured using a hardened field, self-aligned silicongate CMOS process. It is a general purpose programmable I/O device which may be used with many different microprocessors. There are 24 I/O pins which are organized into two 8-bit and two 4-bit ports. Each port may be programmed to function as either an input or an output. Additionally, one of the 8-bit ports may be programmed for bi-directional operation and the two 4-bit ports can be programmed to provide handshaking capabilities. The high performance, radiation hardness, and industry standard configuration of the HS-82C55ARH make it compatible with the HS-80C86RH radiation hardened microprocessor.

Static CMOS circuit design insures low operating power. Bus hold circuitry eliminates the need for pull-up resistors. The Harris hardened field CMOS process results in performance equal to or greater than existing radiation resistant products at a fraction of the power.

## Ordering Information

PART NUMBER	TEMPERATURE	PACKAGE
HS1-82C55ARH-Q	-55°C to +125°C	40 Lead SBDIP
HS1-82C55ARH-8	-55°C to +125°C	40 Lead SBDIP
HS1-82C55ARH/Sample	+25°C	40 Lead SBDIP

## **Pinout**

40 LEAD CERAMIC DUAL-IN-LINE METAL SEAL PACKAGE (SBDIP) MIL-STD-1835 CDIP2-T40 TOP VIEW

PA3	回	U	40 PA4	
PA2	2		39 PA5	
PA1	3		38 PA6	
PA0	4		37 PA7	
RD	5		36 WR	
<del>cs</del>	6		35 RESET	
GND	7		34 D0	
<b>A</b> 1	8		33 D1	
A0	9		32 D2	
PC7	10		31 D3	
PC6	11		30 D4	
PC5	12		29 D5	
PC4	13		28 D6	
PC0	14		27 D7	
PC1	15		26 VDD	
PC2	16		25 PB7	
PC3	17		24 PB6	
PB0	18		23 PB5	
PB1	19		22 PB4	
PB2	20		21 PB3	

## Pin Description

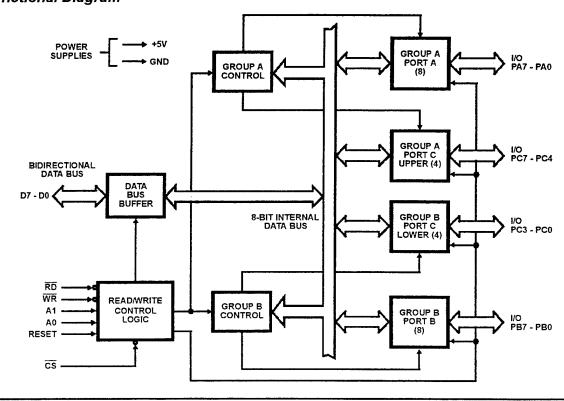
PIN	DESCRIPTION
D7 - D0	Data Bus (Bi-Directional
RESET	Reset Input
<del>CS</del>	Chip Select
RD	Read Input
WR	Write Input
A0 - A1	Port Address
PA7 - PA0	Port A (Bit)
PB& - PB0	Port B (Bit)
PC7 - PC0	Port C (Bit)
VDD	+5 volts
GND	0 volts

## HS-82C55ARH

## Pin Description

SYMBOL	PIN NUMBERS	TYPE	DESCRIPTION
PA0-7	1-4, 37-40	1/0	Port A: General purpose I/O Port. Data direction and mode is determined by the contents of the Control Word.
PB0-7	18-25	1/0	Port B: General purpose I/O port. See Port A.
PC0-3	14-17	1/0	Port C (Lower): Combination I/O port and control port associated with Port B. See Port A.
PC4-7	10-13	1/0	Port C (Upper): Combination I/O Port and control port associated with Port A. See Port A.
D0-7	27-34	I/O	Bidirectional Data Bus: Three-State data bus enabled as an input when CS and WR are low and as an output when CS and RD are low.
VDD	26	1	VDD: The +5V power supply pin. A $0.1\mu F$ capacitor between pins 26 and 7 is recommended for decoupling.
GND	7	1	Ground.
cs	6		Chip Select: A "low" on this input pin enables the communication between the HS-82C55ARH and the CPU.
RD	5	l	Read: A "low" on this input pin enables the HS-82C55ARH to send the data or status information to the CPU on the data bus. In essence, it allows the CPU to "read from" the HS-82C55ARH.
WR	36		Write: A "low" on this input pin enables the CPU to write data or control words into the HS-82C55ARH.
A0 and A1	8, 9	ı	Port Select 0 and Port Select 1: These input signals, in conjunction with the RD and WR inputs, control the selection of one of the three ports or the control word registers. They are normally connected to the Least Significant Bits of the address bus (A0 and A1).
Reset	35	1	Reset: A "high" on this input clears the control register and all ports (A, B, C) are set to the input mode. "Bus hold" devices internal to the HS-82C55ARH will hold the I/O port inputs to a logic "1" state with a maximum hold current of 400µA.

## Functional Diagram



## Reliability Information **Absolute Maximum Ratings** Thermal Resistance $\theta_{JA}$ 40°C/W 6°C/W Input, Output or I/O Voltage . . . . . . . . . . . VSS-0.3V to VDD+0.3V Maximum Package Power Dissipation at +125°C Ambient Storage Temperature Range . . . . . . . . . -65°C to +150°C Junction Temperature.....+175°C If device power exceeds package dissipation capability, provide heat Lead Temperature (Soldering 10s).....+300°C sinking or derate linearly at the following rate: CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied **Operating Conditions**

## TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

<u> </u>			amouto :		LIMITS		
PARAMETER	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	MIN	MAX	UNITS
TTL Output High Voltage	VOH1	VDD = 4.5V, IO = -2.5mA, VIN = 0V, 4.5V	1, 2, 3	-55°C, +25°C, +125°C	3.0	-	٧
CMOS Output High Voltage	VOH2	VDD = 4.5V, IO = -100μA, VIN = 0V, 4.5V	1, 2, 3	-55°C, +25°C, +125°C	VDD- 0.4	-	٧
Output Low Voltage	VOL	VDD = 4.5V, IO = 2.5mA, VIN = 0V, 4.5V	1, 2, 3	-55°C, +25°C, +125°C	-	0.4	٧
Input Leakage Current	IIL or IIH	VDD = 5.5V, VIN = 0V, 5.5V	1, 2, 3	-55°C, +25°C, +125°C	-1.0	1.0	μА
Output Leakage Current	IOZL or IOZH	VDD = 5.5V, VIN = 0V, 5.5V	1, 2, 3	-55°C, +25°C, +125°C	-10	10	μA
Input Current Bus Hold High	ІВНН	VDD = 4.5V or 5.5V, VIN = 3.0V (See Note 1) Ports A, B, C	1, 2, 3	-55°C, +25°C, +125°C	-800	-60	μΑ
Input Current Bus Hold Low	IBHL	VDD = 4.5V or 5.5V, VIN = 1.0V (See Note 2) Port A	1, 2, 3	-55°C, +25°C, +125°C	60	800	μΑ
Standby Power Supply Current	IDDSB	VDD = 5.5V, IO = 0mA, VIN =GND or VDD	1, 2, 3	-55°C, +25°C, +125°C	-	20	μА
Darlington Drive Voltage	VDAR	VDD = 4.5V, IO = -2.0mA, VIN = GND or VDD	1, 2, 3	-55°C, +25°C, +125°C	3.9	-	٧
Functional Tests	FT	VDD = 4.5V and 5.5V, VIN_= GND or VDD, f = 1MHz	7, 8A, 8B	-55°C, +25°C, +125°C		-	-
Noise Immunity Functional Test (Note 4)	FN	VDD = 5.5V, VIN = GND or VDD - 1.5V and VDD = 4.5V, VIN = 0.8V or VDD	7, 8A, 8B	-55°C, +25°C, +125°C	-	-	-

## NOTES:

1. IBHH should be measured after raising VIN and then lowering to 3.0V.

Operating Voltage Range . . . . . . . . . . . . . . . . . +4.5V to +5.5V

Operating Temperature Range . . . . . . . . -55°C to +125°C

- 2. IBHL should be measured after lowering VIN to VSS and then raising to 0.8V.
- 3. No internal current limiting exists on the Port Outputs. A resistor must be added externally to limit the current.
- 4. For VIH (VDD = 5.5V) and VIL (VDD = 4.5V) each of the following groups is tested separately with all other inputs using VIH = 2.6V. VIL = 0.4V: PA, PB, PC, Control Pins (Pins 5, 6, 8, 9, 35, 36).

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS T<sub>A</sub> = -55°C to +125°C

			SUB-		LIN	IITS	
PARAMETER	SYMBOL	CONDITIONS	GROUPS	TEMPERATURE	MIN	MAX	UNITS
READ							
Address Stable Before	TAVRL	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	0	-	ns
Address Stable After RD	TRHAX	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	0	-	ns
RD Pulse Width	TRLRH	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	250	•	ns
Data Valid From RD	TRLDV	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	-	200	ns
Data Float After RD	TRHDX	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	10	-	ns
Time Between RDs and/ or WRs	TRWHRWL	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	300	-	ns
WRITE							
Address Stable Before WR	TAVWL.	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	0	-	ns
Address Stable After WR	TWHAX	VDD = 4.5, 5.5V, Ports A and B	9, 10, 11	-55°C, +25°C, +125°C	20	-	ns
		VDD = 4.5, 5.5V, Port C	9, 10, 11	-55°C, +25°C, +125°C	100	,	ns
WR Pulse Width	TWLWH	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	100	-	ns
Data Valid to WR High	TDVWH	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	100	-	ns
Data Valid After WR High	TWHDX	VDD = 4.5, 5.5V, Ports A and B	9, 10, 11	-55°C, +25°C, +125°C	30	-	ns
		VDD = 4.5, 5.5V, Port C	9, 10, 11	-55°C, +25°C, +125°C	100	-	
OTHER TIMINGS							
WR = 1 to Output	TWHPV	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	-	350	ns
Peripheral Data Before RD	TPVRL	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	0	-	ns
Peripheral Data After RD	TRHPX	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	0	-	ns
ACK Pulse Width	TKLKH	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	200	-	ns
STB Pulse Width	TSLSH	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	100	-	ns
Peripheral Data Before STB High	TPVSH	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	20	-	ns
Peripheral Data After STB High	TSHPX	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	50	-	ns
ACK = 0 to Output	TKLPV	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	-	175	ns
ACK = 1 to output Float	TKHPZ	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	10	-	ns

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS  $T_A = -55^{\circ}C$  to +125°C (Continued)

			SUB-		LIM	IITS	
PARAMETER	SYMBOL	CONDITIONS	GROUPS	TEMPERATURE	MIN	MAX	UNITS
WR = 1 to OBF = 0	TWHOL	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	-	150	ns
ACK = 0 to OBF = 1	TKLOH	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	-	150	ns
STB = 0 to IBF = 1	TSLIH	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	-	150	ns
RD = 1 to IBF = 0	TRHIL	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	-	150	ns
RD = 0 to INTR = 1	TRLNL	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	-	200	ns
STB = 1 t INTR = 1	тѕнин	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	<del>-</del>	150	ns
ACK = 1 to INTR = 1	TKHNH	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	-	150	ns
WR = 0 to INTR = 0	TWLNL	VDD = 4.5, 5.5V	9, 10, 11	-55°C, +25°C, +125°C	-	200	ns
RESET Pulse Width	TRSHRSL	VDD = 4.5, 5.5V (Note 2)	9, 10, 11	-55°C, +25°C, +125°C	500	-	ns

## NOTES

- 1. AC's tested at worst case VDD, guaranteed over full operating range.
- 2. Period of initial RESET pulse after power-on must be at least 50µs. Subsequenct RESET pulses may be 500ns minimum.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

				LIN	IITS	
PARAMETER	SYMBOL	CONDITIONS	TEMPERATURE	MIN	MAX	UNITS
Input Capacitance	CIN	VDD = Open, f = 1MHz, All measurements referenced to device ground	T <sub>A</sub> = +25°C	<u>-</u>	10	pF
I/O Capacitance	CI/O .	VDD = Open, f = 1MHz, All measurements referenced to device ground	T <sub>A</sub> = +25°C	-	20	pF
Data Float After RD	TRHDX	VDD = 4.5V and 5.5V	-55°C < T <sub>A</sub> < +125°C	-	75	ns
ACK = 1 to Output Float	TKHPZ	VDD = 4.5V and 5.5V	-55°C < T <sub>A</sub> < +125°C	-	250	ns <sub>.</sub>

NOTE: The parameters listed in Table 3 are controlled via design or process parameters and are not directly tested. These parameters are characterized upon initial design release and upon design changes which would affect these characteristics

## TALBE 4. POST 100K RAD ELECTRICAL PERFORMANCE CHARACTERISTICS

See +25°C limits in Table 1 and Table 2 for Post RAD limits (Subgroups 1, 7, 9)

TABLE 5. BURN-IN DELTA PARAMETERS (+25°C)

PARAMETER	SYMBOL	DELTA LIMITS
Static Current	IDDSB	±10μA
Input Leakage Current	IIL, IIH	±200nA
Output Leakage Current	IOŽL, IOŽH	±2μA
Low Level Output Voltage	VOL	±80mV
TTL Output High Voltage	VOH1	±600mV
CMOS Output High Voltage	VOH2	±150mV

## TABLE 6. APPLICABLE SUBGROUPS

		GROUP A SUBGROUPS				
CONFORMANCE GROUP	MIL-STD-883 METHOD	TESTED FOR -Q	RECORDED FOR -Q	TESTED FOR -8	RECORDED FOR -8	
Initial Test	100% 5004	1, 7, 9	1 (Note 2)	1, 7, 9		
Interim Test	100% 5004	1, 7, 9, Δ	1, ∆ (Note 2)	. 1, 7, 9		
PDA	100% 5004	1, 7, ∆	-	1, 7	-	
Final Test	100% 5004	2, 3, 8A, 8B, 10, 11	· -	2, 3, 8A, 8B, 10, 11		
Group A (Note 1)	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	-	1, 2, 3, 7, 8A, 8B, 9, 10, 11		
Subgroup B5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Δ	1, 2, 3, ∆ (Note 2)	N/A		
Subgroup B6	Sample 5005	1, 7, 9	-	N/A		
Group C	Sample 5005	N/A	N/A	1, 2, 3, 7, 8A, 8B, 9, 10, 11		
Group D	Sample 5005	1, 7, 9	-	1,7,9		
Group E, Subgroup 2	Sample 5005	1, 7, 9		1,7.9		

## NOTES:

- 1. Alternate Group A testing in accordance with MIL-STD-883 method 5005 may be exercised.
- 2. Table 5 parameters only

## HS-82C55ARH

## Harris Space Level Product Flow -Q

Wafer Lot Acceptance (All Lots) Method 5007 (Includes SEM)

GAMMA Radiation Verification (Each Wafer) Method 1019, 2 Samples/Wafer, 0 Rejects

100% Die Attach

100% Nondestructive Bond Pull, Method 2023

Sample - Wire Bond Pull Monitor, Method 2011

Sample - Die Shear Monitor, Method 2019 or 2027

100% Internal Visual Inspection, Method 2010, Condition A

CSI and/or GSI PreCap (Note 6)

100% Temperature Cycle, Method 1010, Condition C, 10 Cycles

100% Constant Acceleration, Method 2001, Condition per Method 5004

100% PIND, Method 2020, Condition A

100% External Visual

100% Serialization

100% Initial Electrical Test (T0)

100% Static Burn-In 1, Condition A or B, 72 Hours Min, +125°C Min, Method 1015

100% Interim Electrical Test 1 (T1)

100% Delta Calculation (T0-T1)

100% PDA 1, Method 5004 (Note 1)

100% Dynamic Burn-In, Condition D, 240 Hours, +125°C or Equivalent, Method 1015

100% Interim Electrical Test 2(T2)

100% Delta Calculation (T0-T2)

100% PDA 2, Method 5004 (Note 1)

100% Final Electrical Test

100% Fine/Gross Leak, Method 1014

100% Radiographic (X-Ray), Method 2012 (Note 2)

100% External Visual, Method 2009

Sample - Group A. Method 5005 (Note 3)

Sample - Group B, Method 5005 (Note 4)

Sample - Group D, Method 5005 (Notes 4 and 5)

100% Data Package Generation (Note 7)

CSI and/or GSI Final (Note 6)

## NOTES:

- 1. Failures from subgroup 1, 7 and deltas are used for calculating PDA. The maximum allowable PDA = 5% with no more than 3% of the failures from subgroup 7.
- 2. Radiographic (X-Ray) inspection may be performed at any point after serialization as allowed by Method 5004.
- 3. Alternate Group A testing may be performed as allowed by MIL-STD-883, Method 5005.
- 4. Group B and D inspections are optional and will not be performed unless required by the P.O. When required, the P.O. should include separate line items for Group B Test, Group B Samples, Group D Test and Group D Samples.
- 5. Group D Generic Data, as defined by MIL-I-38535, is optional and will not be supplied unless required by the P.O. When required, the P.O. should include a separate line item for Group D Generic Data. Generic data is not guaranteed to be available and is therefore not available in all cases.
- 6. CSI and/or GSI inspections are optional and will not be performed unless required by the P.O. When required, the P.O. should include separate line items for CSI PreCap inspection, CSI final inspection, GSI PreCap inspection, and/or GSI final inspection.
- 7. Data Package Contents:
  - Cover Sheet (Harris Name and/or Logo, P.O. Number, Customer Part Number, Lot Date Code, Harris Part Number, Lot Number, Quantity).
  - Wafer Lot Acceptance Report (Method 5007). Includes reproductions of SEM photos with percent of step coverage.
  - GAMMA Radiation Report. Contains Cover page, disposition, Rad Dose, Lot Number, Test Package used, Specification Numbers, Test
    equipment, etc. Radiation Read and Record data on file at Harris.
  - X-Ray report and film. Includes penetrometer measurements.
  - Screening, Electrical, and Group A attributes (Screening attributes begin after package seal).
  - Lot Serial Number Sheet (Good units serial number and lot number).
  - · Variables Data (All Delta operations). Data is identified by serial number. Data header includes lot number and date of test.
  - Group B and D attributes and/or Generic data is included when required by the P.O.
  - The Certificate of Conformance is a part of the shipping invoice and is not part of the Data Book. The Certificate of Conformance is signed by an authorized Quality Representative.

## HS-82C55ARH

## Harris Space Level Product Flow -8

GAMMA Radiation Verification (Each Wafer) Method 1019, 2 Samples/Wafer, 0 Rejects

100% Die Attach

Periodic- Wire Bond Pull Monitor, Method 2011

Periodic- Die Shear Monitor, Method 2019 or 2027

100% Internal Visual Inspection, Method 2010, Condition B

CSI an/or GSI PreCap (Note 5)

100% Temperature Cycle, Method 1010, Condition C, 10 Cycles

100% Constant Acceleration, Method 2001, Condition per Method 5004

100% External Visual

100% Initial Electrical Test

100% Dynamic Burn-In, Condition D, 160 Hours, +125°C or Equivalent, Method 1015

100% Interim Electrical Test

100% PDA, Method 5004 (Note 1)

100% Final Electrical Test

100% Fine/Gross Leak, Method 1014

100% External Visual, Method 2009

Sample - Group A, Method 5005 (Note 2)

Sample - Group B, Method 5005 (Note 3)

Sample - Group C, Method 5005 (Notes 3 and 4)

Sample - Group D, Method 5005 (Notes 3 and 4)

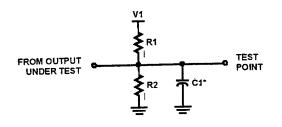
100% Data Package Generation (Note 6)

CSI and/or GSI Final (Note 5)

## NOTES:

- 1. Failures from subgroup 1, 7 are used for calculating PDA. The maximum allowable PDA = 5%.
- 2. Alternate Group A testing may be performed as allowed by MIL-STD-883, Method 5005.
- 3. Group B, C and D inspections are optional and will not be performed unless required by the P.O. When required, the P.O. should include separate line items for Group B Test, Group C Test, Group C Samples, Group D Test and Group D Samples.
- 4. Group C and/or Group D Generic Data, as defined by MIL-I-38535, is optional and will not be supplied unless required by the P.O. When required, the P.O. should include a separate line item for Group C Generic Data and/or Group D Generic Data. Generic data is not guaranteed to be available and is therefore not available in all cases.
- CSI and/or GSI inspections are optional and will not be performed unless required by the P.O. When required, the P.O. should include separate line items for CSI PreCap inspection, CSI final inspection, GSI PreCap inspection, and/or GSI final inspection.
- 6. Data Package Contents:
  - Cover Sheet (Harris Name and/or Logo, P.O. Number, Customer Part Number, Lot Date Code, Harris Part Number, Lot Number, Quantity).
  - GAMMA Radiation Report. Contains Cover page, disposition, Rad Dose, Lot Number, Test Package used, Specification Numbers, Test
    equipment, etc. Radiation Read and Record data on file at Harris.
  - Screening, Electrical, and Group A attributes (Screening attributes begin after package seal).
  - · Group B, C and D attributes and/or Generic data is included when required by the P.O.
  - The Certificate of Conformance is a part of the shipping invoice and is not part of the Data Book. The Certificate of Conformance is signed
    by an authorized Quality Representative.

## AC Test Circuit

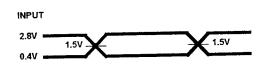


Includes stray and jig capacitance

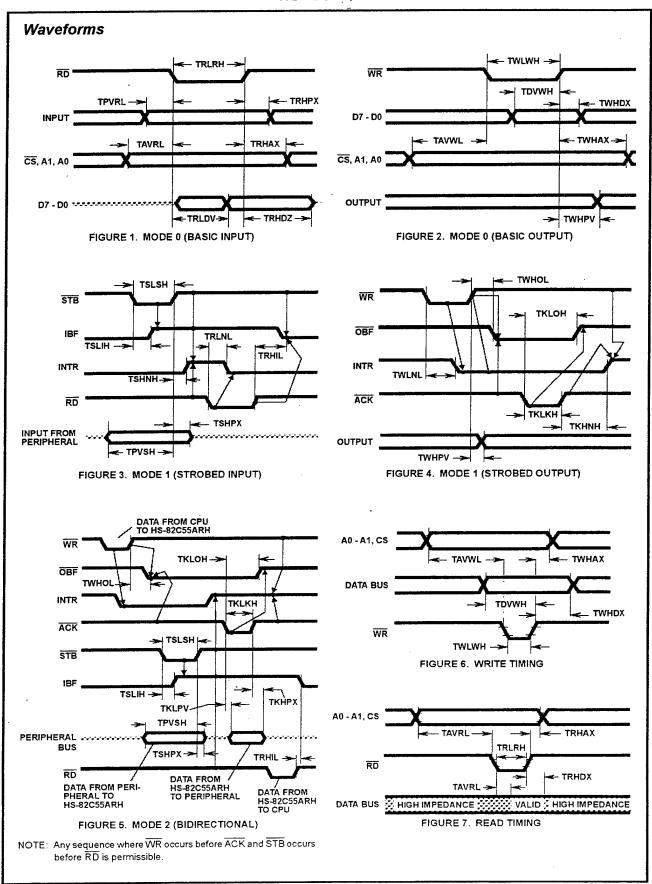
## TEST CONDITIONS DEFINITION TABLE

V1	R1	R2	C1
1.7V	523Ω	Open	150pF

## AC Testing Input, Output Waveforms

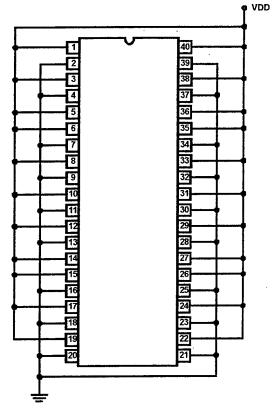


NOTE: AC Testing: All parameters tested as per test circuits. Input rise and fall times are driven at 1V/ns.



# **Burn-In Circuits**

PROGRAMMABLE PERIPHERAL INTERFACE

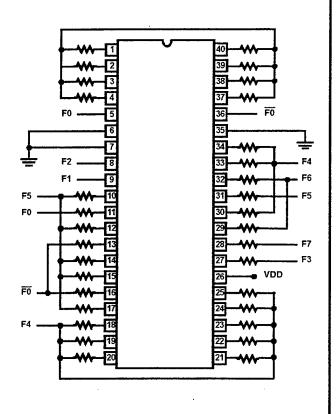


STATIC CONFIGURATION

# NOTES:

- 1. VDD = 6.0V ± 0.5%
- 2. IDD <500µA
- 3. T<sub>A</sub> Min = +125°C

## PROGRAMMABLE PERIPHERAL INTERFACE



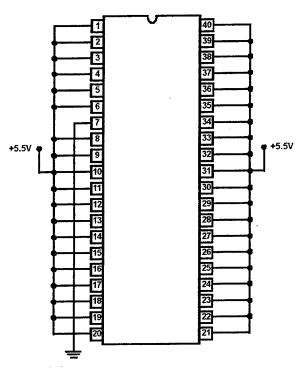
# DYNAMIC CONFIGURATION

# NOTES:

- 1. VDD = 6.0V ± 5% for Burn-In
- 2.  $VDD = 5.0V \pm 5\%$  for Life Test
- 3. All resistors are  $10K\Omega \pm 5\%$
- 4. -0.3V ≤ VIL ≤ 0.8V
- 5. VDD 1.0V ≤ VIH ≤ VDD
- 6. IDD < 5mA
- 7. F0 = 10KHz, 50% Duty cycle
- 8. F1 = F0/2; F2 = F1/2; F3 = F2/2; F4 = F3/2 . . . F7 = F6/2
- 9. TA Min = +125°C

# Irradiation Circuit

CMOS PROGRAMMABLE PERIPHERAL INTERFACE



NOTE:

1. VDD = 5.5V

# Functional Description

The HS-82C55ARH is a programmable peripheral interface designed to allow microcomputer systems to control and interface with all types of peripheral devices. It has the ability to generate and respond to all asynchronous handshaking signals necessary to transfer data to and from peripheral devices, and it can also interrupt the processor when a peripheral needs servicing. These capabilities allow the HS-82C55ARH to be used in an unlimited number of applications including EXTERNAL SYSTEM CONTROL, ASYNCHRONOUS DATA TRANSFER, and SYSTEMS MONITORING.

## **Data Bus Buffer**

This tri-state bidirectional 8-bit buffer is used to interface the HS-82C55ARH to the system data bus (see Figure 8). Data is transmitted or received by the buffer upon execution of input or output instructions by the CPU. Control words and status information are also transferred through the data bus buffer.

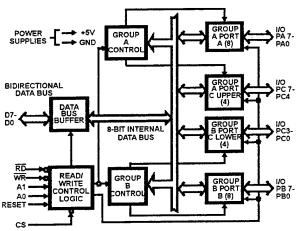


FIGURE 8. BLOCK DIAGRAM DATA BUS BUFFER, READWRITE, GROUP A AND B CONTROL LOGIC FUNCTIONS

## Read/Write and Control Logic

The function of this block is to manage all of the internal and external transfer of both Data and Control or Status words. It accepts inputs from the CPU Address and Control busses and in turn, issues commands to both of the Control Groups.

## Group A and Group B Controls

The functional configuration of each port is programmed by the systems software. In essence, the CPU writes a control word to the HS-82C55ARH. The control word contains information such as "mode", "bit set", "bit reset", etc., that initializes the functional configuration of the HS-82C55ARH.

Each of the Control blocks (Group A and Group B) accepts "commands" from the Read/Write Control Logic, receives "control words" from the internal data bus and issues the proper commands to its associated ports.

Control Group - Port A and Port C upper (C7 - C4)

Control Group - Port B and Port C lower (C3 - C0).

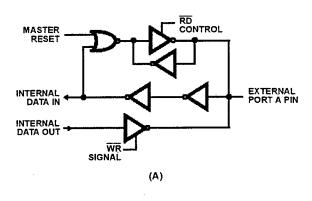
## Ports A, B, C

The HS-82C55ARH contains three 8-bit ports (A, B and C). All can be configured to a wide variety of functional characteristics by the system software but each has its own special features or "personality" to further enhance the power and flexibility of the HS-82C55ARH.

Port A One 8-bit data output latch/buffer and one 8-bit data input latch. Both "pull-up" and "pull-down" bus hold devices are present on Port A. See Figure 9A.

Port B One 8-bit data input/output latch/buffer and one 8-bit data input buffer. See Figure 9B.

Port C One 8-bit data output latch/buffer and one 8-bit data input buffer (no latch for input). This port can be divided into two 4-bit ports under the mode control. Each 4-bit port contains a 4-bit latch and can be used for the control signal outputs and status signal inputs in conjunction with Ports A and B. See Figure 9B.



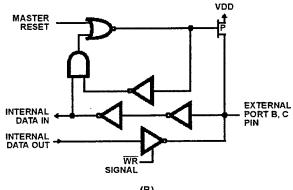


FIGURE 9. I/O PORT CONFIGURATION

# Operational Description

# **Control Word**

The data direction and mode of Ports A. B and C are determined by the contents of the Control Word. See Figure 11. The Control Word can be both written and read as shown in Table 1 and 2. During write operations, the function of the Control Word being written is determined by data bit D7. If D7 is low, the data on D0 - D3 will set or reset one of the bits of Port C. See Figure 12. During read Operations, the

Control Word will always be in the format illustrated in Figure 11 with Bit D7 high to indicate Control Word Mode Information.

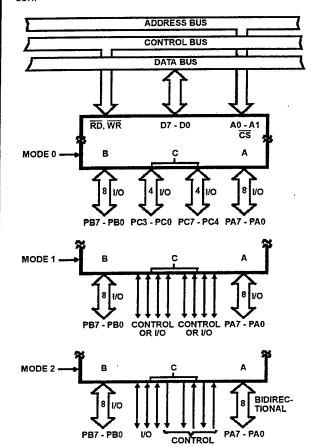


FIGURE 10. BASIC MODE DEFINITIONS & BUS INTERFACE

TABLE 1.

T,	۹1	A0	RD	WR	cs	INPUT OPERATION (READ)
Г	0	٥.	0	1	0	Port A - Data Bus
	0	1	0	1	0	Port B - Data Bus
	1	0	0	1	0	Port C - Data Bus
Г	1	1	0	1	0	Control Word - Data Bus

TABLE 2.

A1	A0	RD	WR	cs	OUTPUT OPERATION (WRITE)
0	0	1	0	0	Data Bus - Port A
0	1	1	0	0	Data Bus - Port B
1	0	1	0	0	Data Bus - Port C
1	1	1	0	0	Data Bus - Control Word

## TABLE 3.

A1	, A0	RD	WR	cs	DISABLE FUNCTION
Х	Х	Х	Х	1	Data Bus - 3-State
Х	Х	1	1	0	Data Bus - 3-State

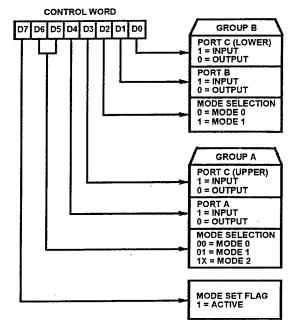


FIGURE 11. MODE SET CONTROL WORD FORMAT

# **Mode Selection**

There are three basic modes of operation that can be selected by the system software:

Mode 0 - Basic Input/Output

Mode 1 - Strobed Input/Output

Mode 2 - Bidirectional Bus

When the RESET input goes "high", all ports will be set to the input mode with all 24 port lines held at the logic "one" level by internal bus hold devices. After reset, the HS-82C55ARH can remain in the input mode with no additional initialization required. This eliminates the need for pullup or pulldown resistors in all CMOS designs. During the execution of the system program, any of the other modes may be selected using a single output instruction. This allows a single HS-82C55ARH to service a variety of peripheral devices with a simple software maintenance routine.

The modes for Port A and Port B can be separately defined while Port C is divided into two portions as required by the Port A and Port B definitions. All of the output registers, including the status register, will be reset whenever the mode is changed. Modes may be combined so that their functional definition can be "tailored" to almost any I/O structure. For instance: Group B can be programmed in Mode 0 to monitor simple switch closings or display computational results, Group A could be programmed in Mode 1 to monitor a keyboard or tape recorder on an interrupt-driven basis.

The mode definitions and possible mode combinations may seem confusing at first but after a cursory review of the complete device operation a simple, logical I/O approach will surface. The design of the HS-82C55ARH has taken into account things such as efficient PC board layout, control signal definition vs PC layout and complete functional flexibility to support almost any peripheral device with no external logic. Such design represents the maximum use of the available pins.

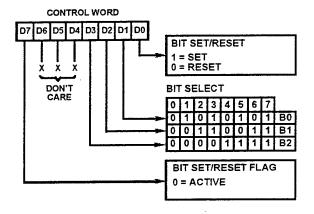


FIGURE 12. BIT SET/RESET CONTROL WORD FORMAT

## Single Bit/Set/Reset Feature

Any of the eight bits of Port C can be Set or Reset using a single OUTput instruction. See Figure 12. This feature reduces software requirements in control-based applications.

## Interrupt Control Functions

When the HS-82C55ARH is programmed to operate in Mode 1 or Mode 2, control signals are provided that can be used as interrupt request inputs to the CPU. The interrupt request signals, generated from Port C, can be inhibited or enable by setting or resetting the associated INTE flip-flop, using the Bit Set/Reset function of Port C.

This function allows the programmer to enable or disable a CPU interrupt by a specific I/O device without affecting any other device in the interrupt structure.

INTE Flip-Flop Definition:

(BIT-SET) - INTE is SET - Interrupt enable.

(BIT-RESET) - INTE is RESET - Interrupt disable.

NOTE: All mask flip-flops are automatically reset during mode selection and device Reset.

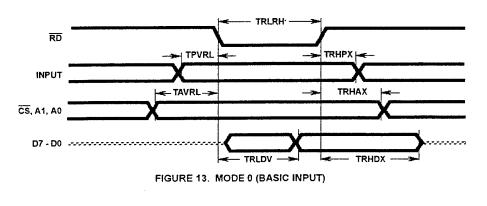
# **Operating Modes**

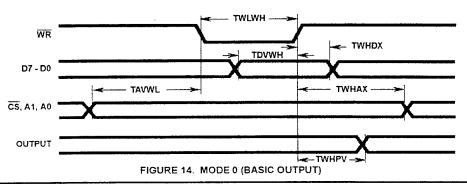
# Mode 0 (Basic Input/Output)

This functional configuration provides simple input and output operations for each of the three ports. No handshaking it required, data is simply written to or read from a specific port.

Mode 0 Basic Functional Definitions:

- · Two 8-bit ports and two 4-bit ports
- · Any port can be input or output
- · Outputs are latched
- · Inputs are not latched
- · 16 different Input/Output configurations possible



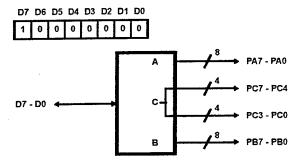


# Mode 0 Port Definition

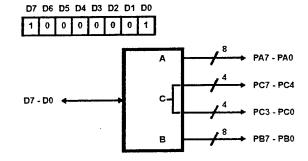
	Α		В		GROUP A		GROUP B	
D4	D3	D1	D0	PORT A	PORT C (UPPER)	NO.	PORTB	PORT C (LOWER)
O	0	0	0	Output	Output	0	Output	Output
0	0	0	1	Output	Output	1	Output	Input
0	0	1	0	Output	Output	2	Input	Output
0	0	1	1	Output	Output	3	Input	Input
0	1	0	0	Output	Input	4	Output	Output
0	1	0	1	Output	Input	5	Output	Input
0	1	1	0	Output	Input	6	Input	Output
0	1	1	1	Output	Input	7	Input	Input
1	0	0	0	Input	Output	8	Output	Output
1	0	0	1	Input	Output	9	Output	Input
1	0	1	0	Input	Output	10	Input	Output
1	0	1	1	Input	Output	11	Input	Input
1	1	0	0	Input	Input	12	Output	Output
1	1	0	1	Input	Input	13	Output	Input
1	1	1	0	Input	Input	14	Input	Output
1	1	1	1	Input	Input	15	Input	Input

# Mode 0 Configurations

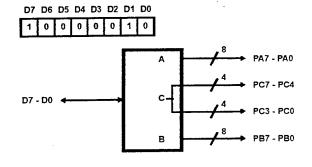
**CONTROL WORD #0** 



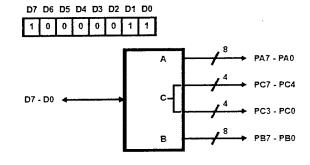
# CONTROL WORD #1

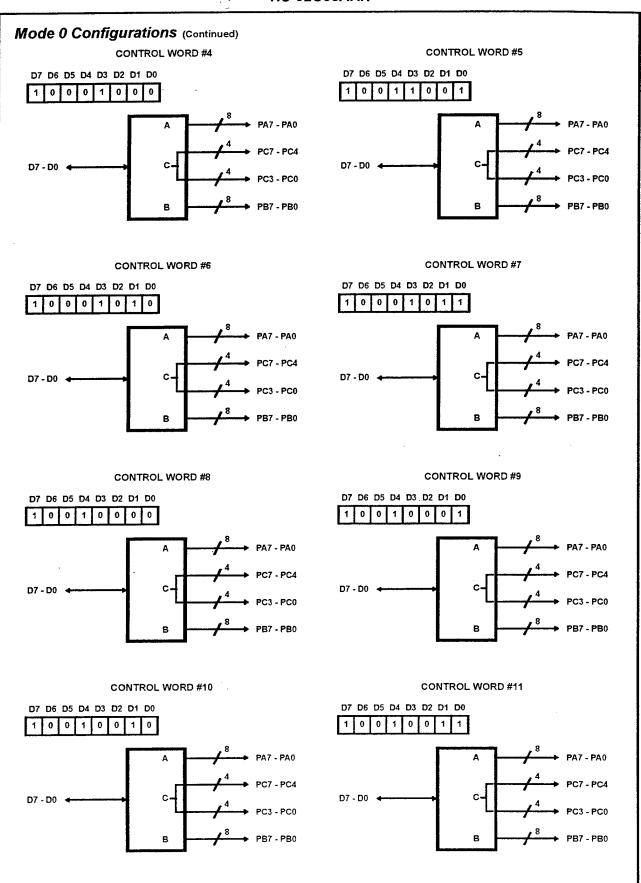


## **CONTROL WORD #2**



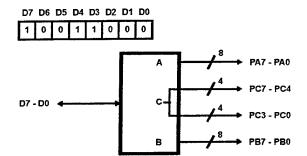
# CONTROL WORD #3



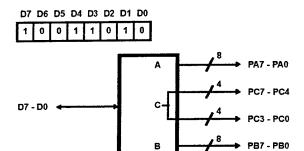


## Mode 0 Configurations (Continued)

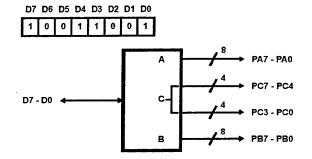
**CONTROL WORD #12** 



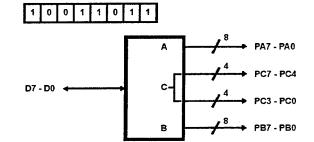
#### **CONTROL WORD #14**



## **CONTROL WORD #13**



**CONTROL WORD #15** 



# **Operating Modes**

## Mode 1 (Strobed Input/Output)

This functional configuration provides a means for transferring I/O data to or from a specified port in conjunction with strobes or "handshaking" signals. In Mode 1, Port A and Port B use the lines on Port C to generate or accept these "handshaking" signals.

Mode 1 Basic Functional Definitions:

- Two Groups (Group A and Group B)
- Each group contains one 8-bit port and one 4-bit control/ data port.
- The 8-bit data port can be either input or output. Both inputs and outputs are latched.
- The 4-bit port is used for control and status of the 8-bit port.

# Input Control Signal Definition

## STB (Strobe input)

A "low" on this input loads data into the input latch.

## IBF (input Buffer Full F/F)

A "high" on this output indicates that the data has been loaded into the input latch; in essence, an acknowledgment. IBF is set by STB input being low and is reset by the rising edge of the RD input.

## **INTR (Interrupt Request)**

D7 D6 D5 D4 D3 D2 D1 D0

A "high" on this output can be used to interrupt the CPU when an input device is requesting service. INTR is set by the rising edge of  $\overline{\text{STB}}$  and reset by the falling edge of  $\overline{\text{RD}}$ . This procedure allows an input device to request service from the CPU by simply strobing its data into the port.

## INTE A

Controlled by Bit Set/Reset of PC4.

## INTE B

Controlled by Bit Set/Reset of PC2.

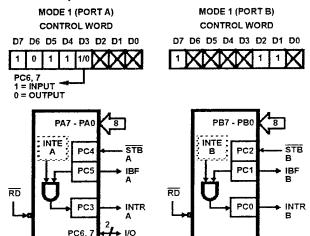


FIGURE 15. MODE 1 INPUT

Spec Number 518060

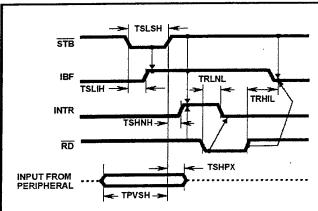


FIGURE 16. MODE 1 (STROBED INPUT)

# **Output Control Signal Definition**

## **OBF** (Output Buffer Full F/F)

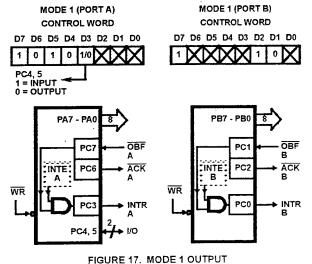
The OBF output will go "low" to indicate that the CPU has written data out to the specified port. This does not mean valid data is sent out of the port at this time since OBF can go true before data is available. Data is guaranteed valid at the rising edge of OBF. See Note 1. The OBF F/F will be set by the rising edge of the WR input and reset by ACK input being low.

# ACK (Acknowledge Input)

A "low" on this input informs the HS-82C55ARH that the data from Port A or Port B is ready to be accepted. In essence, a response from the peripheral device indicating that it is ready to accept data. See Note 1.

# **INTR (Interrupt Request)**

A "high" on this output can be used to interrupt the CPU when an output device has accepted data transmitted by the CPU. INTR is set by the rising edge of ACK and reset by the falling edge of WR.



#### INTE A

Controlled by Bit Set/Reset of PC6.

## INTE B

Controlled by Bit Set/Reset of PC2.

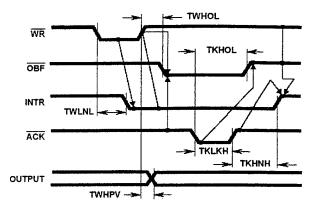


FIGURE 18. MODE 1 (STROBED OUTPUT)

#### NOTE:

To strobe data into the peripheral device, the user must operate the strobe line in a hand shaking mode. The user needs to send OBF to the peripheral device, generate an ACK from the peripheral device and then latch data into the peripheral device on the rising edge of OBF.

Combinations of Mode 1: Port A and Port B can be individually defined as input or output in Mode 1 to support a wide variety of strobed I/O applications.

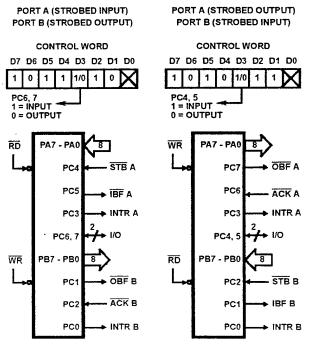


FIGURE 19. COMBINATIONS OF MODE 1

# **Operating Modes**

## MODE 2 (Strobed Bidirectional Bus I/O)

The functional configuration provides a means for communicating with a peripheral device or structure on a single 8-bit bus for both transmitting and receiving data (bidirectional bus I/O). "Handshaking" signals are provided to maintain proper bus flow discipline similar to MODE 1. Interrupt generation and enable/disable functions are also available.

# Mode 2 Basic Functional Definitions:

- · Used in Group A only.
- One 8-bit, bidirectional bus port (Port A) and a 5-bit control port (Port C).
- Both inputs and outputs are latched.
- The 5-bit control port (Port C) is used for control and status for the 8-bit, bidirectional bus port (Port A).

# Bidirectional Bus I/O Control Signal Definition

## **INTR (Interrupt Request)**

A high on this output can be used to interrupt the CPU for both input or output operations. INTR will be set either by the rising edge of  $\overline{ACK}$  (INTE1 = 1) or the rising edge of  $\overline{STB}$  (INTE2 = 1). INTR will be reset by the falling edge of  $\overline{WR}$  (if previously set by the rising edge or  $\overline{ACK}$ ), the falling edge of  $\overline{RD}$  (if previously set by the rising edge of  $\overline{STB}$ ), or the falling edge of  $\overline{WR}$  when immediately following a low  $\overline{RD}$  pulse or the falling edge of  $\overline{RD}$  when immediately following a low  $\overline{WR}$  pulse (if previously set by the rising edges of both  $\overline{ACK}$  and  $\overline{STB}$ ).

# **Output Operations**

## **OBF** (Output Buffer Full)

The  $\overline{\text{OBF}}$  output will go "low" to indicate that the CPU has written data out to Port A.

## **ACK** (Acknowledge)

A "low" on this input enables the tri-state output buffer of Port A to send out the data. Otherwise, the output buffer will be in the high impedance state.

# INTE 1 (The INTE Flip-Flop Associated with OBF)

Controlled by Bit Set/Reset of PC6.

## Input Operations

## STB (Strobe Input)

A "low" on this input loads data into the input latch.

# IBF (Input Buffer Full F/F)

A "high" on this output indicates that data has been loaded into the input latch.

# INTE 2 (The INTE Flip-Flop Associated with IBF)

Controlled by Bit Set/Reset of PC4.

# CONTROL WORD D7 D6 D5 D4 D3 D2 D1 D0 1 0 1/0 1/0 1/0 PC2 - PC0 1 = INPUT 0 = OUTPUT PORT B 1 = INPUT 0 = OUTPUT GROUP B MODE 0 = MODE 0 1 = MODE 1

FIGURE 20. MODE CONTROL WORD

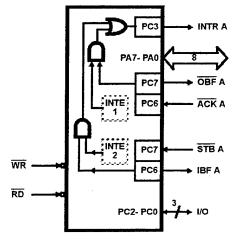
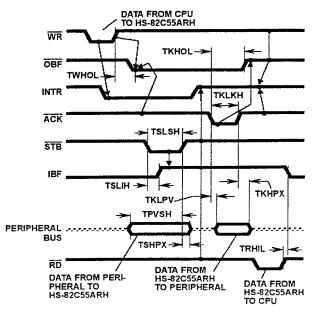


FIGURE 21. MODE 2 (BIDIRECTIONAL)



NOTE: Any sequence where  $\overline{WR}$  occurs before  $\overline{ACK}$  and  $\overline{STB}$  occurs before  $\overline{RD}$  is permissible.

FIGURE 22. MODE 2 (BIDIRECTIONAL)

MODE	DEFINITION	SUMMARY
------	------------	---------

	MODE 0		MOD	E1	MODE 2	
	IN	OUT	1N	OUT	GROUP A ONLY	
PA0 AP1 PA2 PA3 PA4 PA5 PA6 PA7	In In In In In In	Out	In In In In In In	Out		
PB0 PB1 PB2 PB3 PB4 PB5 PB6 PB7	in . In In In In In	Out Out Out Out Out Out Out Out	in In In In In In In	Out	- - - - - -	Mode 0 or Mode 1 Only
PC0 PC1 PC2 PC3 PC4 PC5 PC6 PC7	In In In In In In	Out	INTR B IBF B STB B INTR A STB A IBF A I/O I/O	INTR B OBF B ACK B INTR A I/O I/O ACK A OBF A	I/O I/O I/O INTR A STB A IBF A ACK A OBF A	

# **Special Mode Combination Considerations**

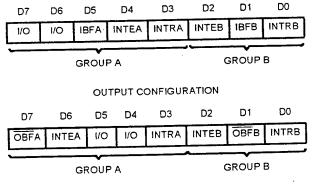
There are several combinations of modes possible. For any combination, some or all of Port C lines are used for control or status. The remaining bits are either inputs or outputs as defined by a "Set Mode" command.

During a read of Port C, the state of all the Port C lines, except the  $\overline{ACK}$  and  $\overline{STB}$  lines, will be placed on the data bus. In place of the ACK and STB line states, flag status will appear on the data bus in the PC2, PC4, and PC6 bit positions as illustrated by Figure 25.

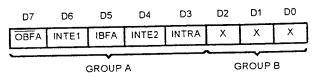
Through a "Write Port C" command, only the Port C pins programmed as outputs in a Mode 0 group can be written. No other pins can be affected by a "Write Port C" command, nor can the interrupt enable flags be accessed. To write to any Port C output programmed as an output in a Mode 1 group or to change an interrupt enable flag, the "Set/Reset Port C Bit" command must be used.

With a "Set/Reset Port C Bit" command, any Port C line programmed as an output (including IBF and OBF) can be written, or an interrupt enable flag can be either set or reset. Port C lines programmed as inputs, including ACK and STB lines, associated with Port C fare not affected by a "Set/Reset Port C Bit" command. Writing to the corresponding Port C bit positions of the ACK and STB lines with the "Set/Reset Port C Bit" command will affect the Group A and Group B interrupt enable flags, as illustrated in Figure 25.

# INPUT CONFIGURATION



# FIGURE 23. MODE 1 STATUS WORD FORMAT



NOTE: (Defined by Mode 0 or Mode 1 Selection)

FIGURE 24. MODE 2 STATUS WORD FORMAT

# **Current Drive Capability**

Any output on Port A, B or C can sink or source 2.5mA. This feature allows the 82C55A to directly drive Darlington type drivers and high-voltage displays that require such sink or source current.

# Reading Port C Status (Figures 23 and 24)

In Mode 0, Port C transfers data to or from the peripheral device. When the 82C55A is programmed to function in Modes 1 or 2, Port C generates or accepts "hand shaking" signals with the peripheral device. Reading the contents of Port C allows the programmer to test or verify the "status" of each peripheral device and change the program flow accordingly.

There is no special instruction to read the status information from Port C. A normal read operation of Port C is executed to perform this function.

INTERRUPT ENABLE FLAG*	POSITION	ALTERNATE PORT C PIN SIGNAL (MODE)
INTE B	PC2	ACKB (Output Mode 1) or STBB (Input Mode 1)
INTE A2	PC4	STBA (Input Mode 1 or Mode 2)
INTE A1	PC6	ACKA (Output Mode 1 or Mode 2)

FIGURE 25. INTERRUPT ENABLE FLAGS IN MODES 1 AND 2

# Metallization Topology

DIE DIMENSIONS:

3420μm × 4350μm × 485μm ± 25μm

**METALLIZATION:** 

Type: Al/Si

Thickness: 11kÅ ± 2kÅ

GLASSIVATION:

Type: SiO2

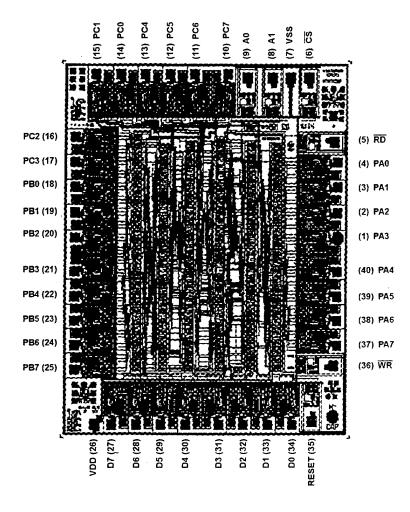
Thickness: 8kÅ ± 1kÅ

WORST CASE CURRENT DENSITY:

 $7.7 \times 10^4 \, \text{A/cm}^2$ 

# Metallization Mask Layout

HS-82C55ARH



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